MBM29DL32XTE/BE80/90



Data Sheet (Retired Product)

This product has been retired and is not recommended for new designs. Availability of this document is retained for reference and historical purposes only.

Continuity of Specifications

There is no change to this data sheet as a result of offering the device as a Spansion product. Any changes that have been made are the result of normal data sheet improvement and are noted in the document revision summary.

For More Information

Please contact your local sales office for additional information about Spansion memory solutions.



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SPANSION™ Flash Memory

Data Sheet



September 2003

This document specifies SPANSION[™] memory products that are now offered by both Advanced Micro Devices and Fujitsu. Although the document is marked with the name of the company that originally developed the specification, these products will be offered to customers of both AMD and Fujitsu.

Continuity of Specifications

There is no change to this datasheet as a result of offering the device as a SPANSIONTM product. Future routine revisions will occur when appropriate, and changes will be noted in a revision summary.

Continuity of Ordering Part Numbers

AMD and Fujitsu continue to support existing part numbers beginning with "Am" and "MBM". To order these products, please use only the Ordering Part Numbers listed in this document.

For More Information

Please contact your local AMD or Fujitsu sales office for additional information about SPANSION[™] memory solutions.





FLASH MEMORY

CMOS

32 M (4 M \times 8/2 M \times 16) BIT Dual Operation

MBM29DL32XTE/BE80/90

■ DESCRIPTION

The MBM29DL32XTE/BE are a 32 M-bit, 3.0 V-only Flash memory organized as 4 Mbytes of 8 bits each or 2 Mwords of 16 bits each. These devices are designed to be programmed in-system with the standard system 3.0 V Vcc supply. 12.0 V VPP and 5.0 V Vcc are not required for write or erase operations. The devices can also be reprogrammed in standard EPROM programmers.

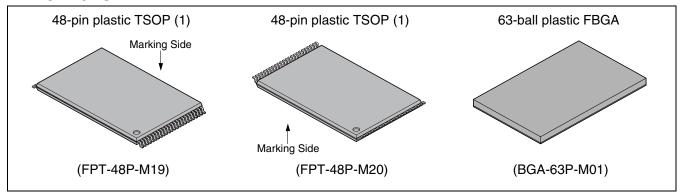
MBM29DL32XTE/BE are organized into two banks, Bank 1 and Bank 2, which are considered to be two separate memory arrays for operations. It is the Fujitsu's standard 3 V only Flash memories, with the additional capability of allowing a normal non-delayed read access from a non-busy bank of the array while an embedded write (either a program or an erase) operation is simultaneously taking place on the other bank.

(Continued)

■ PRODUCT LINE UP

Part No.	MBM29D	L32XTE/BE
Fait No.	80	90
Power Supply Voltage Vcc (V)	3.3 +0.3 -0.3	3.0 +0.6 -0.3
Max Address Access Time (ns)	80	90
Max CE Access Time (ns)	80	90
Max OE Access Time (ns)	30	35

PACKAGES





(Continued)

In the MBM29DL32XTE/BE, a new design concept is implemented, so called "Sliding Bank Architecture". Under this concept, the MBM29DL32XTE/BE can be produced a series of devices with different Bank 1/Bank 2 size combinations; 4 Mb/28 Mb, 8 Mb/24 Mb, 16 Mb/16 Mb.

To eliminate bus contention the devices have separate chip enable (\overline{CE}) , write enable (\overline{WE}) , and output enable (\overline{OE}) controls.

The MBM29DL32XTE/BE are pin and command set compatible with JEDEC standard E²PROMs. Commands are written to the command register using standard microprocessor write timings. Register contents serve as input to an internal state-machine which controls the erase and programming circuitry. Write cycles also internally latch addresses and data needed for the programming and erase operations.

Typically, each sector can be programmed and verified in about 0.5 seconds.

A sector is typically erased and verified in 1.0 second. (If already completely preprogrammed.)

The devices also feature a sector erase architecture. The sector mode allows each sector to be erased and reprogrammed without affecting other sectors. The MBM29DL32XTE/BE are erased when shipped from the factory.

Internally generated and regulated voltages are provided for the program and erase operations. A low V_{CC} detector automatically inhibits write operations on the loss of power. The end of program or erase is detected by \overline{Data} Polling of DQ_7 , by the Toggle Bit feature on DQ_6 , or the RY/ \overline{BY} output pin. Once the end of a program or erase cycle has been completed, the devices internally reset to the read mode.

The MBM29DL32XTE/BE memories electrically erase the entire chip or all bits within a sector simultaneously via Fowler-Nordhiem tunneling. The bytes/words are programmed one byte/word at a time using the EPROM programming mechanism of hot electron injection.

■ FEATURES

- 0.23 μ m Process Technology
- Simultaneous Read/Write operations (dual bank)

Multiple devices available with different bank sizes (Refer to "MBM29DL32XTE/BE Device Bank Divisions" in "EFEATURES")

Host system can program or erase in one bank, then immediately and simultaneously read from the other bank Zero latency between read and write operations

Read-while-erase

Read-while-program

• Single 3.0 V read, program, and erase

Minimizes system level power requirements

Compatible with JEDEC-standard commands

Uses same software commands as E²PROMs

Compatible with JEDEC-standard world-wide pinouts

48-pin TSOP (1) (Package suffix : TN – Normal Bend Type, TR – Reversed Bend Type) 63-ball FBGA (Package suffix : PBT)

- Minimum 100,000 program/erase cycles
- High performance

80 ns maximum access time

· Sector erase architecture

Eight 4 Kword and sixty-three 32 Kword sectors in word mode

Eight 8 Kbyte and sixty-three 64 Kbyte sectors in byte mode

Any combination of sectors can be concurrently erased. Also supports full chip erase.

- Boot Code Sector Architecture
 - T = Top sector
 - B = Bottom sector
- HiddenROM region

64 Kbyte of HiddenROM, accessible through a new "HiddenROM Enable" command sequence Factory serialized and protected to provide a secure electronic serial number (ESN)

WP/ACC input pin

At V_{IL} , allows protection of boot sectors, regardless of sector group protection/unprotection status At V_{ACC} , increases program performance

Embedded Erase[™] Algorithms

Automatically pre-programs and erases the chip or any sector

Embedded Program[™] Algorithms

Automatically writes and verifies data at specified address

- Data Polling and Toggle Bit feature for detection of program or erase cycle completion
- Ready/Busy output (RY/BY)

Hardware method for detection of program or erase cycle completion

Automatic sleep mode

When addresses remain stable, automatically switch themselves to low power mode.

- Low Vcc write inhibit ≤ 2.5 V
- Erase Suspend/Resume

Suspends the erase operation to allow a read data and/or program in another sector within the same device

Sector group protection

Hardware method disables any combination of sector groups from program or erase operations

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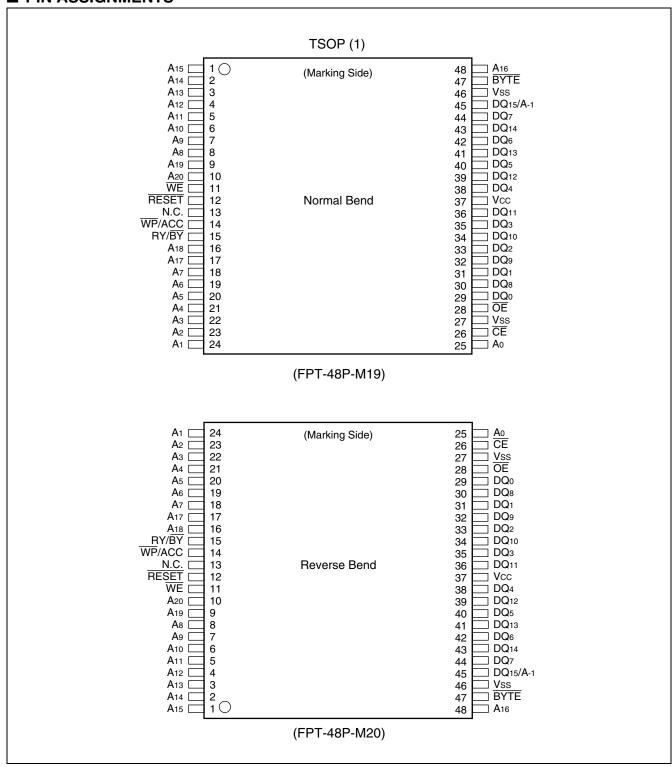
(Continued)

- Sector Group Protection Set function by Extended sector group protection command
- Fast Programming Function by Extended Command
- Temporary sector group unprotection
 Temporary sector group unprotection via the RESET pin.
- In accordance with CFI (Common Flash Memory Interface)

MBM29DL32XTE/BE Device Bank Divisions

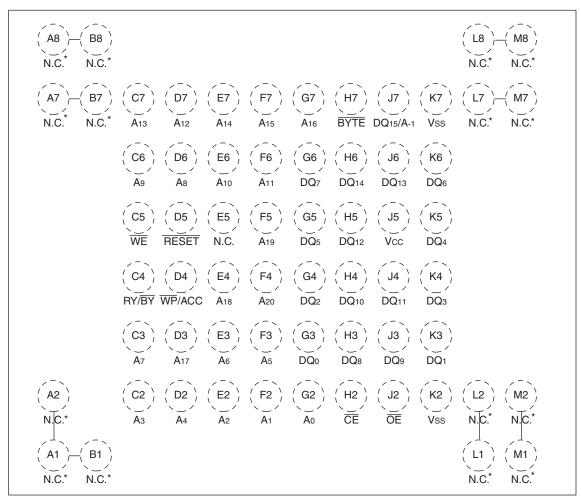
Device	Organiza-		Bank 1		Bank 2
Part Number	tion	Mega- bits	Sector sizes	Mega- bits	Sector sizes
MBM29DL322TE/BE		4 Mbit	Eight 8 Kbyte/4 Kword, seven 64 Kbyte/32 Kword	28 Mbit	Fifty-six 64 Kbyte/32 Kword
MBM29DL323TE/BE	× 8/× 16	8 Mbit	Eight 8 Kbyte/4 Kword, fifteen 64 Kbyte/32 Kword	24 Mbit	Forty-eight 64 Kbyte/32 Kword
MBM29DL324TE/BE		16 Mbit	Eight 8 Kbyte/4 Kword, thirty-one 64 Kbyte/ 32 Kword	16 Mbit	Thirty-two 64 Kbyte/32 Kword

■ PIN ASSIGNMENTS



(Continued)





(BGA-63P-M01)

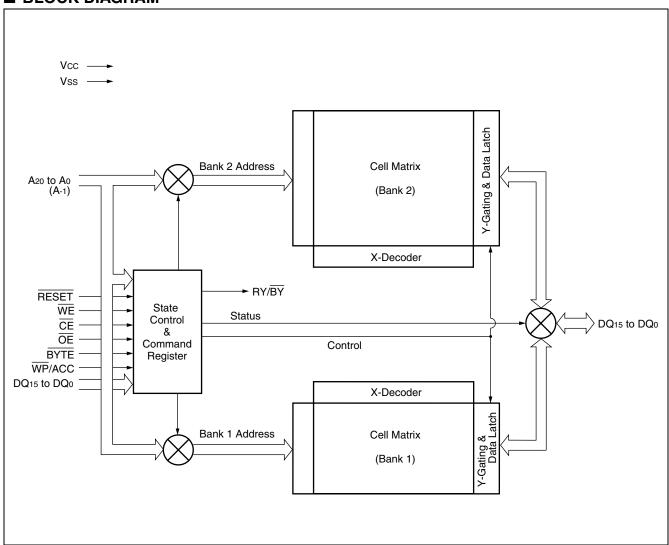
^{*:} Peripheral Balls on each corner are shorted together via substrate but not connected to the die.

■ PIN DESCRIPTIONS

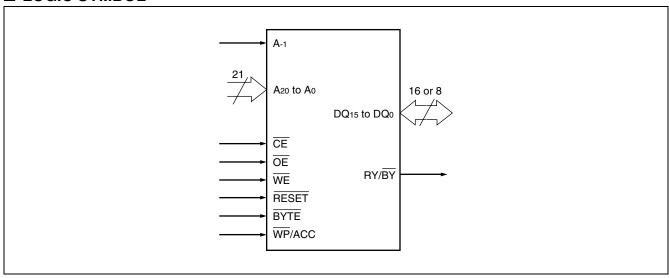
MBM29DL32XTE/BE Pin Configuration

Pin Name	Function
A ₂₀ to A ₀ , A ₋₁	Address Input
DQ ₁₅ to DQ ₀	Data Input/Output
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
RY/ BY	Ready/Busy Output
RESET	Hardware Reset Pin/Temporary Sector Group Unprotection
BYTE	Selects 8-bit or 16-bit mode
WP/ACC	Hardware Write Protection/Program Acceleration
N.C.	No Internal Connection
Vss	Device Ground
Vcc	Device Power Supply

■ BLOCK DIAGRAM



■ LOGIC SYMBOL



■ DEVICE BUS OPERATION

MBM29DL32XTE/BE User Bus Operations (BYTE = VIH)

Operation	CE	ŌĒ	WE	Αo	A 1	A 6	A 9	DQ ₁₅ to DQ ₀	RESET	WP/ACC
Auto-Select Manufacturer Code*1	L	L	Н	L	L	L	VID	Code	Н	Х
Auto-Select Device Code*1	L	L	Н	Н	L	L	VID	Code	Н	Х
Read*3	L	L	Н	A o	A 1	A 6	A 9	D оит	Н	Х
Standby	Н	Х	Х	Χ	Χ	Χ	Х	High-Z	Н	Х
Output Disable	L	Н	Н	Χ	Χ	Χ	Х	High-Z	Н	Х
Write (Program/Erase)	L	Н	L	Ao	A 1	A 6	A 9	Dın	Н	Х
Enable Sector Group Protection*2, *4	L	VID	7	L	Н	L	VID	Х	Н	Х
Verify Sector Group Protection*2, *4	L	L	Н	L	Н	L	VID	Code	Н	Х
Temporary Sector Group Unprotection*5	Х	Х	Х	Χ	Χ	Χ	Х	Х	V _{ID}	Х
Reset (Hardware) /Standby	Х	Х	Х	Χ	Χ	Χ	Х	High-Z	L	Х
Boot Block Sector Write Protection	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Х	Х	L

Legend: $L = V_{IL}$, $H = V_{IH}$, $X = V_{IL}$ or V_{IH} , T = Pulse input. See DC Characteristics for voltage levels.

^{*1 :} Manufacturer and device codes are accessed via a command register write sequence. See "MBM29DL32XTE/BE Command Definitions".

^{*2 :} Refer to the section on Sector Group Protection.

^{*3 :} \overline{WE} can be V_{IL} if \overline{OE} is V_{IL} , \overline{OE} at V_{IH} initiates the write operations.

^{*4 :} $Vcc = 3.3 V \pm 10\%$

^{*5 :} Also used for the extended sector group protection.

MBM29DL32XTE/BE User Bus Operations (BYTE = VIL)

Operation	CE	ŌĒ	WE	DQ ₁₅ /A-1	Ao	A 1	A 6	A 9	DQ ₇ to DQ ₀	RESET	WP/ACC
Auto-Select Manufacturer Code*1	L	L	Н	L	L	L	L	VID	Code	Н	Χ
Auto-Select Device code*1	L	L	Н	L	Н	L	L	VID	Code	Н	Х
Read*3	L	L	Н	A- 1	A o	A 1	A 6	A 9	D оит	Н	Х
Standby	Н	Χ	Х	Χ	Χ	Χ	Х	Х	High-Z	Н	Х
Output Disable	L	Н	Н	Χ	Χ	Χ	Χ	Х	High-Z	Н	Х
Write (Program/Erase)	L	Н	L	A- 1	A ₀	A ₁	A 6	A 9	Din	Н	Х
Enable Sector Group Protection	L	VID	ப	L	L	Н	L	VID	Х	Н	Х
Verify Sector Group Protection*2, *4	L	L	Н	L	L	Н	L	VID	Code	Н	Х
Temporary Sector Group Unprotection*5	Х	Х	Х	Х	Х	Х	Х	Х	Х	VID	Х
Reset (Hardware) /Standby	Χ	Х	Х	Х	Χ	Χ	Х	Х	High-Z	L	Х
Boot Block Sector Write Protection	Χ	Χ	Χ	Х	Χ	Χ	Χ	Χ	Х	Х	L

Legend: $L = V_{IL}$, $H = V_{IH}$, $X = V_{IL}$ or V_{IH} , T = Pulse input. See DC Characteristics for voltage levels.

^{*1 :} Manufacturer and device codes are accessed via a command register write sequence. See "MBM29DL32XTE/BE Command Definitions".

^{*2 :} Refer to the section on Sector Group Protection.

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^{*4 :} $Vcc = 3.3 V \pm 10\%$

^{*5 :} Also used for the extended sector group protection.

MBM29DL32XTE/BE Command Definitions

Comma sequen		Bus write cy-	First write		Second write of		Third write		Fourth read/v	write	Fifth write		Sixth write	
334.5		cles req'd	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data
Read/	Word	1	XXXh	F0h										
Reset*1	Byte		700011	1 011										
Read/	Word	3	555h	AAh	2AAh	55h	555h	F0h	RA*7	RD*7				
Reset*1	Byte		AAAh	70	555h	00	AAAh							
Autoselect	Word	3	555h	AAh	2AAh	55h	(BA) 555h	90h	IA* ⁷	ID*7	_		_	
71010001001	Byte)	AAAh	70 111	555h	0011	(BA) AAAh	0011	17 (1.5				
Program	Word	4	555h	AAh	2AAh	55h	555h	A0h	PA	PD				
Tiogram	Byte	4	AAAh	7711	555h	3311	AAAh	Aun	1 /	ן ו				
Program Suspend		1	ВА	B0h	_		_		_		_		_	
Program Resume		1	ВА	30h	_	_	_	_	_	_	_	_	_	_
Chin Evans	Word	6	555h	AAh	2AAh		555h	006	555h	AAh	2AAh		555h	10h
Chip Erase	Byte	ь	AAAh	AAn	555h	55h	AAAh	80h	AAAh	AAn	555h	55h	AAAh	TUN
Sector	Word	6	555h	AAh	2AAh	55h	555h	80h	555h	AAh	2AAh		SA	30h
Erase	Byte	О	AAAh	AAn	555h	3311	AAAh	OUII	AAAh	AAn	555h	55h	SA	3011
Erase Susp	end	1	ВА	B0h	_									
Erase Resu	me	1	ВА	30h										
Set to	Word	3	555h	AAh	2AAh	EEh	555h	20h						
Fast Mode	Byte	3	AAAh	AAn	555h	55h	AAAh	2011	_		_		_	
Fast Program *2	Word Byte	2	XXXh	A0h	PA	PD	_		_		_		_	_
Reset from	Word					*6								
Fast Mode	Byte	2	BA	90h	XXXh	F0h	_		_		_		_	
Extended Sector	Word		NAM.	001	004	001	004	401	0.0.4	0.0				
Group Protection	Byte	4	XXXh	60h	SPA	60h	SPA	40h	SPA	SD				
Quan:*4	Word	4	(BA) 55h	OOL										
Query*4	Byte	1	(BA) AAh	98h										

(Continued)

Comman sequence	-	Bus write cy-	First write		Second write of		Third write o		Fourth read/v cyc	write	Fifth write		Sixth write	
		cles req'd	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data	Addr.	Data
HiddenROM	Word	3	555h	AAh	2AAh	55h	555h	88h						
Entry	Byte	3	AAAh	7711	555h	3311	AAAh	0011						
HiddenROM	Word	4	555h	AAh	2AAh	55h	555h	A0h	(HRA)	PD				
Program *5	Byte	4	AAAh	7711	555h 55h	AAAh	Aui	PA	וו					
HiddenROM	Word	6	555h	AAh	2AAh	55h	555h	80h	555h	AAh	2AAh	55h	HRA	30h
Erase *5	Byte	O	AAAh	7711	555h	3311	AAAh	0011	AAAh	7711	555h	3311	11117	3011
HiddenROM	Word	4	555h	ΔΔh	2AAh	55h	(HRBA) 555h	90h	XXXh	00h				
Exit *5 Byte	4	AAAh		3311	(HRBA) AAAh		7000	0011						

- *1 : Both of these reset commands are equivalent.
- *2 : This command is valid during Fast Mode.
- *3 : This command is valid while $\overline{RESET} = V_{ID}$ (except during HiddenROM MODE).
- *4: The valid address are A6 to A0.
- *5: This command is valid during HiddenROM mode.
- *6: The data "00h" is also acceptable.
- *7: The fourth bus cycle is only for read.
- Notes: Address bits A₂₀ to A₁₁ = X = "H" or "L" for all address commands except or Program Address (PA), Sector Address (SA), Bank Address (BA) and Sector Group Address (SPA).
 - Bus operations are defined in "MBM29DL32XTE/BE User Bus Operations (BYTE = V_{IH})" and "MBM29DL32XTE/BE User Bus Operations (BYTE = V_{IL})".
 - RA = Address of the memory location to be read
 - IA = Autoselect read address sets both the bank address specified at $(A_{19}, A_{18}, A_{17}, A_{16}, A_{15})$ and all the other $A_6, A_1, A_0, (A_{-1})$.
 - PA = Address of the memory location to be programmed Addresses are latched on the falling edge of the write pulse.
 - SA = Address of the sector to be erased. The combination of A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} , and A_{12} will uniquely select any sector.
 - BA = Bank Address (A20 to A15)
 - RD = Data read from location RA during read operation.
 - ID = Device code/manufacture code for the address located by IA.
 - PD = Data to be programmed at location PA. Data is latched on the rising edge of write pulse.
 - SPA = Sector group address to be protected. Set sector group address and $(A_6, A_1, A_0) = (0, 1, 0)$.
 - SD = Sector group protection verify data. Output 01h at protected sector group addresses and output 00h at unprotected sector group addresses.
 - HRA = Address of the HiddenROM area

29DL32XTE (Top Boot Type) Word Mode: 1F8000h to 1FFFFFh

Byte Mode: 3F0000h to 3FFFFh

29DL32XBE (Bottom Boot Type) Word Mode: 000000h to 007FFFh

Byte Mode: 000000h to 00FFFFh

• HRBA = Bank Address of the HiddenROM area

29DL32XTE (Top Boot Type) : $A_{20} = A_{19} = A_{18} = A_{17} = A_{16} = A_{15} = V_{IH}$ 29DL32XBE (Bottom Boot Type) : $A_{20} = A_{19} = A_{18} = A_{17} = A_{16} = A_{15} = V_{IL}$

• The system should generate the following address patterns :

Word Mode: 555h or 2AAh to addresses A10 to A0

Byte Mode : AAAh or 555h to addresses A_{10} to A_{0} , and A_{-1}

- Both Read/Reset commands are functionally equivalent, resetting the device to the read mode.
- The command combinations not described in "MBM29DL32XTE/BE Command Definitions" are illegal.

In case of applying V_{ID} on A_9 , since both Bank 1 and Bank 2 enters Autoselect mode, the simultaneous operation can not be executed.

MBM29DL322TE/BE Sector Group Protection Verify Autoselect Codes

	Туре		A ₂₀ to A ₁₂	A 6	A 1	A 0	A- 1*1	Code (HEX)
Manufac	ture's Code		BA*3	VıL	Vıl	VıL	VIL	04h
	MBM29DL322TE	Byte	BA*3	VIL	VIL	Vih	VıL	55h
Device	MDMZ9DL3221E	Word	DA -	VIL	VIL	VIH	Х	2255h
Code	MBM29DL322BE	Byte	BA*3	VIL	VIL	ViH	VıL	56h
	MIDINIZADE255	Word	DA °	VIL	VIL	VIH	Х	2256h
Sector G	or Group Protection		Sector group addresses	VıL	ViH	VıL	VIL	01h*2

^{*1 :} A-₁ is for Byte mode. At Byte mode, DQ₈ to DQ₁₄ are High-Z and DQ₁₅ is A-₁, the lowest address.

Extended Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ ₅	DQ ₄	DQ ₃	DQ ₂	DQ ₁	DQ ₀
Manufa	cturer's Code		04h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL322	(B) *	55h	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	1	0	1
Device	TE	(W)	2255h	0	0	1	0	0	0	1	0	0	1	0	1	0	1	0	1
Code	MBM29DL322	(B) *	56h	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	1	1	0
	BE	(W)	2256h	0	0	1	0	0	0	1	0	0	1	0	1	0	1	1	0
Sector	Group Protectio	n	01h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

^{*:} At Byte mode, DQ8 to DQ14 are High-Z and DQ15 is A-1, the lowest address.

(B) : Byte mode(W) : Word modeHI-Z : High-Z

^{*2 :} Outputs 01h at protected sector group addresses and outputs 00h at unprotected sector group addresses.

^{*3:} When V_{ID} is applied to A₉, both Bank 1 and Bank 2 are put into Autoselect mode, which makes simultaneous operation unable to be executed. Consequently, specifying the bank address is not required. However, the bank address needs to be indicated when Autoselect mode is read out at command mode, because then it enables to activate simultaneous operation.

MBM29DL323TE/BE Sector Group Protection Verify Autoselect Codes

	Туре		A ₂₀ to A ₁₂	A 6	A 1	A 0	A- 1*1	Code (HEX)
Manufac	ture's Code		BA*3	VıL	Vıl	VıL	VIL	04h
	MBM29DL323TE	Byte	BA*3	VIL	VIL	Vih	VıL	50h
Device	WIDIWIZ9DE3231E	Word	DA ·	V IL	VIL	VIH	Х	2250h
Code	MBM29DL323BE	Byte	BA*3	VIL	VIL	Vih	Vıl	53h
	WIDIWIZƏDESZSIDE	Word	DA ·	V IL	VIL	VIH	Х	2253h
Sector G	roup Protection		Sector group addresses	VıL	VIH	VıL	VıL	01h*²

^{*1 :} A-1 is for Byte mode. At Byte mode, DQ8 to DQ14 are High-Z and DQ15 is A-1, the lowest address.

Extended Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ ₁₀	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ ₅	DQ ₄	DQ ₃	DQ ₂	DQ ₁	DQo
Manufa	acturer's Code		04h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL323	(B) *	50h	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	0	0	0
Device	TE	(W)	2250h	0	0	1	0	0	0	1	0	0	1	0	1	0	0	0	0
Code	MBM29DL323	(B) *	53h	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	0	0	1	1
	BE	(W)	2253h	0	0	1	0	0	0	1	0	0	1	0	1	0	0	1	1
Sector	Group Protection	า	01h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

^{*:} At Byte mode, DQ8 to DQ14 are High-Z and DQ15 is A-1, the lowest address.

(B) : Byte mode(W) : Word modeHI-Z : High-Z

^{*2 :} Outputs 01h at protected sector group addresses and outputs 00h at unprotected sector group addresses.

^{*3:} When V_{ID} is applied to A₉, both Bank 1 and Bank 2 are put into Autoselect mode, which makes simultaneous operation unable to be executed. Consequently, specifying the bank address is not required. However, the bank address needs to be indicated when Autoselect mode is read out at command mode, because then it enables to activate simultaneous operation.

MBM29DL324TE/BE Sector Group Protection Verify Autoselect Codes

	Туре		A ₂₀ to A ₁₂	A 6	A 1	Ao	A- 1*1	Code (HEX)
Manufac	ture's Code		BA*3	VıL	Vıl	VıL	VIL	04h
	MBM29DL324TE	Byte	BA*3	VIL	VIL	ViH	VıL	5Ch
Device	MDM29DL3241L	Word	DA ·	V IL	VIL	VIH	Х	225Ch
Code	MBM29DL324BE	Byte	BA*3	VIL	VIL	Vih	VIL	5Fh
	MDM29DL324BE	Word	DA -	V IL	VIL	VIH	Х	225Fh
Sector G	Sector Group Protection		Sector group addresses	VIL	ViH	VıL	VIL	01h⁺²

^{*1 :} A-1 is for Byte mode. At Byte mode, DQ8 to DQ14 are High-Z and DQ15 is A-1, the lowest address.

Extended Autoselect Code Table

	Туре		Code	DQ ₁₅	DQ ₁₄	DQ ₁₃	DQ ₁₂	DQ ₁₁	DQ 10	DQ ₉	DQ ₈	DQ ₇	DQ ₆	DQ ₅	DQ ₄	DQ ₃	DQ ₂	DQ ₁	DQo
Manufa	acturer's Code		04h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
	MBM29DL324	(B) *	5Ch	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	1	0	0
Device	TE	(W)	225Ch	0	0	1	0	0	0	1	0	0	1	0	1	1	1	0	0
Code	MBM29DL324	(B) *	5Fh	A- 1	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	HI-Z	0	1	0	1	1	1	1	1
	BE	(W)	225Fh	0	0	1	0	0	0	1	0	0	1	0	1	1	1	1	1
Sector	Group Protection	า	01h	A- ₁ /	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

^{*:} At Byte mode, DQ8 to DQ14 are High-Z and DQ15 is A-1, the lowest address.

(B) : Byte mode(W) : Word modeHI-Z : High-Z

^{*2 :} Outputs 01h at protected sector group addresses and outputs 00h at unprotected sector group addresses.

^{*3:} When V_{ID} is applied to A₉, both Bank 1 and Bank 2 are put into Autoselect mode, which makes simultaneous operation unable to be executed. Consequently, specifying the bank address is not required. However, the bank address needs to be indicated when Autoselect mode is read out at command mode, because then it enables to activate simultaneous operation.

■ FLEXIBLE SECTOR-ERASE ARCHITECTURE

Sector Address Table (MBM29DL322TE)

Sec						Sec							Sector	9DL3221E)	
No	Bank			Baı									size		
SA1		tor	A 20	ı .		1		A 15	A 14	A 13	A 12	A 11		Address range	Address range
SA2		SA0	0	0	0	0	0	0	Х	Х	Х	Х	64/32	000000h to 00FFFFh	000000h to 007FFFh
SA3		SA1	0	0	0	0	0	1	Χ	Х	Х	Х	64/32	010000h to 01FFFFh	008000h to 00FFFFh
SA4		SA2	0	0	0	0	1	0	Х	Х	Х	Х	64/32	020000h to 02FFFFh	010000h to 017FFFh
SA5		SA3	0	0	0	0	1	1	Х	Х	Х	Χ	64/32	030000h to 03FFFFh	018000h to 01FFFFh
SA6		SA4	0	0	0	1	0	0	Х	Х	Х	Х	64/32	040000h to 04FFFFh	020000h to 027FFFh
SA7		SA5	0	0	0	1	0	1	Х	Х	Х	Х	64/32	050000h to 05FFFFh	028000h to 02FFFFh
SAB 0 0 1 0 0 0 X X X X 64/32 080000h to 08FFFFh 040000h to 047FFFh		SA6	0	0	0	1	1	0	Х	Х	Х	Х	64/32	060000h to 06FFFFh	030000h to 037FFFh
SA9		SA7	0	0	0	1	1	1	Х	Х	Х	Х	64/32	070000h to 07FFFFh	038000h to 03FFFFh
SA10		SA8	0	0	1	0	0	0	Χ	Х	Х	Χ	64/32	080000h to 08FFFFh	040000h to 047FFFh
SA11 0 0 1 1 1 X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FFFFh SA12 0 0 1 1 0 0 0 X X X X 64/32 0C0000h to 0CFFFFh 060000h to 067FFFh SA13 0 0 1 1 1 0 0 1 X X X X 64/32 0D0000h to 0DFFFFh 068000h to 06FFFFh SA14 0 0 1 1 1 1 X X X X 64/32 0E0000h to 0EFFFFh 070000h to 07FFFFh SA15 0 0 1 1 1 1 1 X X X X 64/32 0E0000h to 0EFFFFh 078000h to 07FFFFh SA15 0 0 1 1 1 1 1 X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFFh SA16 0 1 0 0 0 0 0 X X X X 64/32 100000h to 10FFFFh 088000h to 08FFFFh SA17 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFFh 088000h to 08FFFFh SA18 0 1 0 0 0 1 1 X X X X 64/32 120000h to 12FFFFh 098000h to 09FFFFh SA20 0 1 0 1 0 0 X X X X 64/32 130000h to 13FFFFh 098000h to 09FFFFh SA21 0 1 0 1 0 1 X X X X 64/32 130000h to 14FFFFh 088000h to 08FFFFh SA22 0 1 0 1 1 0 X X X X 64/32 150000h to 15FFFFh 088000h to 08FFFFh SA23 0 1 0 1 1 1 X X X X 64/32 150000h to 15FFFFh 088000h to 08FFFFh SA25 0 1 1 0 0 0 X X X X 64/32 180000h to 18FFFFh 088000h to 08FFFFh SA26 0 1 1 0 0 0 X X X X 64/32 180000h to 18FFFFh 0D8000h to 0FFFFFh SA28 0 1 1 0 1 X X X X 64/32 180000h to 18FFFFh 0D8000h to 0FFFFFh SA29 0 1 1 1 0 X X X X 64/32 180000h to 18FFFFh 0B8000h to 0FFFFFh SA29 0 1 1 1 1 0 X X X X 64/32 180000h to 18FFFFh 0E8000h to 0FFFFFh SA30 0 1 1 1 1 1 X X X X 64/32 180000h to 18FFFFh 0F8000h to 0FFFFFh SA31 0 1 1 1 1 1 1 1 1		SA9	0	0	1	0	0	1	Х	Х	Х	Х	64/32	090000h to 09FFFFh	048000h to 04FFFFh
SA12		SA10	0	0	1	0	1	0	Х	Х	Х	Х	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh
Bank 2 SA13 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFFh 068000h to 06FFFFh SA14 0 0 1 1 1 0 X X X 64/32 0E0000h to 0EFFFFh 070000h to 077FFFh SA15 0 0 1 1 1 X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFFh SA16 0 1 0 0 0 X X X 64/32 100000h to 10FFFFh 078000h to 07FFFh SA17 0 1 0 0 1 X X X 64/32 110000h to 11FFFFh 08000h to 08FFFh SA18 0 1 0 0 1 X X X 64/32 120000h to 12FFFFh 098000h to 09FFFh SA21 0 1 0 1 X X X 64/32 150000h to 15FFFFh 0400		SA11	0	0	1	0	1	1	Х	Х	Х	Х	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh
Bank 2 SA14 0 0 1 1 1 0 X X X 64/32 0E0000h to 0EFFFFh 07000h to 077FFhh SA15 0 0 1 1 1 1 X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFh SA16 0 1 0 0 0 X X X 64/32 10000h to 10FFFFh 080000h to 087FFFh SA17 0 1 0 0 1 X X X 64/32 110000h to 10FFFFh 08000h to 087FFFh SA18 0 1 0 0 1 X X X 64/32 120000h to 12FFFFh 090000h to 097FFFh SA18 0 1 0 0 1 X X X 64/32 120000h to 13FFFFh 090000h to 097FFFh SA20 0 1 0 1 X X X 64/32 150000h to 15FFFFh 0A8000h to 087FFFh <td></td> <td>SA12</td> <td>0</td> <td>0</td> <td>1</td> <td>1</td> <td>0</td> <td>0</td> <td>Х</td> <td>Х</td> <td>Х</td> <td>Х</td> <td>64/32</td> <td>0C0000h to 0CFFFFh</td> <td>060000h to 067FFFh</td>		SA12	0	0	1	1	0	0	Х	Х	Х	Х	64/32	0C0000h to 0CFFFFh	060000h to 067FFFh
Bank 2 SA15 0 0 1 1 1 X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFFh SA16 0 1 0 0 0 X X X 64/32 100000h to 10FFFFh 080000h to 087FFFh SA17 0 1 0 0 1 X X X 64/32 110000h to 10FFFFh 080000h to 087FFFh SA18 0 1 0 0 1 0 X X X 64/32 120000h to 12FFFFh 090000h to 097FFFh SA19 0 1 0 0 X X X 64/32 130000h to 13FFFFh 098000h to 097FFFh SA20 0 1 0 1 X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7FFFh SA21 0 1 0 1 X X X 64/32 150000h to 15FFFFh 0A8000h to 0AFFFFh SA22 <td< td=""><td></td><td>SA13</td><td>0</td><td>0</td><td>1</td><td>1</td><td>0</td><td>1</td><td>Х</td><td>Х</td><td>Х</td><td>Х</td><td>64/32</td><td>0D0000h to 0DFFFFh</td><td>068000h to 06FFFFh</td></td<>		SA13	0	0	1	1	0	1	Х	Х	Х	Х	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh
Bank 2 SA16 0 1 0 0 0 X X X 64/32 100000h to 10FFFFh 080000h to 087FFhh SA17 0 1 0 0 1 X X X 64/32 110000h to 10FFFFh 080000h to 087FFhh SA18 0 1 0 0 1 0 X X X 64/32 120000h to 12FFFFh 090000h to 097FFFh SA19 0 1 0 0 1 1 X X X 64/32 130000h to 13FFFFh 098000h to 097FFFh SA20 0 1 0 1 X X X 64/32 140000h to 14FFFFh 0A8000h to 0A7FFFh SA21 0 1 0 1 X X X 64/32 150000h to 15FFFFh 0A8000h to 0A7FFFh SA22 0 1 0 1 X X X 64/32 160000h to 15FFFFh 0B0000h to 0B7FFFh SA		SA14	0	0	1	1	1	0	Х	Х	Х	Х	64/32	0E0000h to 0EFFFFh	070000h to 077FFFh
SA16 0 1 0 0 0 0 X X X X X 64/32 100000h to 10FFFFh 080000h to 087FFFh SA18 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFFh 088000h to 08FFFFh SA18 0 1 0 0 1 1 X X X X 64/32 120000h to 12FFFFh 098000h to 09FFFFh SA20 0 1 0 1 0 0 X X X X X 64/32 130000h to 13FFFFh 098000h to 09FFFFh SA21 0 1 0 1 0 1 X X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7FFFh SA21 0 1 0 1 1 0 X X X X 64/32 150000h to 15FFFFh 0A0000h to 0AFFFFh SA22 0 1 0 1 1 1 X X X X 64/32 150000h to 15FFFFh 0B0000h to 0BFFFFh SA23 0 1 0 1 1 1 X X X X 64/32 160000h to 15FFFFh 0B0000h to 0BFFFFh SA24 0 1 1 0 0 0 X X X X X 64/32 170000h to 17FFFFh 0B0000h to 0BFFFFh SA25 0 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0C0000h to 0C7FFFh SA26 0 1 1 0 0 1 X X X X X 64/32 190000h to 19FFFFh 0C0000h to 0C7FFFh SA26 0 1 1 0 1 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA26 0 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA26 0 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA27 0 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA28 0 1 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA30 0 1 1 1 1 0 0 X X X X X 64/32 180000h to 1FFFFFh 0E0000h to 0E7FFFh SA30 0 1 1 1 1 0 X X X X X 64/32 180000h to 1FFFFFh 0F0000h to 0FFFFFh SA30 0 1 1 1 1 1 X X X X X 64/32 180000h to 1FFFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F0000h to 0FFFFFh		SA15	0	0	1	1	1	1	Х	Х	Х	Χ	64/32	0F0000h to 0FFFFh	078000h to 07FFFFh
SA17 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFFh 088000h to 08FFFFh SA18 0 1 0 0 1 0 X X X X X 64/32 120000h to 12FFFFh 090000h to 097FFFh SA20 0 1 0 1 0 0 X X X X X 64/32 130000h to 13FFFFh 098000h to 09FFFFh SA21 0 1 0 1 0 1 X X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7FFFh SA22 0 1 0 1 0 1 X X X X 64/32 150000h to 15FFFFh 0A0000h to 0A7FFFh SA22 0 1 0 1 1 1 X X X X 64/32 150000h to 15FFFFh 0B0000h to 0B7FFFh SA23 0 1 0 1 1 1 X X X X X 64/32 160000h to 16FFFFh 0B0000h to 0B7FFFh SA24 0 1 1 0 0 0 X X X X X 64/32 170000h to 17FFFFh 0B0000h to 0B7FFFh SA25 0 1 1 0 0 1 X X X X X 64/32 180000h to 18FFFFh 0C0000h to 0C7FFFh SA26 0 1 1 0 0 1 X X X X X 64/32 190000h to 19FFFFh 0C8000h to 0C7FFFh SA26 0 1 1 0 1 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA27 0 1 1 0 1 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA28 0 1 1 1 0 0 X X X X X 64/32 180000h to 18FFFFh 0D0000h to 0D7FFFh SA29 0 1 1 1 0 1 X X X X X 64/32 110000h to 18FFFFh 0D0000h to 0D7FFFh SA30 0 1 1 1 1 0 X X X X X 64/32 1100000h to 10FFFFh 0E0000h to 0E7FFFh SA30 0 1 1 1 1 X X X X X 64/32 110000h to 10FFFFh 0F0000h to 0FFFFFh SA30 0 1 1 1 1 X X X X X 64/32 110000h to 10FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 1 1 X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 1 1 X X X X X X 64/32 110000h to 110FFFFh 0F0000h to 0FFFFFh SA31 0 1 1 1 1 1 1 1 1 X X X X X X 64/32 110000h to 110FFF		SA16	0	1	0	0	0	0	Х	Х	Х	Х	64/32	100000h to 10FFFFh	080000h to 087FFFh
SA19	_	SA17	0	1	0	0	0	1	Х	Х	Х	Х	64/32	110000h to 11FFFFh	088000h to 08FFFFh
SA20 0 1 0 1 0 0 X X X A 64/32 140000h to 14FFFh 0A0000h to 0A7FFFh SA21 0 1 0 1 X X X X 64/32 150000h to 15FFFh 0A8000h to 0A7FFFh SA22 0 1 0 1 1 0 X X X 64/32 160000h to 16FFFh 0B0000h to 0B7FFh SA23 0 1 0 1 1 X X X 64/32 170000h to 17FFFh 0B8000h to 0B7FFh SA24 0 1 1 0 0 X X X 64/32 180000h to 18FFFFh 0C8000h to 0C7FFFh SA25 0 1 1 0 X X X 64/32 190000h to 18FFFFh 0C8000h to 0C7FFFh SA26 0 1 1 0 X X X 64/32 180000h to 18FFFFh 0D8000h to 0D7FFFh		SA18	0	1	0	0	1	0	Х	Х	Х	Х	64/32	120000h to 12FFFFh	090000h to 097FFFh
SA21 0 1 0 1 0 1 X X X X 64/32 150000h to 15FFFh 0A8000h to 0AFFFh SA22 0 1 0 1 1 1 X X X X 64/32 160000h to 16FFFh 0B0000h to 0B7FFh SA23 0 1 0 1 1 1 X X X X 64/32 170000h to 17FFFh 0B8000h to 0BFFFh SA24 0 1 1 0 0 0 X X X X X 64/32 180000h to 18FFFh 0C0000h to 0C7FFh SA25 0 1 1 0 0 1 X X X X 64/32 190000h to 19FFFh 0C8000h to 0C7FFFh SA26 0 1 1 0 1 0 X X X X X 64/32 190000h to 18FFFh 0D0000h to 0D7FFFh SA27 0 1 1 0 1 X X X X X 64/32 180000h to 18FFFh 0D0000h to 0D7FFFh SA28 0 1 1 0 0 1 X X X X X 64/32 1B0000h to 1BFFFh 0D8000h to 0D7FFFh SA28 0 1 1 1 0 0 X X X X X 64/32 1C0000h to 1CFFFFh 0E0000h to 0E7FFFh SA29 0 1 1 1 0 X X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0E7FFFh SA30 0 1 1 1 1 0 X X X X X 64/32 1E0000h to 1EFFFFh 0F0000h to 0F7FFFh SA31 0 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F8000h to 0F7FFFh		SA19	0	1	0	0	1	1	Х	Х	Х	Х	64/32	130000h to 13FFFFh	098000h to 09FFFFh
SA22		SA20	0	1	0	1	0	0	Х	Х	Х	Х	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh
SA23		SA21	0	1	0	1	0	1	Х	Х	Х	Х	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh
SA24 0 1 1 0 0 0 X X X X 64/32 180000h to 18FFFh 0C0000h to 0C7FFh SA25 0 1 1 0 0 1 X X X X 64/32 190000h to 19FFFh 0C8000h to 0CFFFh SA26 0 1 1 0 1 0 X X X X 64/32 1A0000h to 1AFFFFh 0D0000h to 0D7FFh SA27 0 1 1 0 1 1 X X X X 64/32 1B0000h to 1BFFFh 0D8000h to 0DFFFh SA28 0 1 1 1 0 0 X X X X X 64/32 1C0000h to 1CFFFh 0E0000h to 0E7FFh SA29 0 1 1 1 0 1 X X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0E7FFFh SA30 0 1 1 1 1 0 X X X X X 64/32 1E0000h to 1EFFFh 0F0000h to 0F7FFh SA31 0 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFh 0F8000h to 0F7FFFh		SA22	0	1	0	1	1	0	Х	Х	Х	Х	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh
SA25 0 1 1 0 0 1 X X X X 64/32 190000h to 19FFFh 0C8000h to 0CFFFh SA26 0 1 1 0 1 0 X X X X 64/32 1A0000h to 1AFFFh 0D0000h to 0D7FFh SA27 0 1 1 0 1 1 X X X X 64/32 1B0000h to 1BFFFh 0D8000h to 0DFFFh SA28 0 1 1 1 0 0 X X X X X 64/32 1C0000h to 1CFFFh 0E0000h to 0E7FFh SA29 0 1 1 1 0 1 X X X X X 64/32 1D0000h to 1DFFFh 0E8000h to 0E7FFh SA30 0 1 1 1 1 0 X X X X X 64/32 1E0000h to 1EFFFh 0F0000h to 0F7FFh SA31 0 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFh 0F8000h to 0F7FFFh		SA23	0	1	0	1	1	1	Χ	Х	Х	Χ	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh
SA26 0 1 1 0 1 0 X X X X 64/32 1A0000h to 1AFFFFh 0D0000h to 0D7FFFh SA27 0 1 1 0 1 1 X X X X 64/32 1B0000h to 1BFFFFh 0D8000h to 0DFFFFh SA28 0 1 1 1 0 0 X X X X 64/32 1C0000h to 1CFFFFh 0E0000h to 0E7FFFh SA29 0 1 1 1 0 1 X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0E7FFFh SA30 0 1 1 1 1 0 X X X X 64/32 1E0000h to 1EFFFFh 0F0000h to 0F7FFFh SA31 0 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F8000h to 0F7FFFh		SA24	0	1	1	0	0	0	Χ	Х	Х	Х	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh
SA27 0 1 1 0 1 1 X X X X X A/32 1B0000h to 1BFFFh 0D8000h to 0DFFFh SA28 0 1 1 1 0 0 X X X X A/32 1C0000h to 1CFFFh 0E0000h to 0E7FFh SA29 0 1 1 1 0 1 X X X X A/32 1D0000h to 1DFFFFh 0E8000h to 0E7FFFh SA30 0 1 1 1 1 1 X X X X A/32 1E0000h to 1EFFFFh 0F8000h to 0FFFFFh SA31 0 1 1 1 1 X X X X A/32 1F0000h to 1FFFFFh 0F8000h to 0FFFFFh		SA25	0	1	1	0	0	1	X	Х	X	X	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh
SA28 0 1 1 1 0 0 X X X A 64/32 1C0000h to 1CFFFh 0E0000h to 0E7FFh SA29 0 1 1 1 0 1 X X X A 64/32 1D0000h to 1DFFFh 0E8000h to 0EFFFh SA30 0 1 1 1 1 0 X X X X 64/32 1E0000h to 1EFFFh 0F0000h to 0F7FFh SA31 0 1 1 1 1 X X X A 64/32 1F0000h to 1FFFFh 0F8000h to 0FFFFh		SA26	0	1	1	0	1	0	Х	Х	Х	Х	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh
SA29 0 1 1 1 0 1 X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0EFFFFh SA30 0 1 1 1 1 0 X X X X 64/32 1E0000h to 1EFFFFh 0F0000h to 0F7FFFh SA31 0 1 1 1 1 X X X X X 64/32 1F0000h to 1FFFFFh 0F8000h to 0FFFFFh		SA27	0	1	1	0	1	1	Х	Х	Х	Х	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh
SA30 0 1 1 1 0 X X X X 64/32 1E0000h to 1EFFFFh 0F0000h to 0F7FFFh SA31 0 1 1 1 1 X X X X 64/32 1F0000h to 1FFFFFh 0F8000h to 0FFFFFh		SA28	0	1	1	1	0	0	X	Х	Χ	X	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFh
SA31 0 1 1 1 1 X X X X 64/32 1F0000h to 1FFFFh 0F8000h to 0FFFFh		SA29	0	1	1	1	0	1	Χ	Х	Χ	Χ	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh
		SA30	0	1	1	1	1	0	Χ	Х	Χ	Χ	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFFh
SA32 1 0 0 0 0 X X X X 64/32 200000h to 20FFFFh 100000h to 107FFFh		SA31	0	1	1	1	1	1	Χ	X	Χ	Χ	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFFh
		SA32	1	0	0	0	0	0	Х	Х	Χ	Х	64/32	200000h to 20FFFFh	100000h to 107FFFh

					Sec	tor	addı	ress	;			Sector		
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
	101	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	i - '	Addices range	Addices range
	SA33	1	0	0	0	0	1	Х	Х	Х	Χ	64/32	210000h to 21FFFFh	108000h to 10FFFFh
	SA34	1	0	0	0	1	0	Х	Х	Х	Χ	64/32	220000h to 22FFFFh	110000h to 117FFFh
	SA35	1	0	0	0	1	1	Х	Х	Х	Х	64/32	230000h to 23FFFFh	118000h to 11FFFFh
	SA36	1	0	0	1	0	0	Х	Х	Х	Χ	64/32	240000h to 24FFFFh	120000h to 127FFFh
	SA37	1	0	0	1	0	1	Х	Х	Х	Χ	64/32	250000h to 25FFFFh	128000h to 12FFFFh
	SA38	1	0	0	1	1	0	Х	Х	Х	Х	64/32	260000h to 26FFFFh	130000h to 137FFFh
	SA39	1	0	0	1	1	1	Х	Х	Х	Χ	64/32	270000h to 27FFFFh	138000h to 13FFFFh
	SA40	1	0	1	0	0	0	Х	Х	Х	Χ	64/32	280000h to 28FFFFh	140000h to 147FFFh
	SA41	1	0	1	0	0	1	Х	Х	Х	Х	64/32	290000h to 29FFFFh	148000h to 14FFFFh
	SA42	1	0	1	0	1	0	Х	Х	Х	Χ	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh
	SA43	1	0	1	0	1	1	Х	Х	Х	Χ	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh
Bank 2	SA44	1	0	1	1	0	0	Х	Х	Х	Χ	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
_	SA45	1	0	1	1	0	1	Х	Х	Х	Χ	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA46	1	0	1	1	1	0	Х	Х	Х	Χ	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA47	1	0	1	1	1	1	Х	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
	SA48	1	1	0	0	0	0	Х	Х	Х	Χ	64/32	300000h to 30FFFFh	180000h to 187FFFh
	SA49	1	1	0	0	0	1	Х	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA50	1	1	0	0	1	0	Х	Х	Х	Χ	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA51	1	1	0	0	1	1	Х	Х	Х	Χ	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA52	1	1	0	1	0	0	Х	Х	Х	Χ	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA53	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
	SA54	1	1	0	1	1	0	Х	Х	Х	Χ	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
	SA55	1	1	0	1	1	1	Х	Х	Х	Χ	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA56	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
	SA57	1	1	1	0	0	1	Х	Х	Х	Χ	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA58	1	1	1	0	1	0	Х	Х	Х	Χ	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA59	1	1	1	0	1	1	Х	Х	Х	Х	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA60	1	1	1	1	0	0	Х	Х	Х	Х	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
Bank 1	SA61	1	1	1	1	0	1	Х	Х	Х	Х	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA62	1	1	1	1	1	0	Χ	Х	Х	Χ	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000h to 3F1FFFh	1F8000h to 1F8FFFh
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000h to 3F3FFFh	1F9000h to 1F9FFFh
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000h to 3F5FFFh	1FA000h to 1FAFFFh
	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000h to 3F7FFFh	1FB000h to 1FBFFFh
		•	•	•	•	•	•	•	•	•		•		(Continued)

(Continued)

					Sec	tor a	addı	ress	;			Sector		
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	3	
	SA67	1	1	1	1	1	1	1	0	0	Х	8/4	3F8000h to 3F9FFFh	1FC000h to 1FCFFFh
Bank	SA68	1	1	1	1	1	1	1	0	1	Х	8/4	3FA000h to 3FBFFFh	1FD000h to 1FDFFFh
1	SA69	1	1	1	1	1	1	1	1	0	Х	8/4	3FC000h to 3FDFFFh	1FE000h to 1FEFFFh
	SA70	1	1	1	1	1	1	1	1	1	Х	8/4	3FE000h to 3FFFFFh	1FF000h to 1FFFFFh

Note : The address range is A_{20} : A_{-1} if in byte mode $\overline{(BYTE}=V_{IL})$. The address range is A_{20} : A_0 if in word mode $\overline{(BYTE}=V_{IH})$.

Sector Address Table (MBM29DL322BE)

	_				Sec	tor	addı	ress	;			Sector		
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	g	3
	SA70	1	1	1	1	1	1	Х	Х	Х	Χ	64/32	3F0000h to 3FFFFFh	1F8000h to 1FFFFFh
	SA69	1	1	1	1	1	0	Х	Х	Х	Х	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA68	1	1	1	1	0	1	Х	Х	Х	Χ	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA67	1	1	1	1	0	0	Х	Х	Х	Х	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
	SA66	1	1	1	0	1	1	Х	Х	Х	Х	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA65	1	1	1	0	1	0	Х	Х	Х	Х	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA64	1	1	1	0	0	1	Х	Х	Х	Х	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA63	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
	SA62	1	1	0	1	1	1	Х	Х	Х	Х	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA61	1	1	0	1	1	0	Х	Х	Х	Х	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
Bank	SA60	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
2	SA59	1	1	0	1	0	0	Х	Х	Х	Х	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA58	1	1	0	0	1	1	Х	Х	Х	Х	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA57	1	1	0	0	1	0	Х	Х	Х	Х	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA56	1	1	0	0	0	1	Х	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA55	1	1	0	0	0	0	Х	Х	Х	Х	64/32	300000h to 30FFFFh	180000h to 187FFFh
	SA54	1	0	1	1	1	1	Х	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
	SA53	1	0	1	1	1	0	Х	Х	Х	Х	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA52	1	0	1	1	0	1	Х	Х	Х	Х	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA51	1	0	1	1	0	0	Χ	Х	Х	Χ	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
	SA50	1	0	1	0	1	1	Х	Х	Х	Χ	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh
	SA49	1	0	1	0	1	0	Χ	Х	Х	Χ	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh

SAME No						Sec	tor	addı	ress	;			Sector		
SA48	Bank			Baı	nk a	ddr	ess							(×8)	(×16)
SA47		101	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11		Addices range	Address fallge
SA46		SA48	1	0	1	0	0	1	Х	Х	Х	Х	64/32	290000h to 29FFFFh	148000h to 14FFFFh
SA45		SA47	1	0	1	0	0	0	Х	Х	Х	Х	64/32	280000h to 28FFFFh	140000h to 147FFFh
SA44		SA46	1	0	0	1	1	1	Х	Х	Х	Х	64/32	270000h to 27FFFFh	138000h to 13FFFFh
SA43		SA45	1	0	0	1	1	0	Х	Х	Х	Х	64/32	260000h to 26FFFFh	130000h to 137FFFh
SA42		SA44	1	0	0	1	0	1	Х	Х	Х	Х	64/32	250000h to 25FFFFh	128000h to 12FFFFh
SA41		SA43	1	0	0	1	0	0	Х	Х	Х	Х	64/32	240000h to 24FFFFh	120000h to 127FFFh
SA40		SA42	1	0	0	0	1	1	Х	Х	Х	Х	64/32	230000h to 23FFFFh	118000h to 11FFFFh
SA39		SA41	1	0	0	0	1	0	Х	Х	Х	Х	64/32	220000h to 22FFFFh	110000h to 117FFFh
SA38		SA40	1	0	0	0	0	1	Х	Х	Х	Х	64/32	210000h to 21FFFFh	108000h to 10FFFFh
SA37 0 1 1 1 1 1 0 X X X X 64/32 1E0000h to 1EFFFFh 0F0000h to 0F7F SA36 0 1 1 1 1 0 0 1 X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0EFF SA35 0 1 1 1 0 0 1 X X X X 64/32 1D0000h to 1DFFFFh 0E8000h to 0EFF SA34 0 1 1 0 1 1 X X X X 64/32 1E0000h to 1EFFFFh 0E0000h to 0EFF SA33 0 1 1 0 1 0 1 X X X X 64/32 1B0000h to 1BFFFFh 0D0000h to 0DFF SA33 0 1 1 0 0 1 X X X X 64/32 1A0000h to 1AFFFFh 0D0000h to 0DFF SA31 0 1 1 0 0 0 1 X X X X 64/32 190000h to 1FFFFh 0C8000h to 0CFF SA31 0 1 1 0 0 0 X X X X X 64/32 180000h to 1FFFFh 0C8000h to 0CFF SA39 0 1 0 1 1 1 X X X X X 64/32 180000h to 1FFFFh 0E8000h to 0EFF SA29 0 1 0 1 1 1 X X X X X 64/32 170000h to 1FFFFh 0E8000h to 0EFF SA28 0 1 0 1 1 1 X X X X X 64/32 150000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 1 0 1 X X X X X 64/32 150000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 0 1 1 X X X X X 64/32 130000h to 1FFFFh 0E8000h to 0EFF SA25 0 1 0 0 0 1 X X X X X 64/32 130000h to 1FFFFh 0E8000h to 0EFF SA25 0 1 0 0 0 1 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 0 0 1 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 0 0 1 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 0 0 1 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 0 0 0 1 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA27 0 1 1 0 1 0 0 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 1 1 0 0 0 0 X X X X X 64/32 120000h to 1FFFFh 0E8000h to 0EFF SA26 0 0 1 1 1 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA26 0 0 1 1 1 0 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA18 0 0 1 1 1 0 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA18 0 0 1 0 1 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA18 0 0 1 0 1 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA18 0 0 1 0 1 0 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA17 0 0 1 0 1 0 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA17 0 0 1 0 1 0 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA17 0 0 1 0 1 0 1 X X X X X 64/32 0E0000h to 0EFFFFh 0E8000h to 0EFF SA17 0 0 1 0		SA39	1	0	0	0	0	0	Х	Х	Х	Х	64/32	200000h to 20FFFFh	100000h to 107FFFh
SA36		SA38	0	1	1	1	1	1	Х	Х	Х	Х	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFFh
SA35		SA37	0	1	1	1	1	0	Х	Х	Х	Х	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFFh
SA34 0		SA36	0	1	1	1	0	1	Х	Х	Х	Х	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh
Bank SA33 0 1 1 0 1 0 X X X X 64/32 1A0000h to 1AFFFFh 0D0000h to 0D7F SA32 0 1 1 0 0 1 X X X 64/32 190000h to 18FFFFh 0C8000h to 0CFF SA31 0 1 1 0 0 X X X 64/32 180000h to 18FFFFh 0C0000h to 0CFF SA30 0 1 0 1 1 1 X X X 64/32 170000h to 18FFFFh 0C0000h to 0BFF SA29 0 1 0 1 X X X 64/32 160000h to 18FFFFh 0B0000h to 0BFF SA28 0 1 0 1 X X X 64/32 150000h to 18FFFFh 0A8000h to 0AFF SA26 0 1 0 1 1 X X X 64/32 120000h to 13FFFFh 08000h to 08FF		SA35	0	1	1	1	0	0	Х	Х	Х	Х	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFh
Bank SA32 0 1 1 0 0 1 X X X X 64/32 190000h to 19FFFFh 0C8000h to 0CFF SA31 0 1 1 0 0 0 X X X 64/32 180000h to 18FFFFh 0C0000h to 0CFF SA30 0 1 0 1 1 1 X X X 64/32 170000h to 17FFFFh 0B8000h to 0BFF SA29 0 1 0 1 X X X 64/32 160000h to 16FFFFh 0B0000h to 0BFF SA28 0 1 0 1 X X X 64/32 150000h to 15FFFFh 0A8000h to 0AFF SA26 0 1 0 0 X X X 64/32 130000h to 13FFFFh 0A8000h to 0AFF SA25 0 1 0 0 X X X 64/32 120000h to 12FFFFh 098000h to 08FF SA23 </td <td></td> <td>SA34</td> <td>0</td> <td>1</td> <td>1</td> <td>0</td> <td>1</td> <td>1</td> <td>Х</td> <td>Х</td> <td>Х</td> <td>Х</td> <td>64/32</td> <td>1B0000h to 1BFFFFh</td> <td>0D8000h to 0DFFFFh</td>		SA34	0	1	1	0	1	1	Х	Х	Х	Х	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh
SA31 0 1 1 0 0 0 X X X X 64/32 180000h to 18FFFFh 0C0000h to 0C7F SA30 0 1 0 1 1 1 X X X X 64/32 170000h to 17FFFFh 0B8000h to 0BFF SA29 0 1 0 1 1 0 1 X X X X 64/32 160000h to 16FFFFh 0B0000h to 0B7F SA28 0 1 0 1 0 1 0 X X X X 64/32 150000h to 15FFFFh 0A8000h to 0A7F SA26 0 1 0 1 0 1 X X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7F SA26 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFFh 0A0000h to 0A7F SA25 0 1 0 0 1 1 X X X X 64/32 120000h to 13FFFFh 098000h to 09FF SA25 0 1 0 0 0 1 X X X X 64/32 120000h to 12FFFFh 098000h to 09FF SA24 0 1 0 0 0 1 X X X X 64/32 120000h to 12FFFFh 088000h to 08FF SA23 0 1 0 0 0 0 X X X X X 64/32 110000h to 17FFFFh 088000h to 08FF SA21 0 0 1 1 1 X X X X 64/32 100000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 1 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0C0000h to 0FFFFFh 078000h to 07FF SA20 0 0 1 1 0 0 1 X X X X X 64/32 0C0000h to 0FFFFFh 068000h to 0FFF SA19 0 0 1 1 0 0 1 X X X X X 64/32 0C0000h to 0FFFFFh 068000h to 0FFF SA18 0 0 1 0 1 X X X X X 64/32 0C0000h to 0FFFFFh 058000h to 0FFF SA18 0 0 1 0 1 0 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFF SA16 0 0 1 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFF SA16 0 0 1 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFF SA16 0 0 1 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 0 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 0FFFF SA16 0 0 1 0 0 1 X X X X X 64/32 0B0000h to 0FFFFFH 058000h		SA33	0	1	1	0	1	0	Х	Х	Х	Х	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh
SA30 0 1 0 1 1 1 X X X X 64/32 170000h to 17FFFFh 0B8000h to 0BFF SA29 0 1 0 1 1 0 X X X X X 64/32 160000h to 16FFFFh 0B0000h to 0BFF SA28 0 1 0 1 0 1 X X X X X 64/32 150000h to 15FFFFh 0A8000h to 0AFF SA27 0 1 0 1 0 0 X X X X X 64/32 140000h to 14FFFFh 0A0000h to 0AFF SA26 0 1 0 0 1 1 X X X X X 64/32 130000h to 13FFFFh 098000h to 09FF SA25 0 1 0 0 1 1 X X X X X 64/32 120000h to 12FFFFh 098000h to 09FF SA24 0 1 0 0 0 1 X X X X X 64/32 110000h to 11FFFFh 088000h to 08FF SA23 0 1 0 0 0 0 X X X X X 64/32 110000h to 11FFFFh 088000h to 08FF SA23 0 1 0 0 0 0 X X X X X 64/32 100000h to 10FFFFh 080000h to 08FF SA22 0 0 1 1 1 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA20 0 0 1 1 1 0 X X X X X 64/32 0F0000h to 0FFFFFh 068000h to 06FF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0FFFFFh 068000h to 06FF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0FFFFFh 058000h to 05FF SA18 0 0 1 0 1 0 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FF SA16 0 0 1 0 1 0 X X X X X 64/32 090000h to 0BFFFFh 050000h to 05FF SA16 0 0 1 0 0 1 X X X X X 64/32 090000h to 0BFFFFh 050000h to 05FF		SA32	0	1	1	0	0	1	Х	Х	Х	Х	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh
SA29 0 1 0 1 1 0 X	2	SA31	0	1	1	0	0	0	Х	Х	Х	Х	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh
SA28 0 1 0 1 0 1 X X X X 64/32 150000h to 15FFFFh 0A8000h to 0AFF SA27 0 1 0 1 0 0 X X X X X 64/32 140000h to 14FFFFh 0A0000h to 0AFF SA26 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFFh 098000h to 09FF SA25 0 1 0 0 1 0 X X X X X 64/32 120000h to 12FFFFh 090000h to 09FF SA24 0 1 0 0 0 1 X X X X X 64/32 120000h to 12FFFFh 090000h to 09FF SA24 0 1 0 0 0 0 X X X X X 64/32 110000h to 11FFFFh 088000h to 08FF SA23 0 1 0 0 0 0 X X X X X 64/32 100000h to 10FFFFh 080000h to 08FF SA22 0 0 1 1 1 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA20 0 0 1 1 0 1 X X X X X 64/32 0E0000h to 0EFFFFh 070000h to 07FF SA18 0 0 1 0 1 X X X X X 64/32 0C0000h to 0FFFFFh 068000h to 06FF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FF SA16 0 0 1 0 1 X X X X X 64/32 090000h to 0AFFFFh 050000h to 05FF SA16 0 0 1 0 1 X X X X X 64/32 090000h to 0AFFFFh 050000h to 05FF		SA30	0	1	0	1	1	1	Х	Х	Х	Х	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh
SA27 0 1 0 1 0 0 X X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7F SA26 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFFh 098000h to 09FF SA25 0 1 0 0 1 0 X X X X 64/32 120000h to 12FFFFh 090000h to 097F SA24 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFFh 088000h to 08FF SA23 0 1 0 0 0 0 X X X X X 64/32 110000h to 10FFFFh 088000h to 08FF SA22 0 0 1 1 1 1 X X X X X 64/32 100000h to 10FFFFh 080000h to 08FF SA22 0 0 1 1 1 1 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0E0000h to 0FFFFFh 070000h to 07FF SA20 0 0 1 1 0 1 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 06FF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0FFFFFh 068000h to 06FF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFFh 050000h to 05FF SA16 0 0 1 0 1 X X X X X X 64/32 0A0000h to 0AFFFFh 050000h to 05FF SA16 0 0 1 0 1 X X X X X X 64/32 0A0000h to 0AFFFFh 050000h to 05FF		SA29	0	1	0	1	1	0	Х	Х	Х	Х	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh
SA26		SA28	0	1	0	1	0	1	Х	Х	Х	Х	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh
SA25		SA27	0	1	0	1	0	0	Х	Х	Х	Χ	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh
SA24 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFh 088000h to 08FF SA23 0 1 0 0 0 X X X X X 64/32 100000h to 10FFFh 080000h to 087F SA22 0 0 1 1 1 1 X X X X X 64/32 0F0000h to 0FFFFh 078000h to 07FF SA21 0 0 1 1 1 0 X X X X X 64/32 0E0000h to 0EFFFh 070000h to 07FF SA20 0 0 1 1 0 1 X X X X X 64/32 0D0000h to 0DFFFFh 068000h to 06FF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0CFFFh 060000h to 06FF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFFh 050000h to 05FF SA16 0 0 1 0 1 0 X X X X X 64/32 090000h to 0AFFFFh 048000h to 04FF		SA26	0	1	0	0	1	1	Х	Х	Х	Χ	64/32	130000h to 13FFFFh	098000h to 09FFFFh
SA23		SA25	0	1	0	0	1	0	Х	Х	Х	Х	64/32	120000h to 12FFFFh	090000h to 097FFFh
SA22		SA24	0	1	0	0	0	1	Х	Х	Х	Х	64/32	110000h to 11FFFFh	088000h to 08FFFFh
SA21 0 0 1 1 1 0 X X X X 64/32 0E0000h to 0EFFFh 070000h to 077F SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0CFFFh 060000h to 067F SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFh 050000h to 057F SA16 0 0 1 0 0 1 X X X X X 64/32 090000h to 09FFFFh 048000h to 04FF		SA23	0	1	0	0	0	0	Х	Х	Х	Χ	64/32	100000h to 10FFFFh	080000h to 087FFFh
SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FF SA19 0 0 1 1 0 0 X X X X 64/32 0C0000h to 0CFFFh 060000h to 067F SA18 0 0 1 0 1 1 X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FF SA17 0 0 1 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057F SA16 0 0 1 0 0 1 X X X X 64/32 090000h to 09FFFh 048000h to 04FF		SA22	0	0	1	1	1	1	Х	Х	Х	Х	64/32	0F0000h to 0FFFFh	078000h to 07FFFFh
SA19 0 0 1 1 0 0 X		SA21	0	0	1	1	1	0	Х	Х	Х	Χ	64/32	0E0000h to 0EFFFFh	070000h to 077FFFh
SA18 0 0 1 0 1 1 X		SA20	0	0	1	1	0	1	Х	Х	Х	Х	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh
SA17 0 0 1 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057F SA16 0 0 1 0 0 1 X X X X 64/32 090000h to 09FFFh 048000h to 04FF		SA19	0	0	1	1	0	0	Х	Х	Χ	Х	64/32	0C0000h to 0CFFFFh	060000h to 067FFFh
SA16 0 0 1 0 0 1 X X X X 64/32 090000h to 09FFFh 048000h to 04FF		SA18	0	0	1	0	1	1	Χ	Х	Χ	Χ	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh
		SA17	0	0	1	0	1	0	Х	Х	Х	Χ	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh
		SA16	0	0	1	0	0	1	Х	Х	Х	Χ	64/32	090000h to 09FFFFh	048000h to 04FFFFh
SA15 0 0 1 0 0 0 X X X X 64/32 080000h to 08FFFFh 040000h to 047F		SA15	0	0	1	0	0	0	Χ	Х	Х	Χ	64/32	080000h to 08FFFFh	040000h to 047FFFh

(Continued)

					Sec	tor	addı	ress	;			Sector	(2)	(10)
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)		- rauncee range
	SA14	0	0	0	1	1	1	Х	Х	Х	Х	64/32	070000h to 07FFFFh	038000h to 03FFFFh
	SA13	0	0	0	1	1	0	Х	Х	Х	Х	64/32	060000h to 06FFFFh	030000h to 037FFFh
	SA12	0	0	0	1	0	1	Х	Х	Х	Х	64/32	050000h to 05FFFFh	028000h to 02FFFFh
	SA11	0	0	0	1	0	0	Х	Х	Х	Х	64/32	040000h to 04FFFFh	020000h to 027FFFh
	SA10	0	0	0	0	1	1	Х	Х	Х	Х	64/32	030000h to 03FFFFh	018000h to 01FFFFh
	SA9	0	0	0	0	1	0	Х	Х	Х	Х	64/32	020000h to 02FFFFh	010000h to 017FFFh
	SA8	0	0	0	0	0	1	Х	Х	Х	Х	64/32	010000h to 01FFFFh	008000h to 00FFFFh
Bank 1	SA7	0	0	0	0	0	0	1	1	1	Х	8/4	00E000h to 00FFFFh	007000h to 007FFFh
	SA6	0	0	0	0	0	0	1	1	0	Х	8/4	00C000h to 00DFFFh	006000h to 006FFFh
	SA5	0	0	0	0	0	0	1	0	1	Х	8/4	00A000h to 00BFFFh	005000h to 005FFFh
	SA4	0	0	0	0	0	0	1	0	0	Х	8/4	008000h to 009FFFh	004000h to 004FFFh
	SA3	0	0	0	0	0	0	0	1	1	Х	8/4	006000h to 007FFFh	003000h to 003FFFh
	SA2	0	0	0	0	0	0	0	1	0	Х	8/4	004000h to 005FFFh	002000h to 002FFFh
	SA1	0	0	0	0	0	0	0	0	1	Х	8/4	002000h to 003FFFh	001000h to 001FFFh
	SA0	0	0	0	0	0	0	0	0	0	Х	8/4	000000h to 001FFFh	000000h to 000FFFh

Note : The address range is A_{20} : $A_{\text{--}1}$ if in byte mode $\left(\overline{\text{BYTE}} = V_{\text{IL}}\right)$.

The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Sector Address Table (MBM29DL323TE)

					Sec	tor a	addı	ress	;			Sector		
Bank	Sec-		Baı		ddr							size	(×8)	(×16)
	tor	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	(Kbytes/ Kwords)	Address range	Address range
	SA0	0	0	0	0	0	0	Х	Х	Х	Χ	64/32	000000h to 00FFFFh	000000h to 007FFFh
	SA1	0	0	0	0	0	1	Х	Х	Х	Χ	64/32	010000h to 01FFFFh	008000h to 00FFFFh
	SA2	0	0	0	0	1	0	Х	Х	Х	Χ	64/32	020000h to 02FFFFh	010000h to 017FFFh
	SA3	0	0	0	0	1	1	Х	Х	Х	Χ	64/32	030000h to 03FFFFh	018000h to 01FFFFh
	SA4	0	0	0	1	0	0	Х	Х	Х	Χ	64/32	040000h to 04FFFFh	020000h to 027FFFh
	SA5	0	0	0	1	0	1	Х	Х	Х	Χ	64/32	050000h to 05FFFFh	028000h to 02FFFFh
	SA6	0	0	0	1	1	0	Х	Х	Х	Χ	64/32	060000h to 06FFFFh	030000h to 037FFFh
	SA7	0	0	0	1	1	1	Х	Х	Х	Χ	64/32	070000h to 07FFFFh	038000h to 03FFFFh
	SA8	0	0	1	0	0	0	Х	Х	Х	Χ	64/32	080000h to 08FFFFh	040000h to 047FFFh
	SA9	0	0	1	0	0	1	Х	Х	Х	Χ	64/32	090000h to 09FFFFh	048000h to 04FFFFh
	SA10	0	0	1	0	1	0	Х	Х	Х	Χ	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh
	SA11	0	0	1	0	1	1	Х	Х	Χ	Χ	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh
	SA12	0	0	1	1	0	0	Х	Х	Х	Χ	64/32	0C0000h to 0CFFFh	060000h to 067FFFh
	SA13	0	0	1	1	0	1	Х	Х	Х	Χ	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh
	SA14	0	0	1	1	1	0	Х	Х	Х	Χ	64/32	0E0000h to 0EFFFFh	070000h to 077FFFh
Donle	SA15	0	0	1	1	1	1	Х	Х	Χ	Χ	64/32	0F0000h to 0FFFFh	078000h to 07FFFFh
Bank 2	SA16	0	1	0	0	0	0	Х	Х	Х	Χ	64/32	100000h to 10FFFFh	080000h to 087FFFh
	SA17	0	1	0	0	0	1	Х	Х	Х	Χ	64/32	110000h to 11FFFFh	088000h to 08FFFFh
	SA18	0	1	0	0	1	0	Х	Х	Χ	Χ	64/32	120000h to 12FFFFh	090000h to 097FFFh
	SA19	0	1	0	0	1	1	Х	Х	Х	Χ	64/32	130000h to 13FFFFh	098000h to 09FFFFh
	SA20	0	1	0	1	0	0	Х	Х	Х	Χ	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh
	SA21	0	1	0	1	0	1	Х	Х	Х	Χ	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh
	SA22	0	1	0	1	1	0	Х	Х	Х	Χ	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh
	SA23	0	1	0	1	1	1	Х	Х	Х	Χ	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh
	SA24	0	1	1	0	0	0	Х	Х	Х	X	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh
	SA25	0	1	1	0	0	1	Х	Х	Х	X	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh
	SA26	0	1	1	0	1	0	Х	Х	Χ	X	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh
	SA27	0	1	1	0	1	1	Х	Х	Х	Х	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh
	SA28	0	1	1	1	0	0	Χ	Х	Х	Χ	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFh
	SA29	0	1	1	1	0	1	Χ	Х	Х	Χ	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh
	SA30	0	1	1	1	1	0	Χ	Х	Х	Χ	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFh
	SA31	0	1	1	1	1	1	Χ	Х	Х	Χ	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFh
	SA32	1	0	0	0	0	0	Χ	Х	Х	Χ	64/32	200000h to 20FFFFh	100000h to 107FFFh

					Sec	tor	add	ress	3			Sector		
Bank	Sec- tor		Bai	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
	101	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	/taarooo rango	/tuarooo rungo
	SA33	1	0	0	0	0	1	Х	Х	Х	Х	64/32	210000h to 21FFFFh	108000h to 10FFFFh
	SA34	1	0	0	0	1	0	Х	Х	Х	Х	64/32	220000h to 22FFFFh	110000h to 117FFFh
	SA35	1	0	0	0	1	1	Х	Х	Х	Х	64/32	230000h to 23FFFFh	118000h to 11FFFFh
	SA36	1	0	0	1	0	0	Х	Х	Х	Х	64/32	240000h to 24FFFFh	120000h to 127FFFh
	SA37	1	0	0	1	0	1	Х	Х	Х	Х	64/32	250000h to 25FFFFh	128000h to 12FFFFh
	SA38	1	0	0	1	1	0	Х	Х	Х	Х	64/32	260000h to 26FFFFh	130000h to 137FFFh
	SA39	1	0	0	1	1	1	Х	Х	Х	Х	64/32	270000h to 27FFFFh	138000h to 13FFFFh
Bank 2	SA40	1	0	1	0	0	0	Х	Х	Х	Х	64/32	280000h to 28FFFFh	140000h to 147FFFh
_	SA41	1	0	1	0	0	1	Х	Х	Х	Х	64/32	290000h to 29FFFFh	148000h to 14FFFFh
	SA42	1	0	1	0	1	0	Х	Х	Х	Х	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh
	SA43	1	0	1	0	1	1	Х	Х	Х	Х	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh
	SA44	1	0	1	1	0	0	Х	Х	Х	Х	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
	SA45	1	0	1	1	0	1	Х	Х	Х	Х	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA46	1	0	1	1	1	0	Х	Х	Х	Х	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA47	1	0	1	1	1	1	Х	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
	SA48	1	1	0	0	0	0	Х	Х	Х	Х	64/32	300000h to 30FFFFh	180000h to 187FFFh
	SA49	1	1	0	0	0	1	Х	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA50	1	1	0	0	1	0	Х	Х	Х	Х	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA51	1	1	0	0	1	1	Х	Х	Х	Х	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA52	1	1	0	1	0	0	Х	Х	Х	Х	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA53	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
	SA54	1	1	0	1	1	0	Х	Х	Х	Х	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
	SA55	1	1	0	1	1	1	Х	Х	Х	Х	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA56	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
Bank 1	SA57	1	1	1	0	0	1	Х	Х	Х	Х	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA58	1	1	1	0	1	0	Х	Х	Х	Х	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA59	1	1	1	0	1	1	Х	Х	Х	Х	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA60	1	1	1	1	0	0	Х	Х	Х	Х	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
	SA61	1	1	1	1	0	1	Х	Х	Х	Х	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA62	1	1	1	1	1	0	Х	Х	Х	Х	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000h to 3F1FFFh	1F8000h to 1F8FFFh
	SA64	1	1	1	1	1	1	0	0	1	Χ	8/4	3F2000h to 3F3FFFh	1F9000h to 1F9FFFh
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000h to 3F5FFFh	1FA000h to 1FAFFFh
	SA66	1	1	1	1	1	1	0	1	1	Χ	8/4	3F6000h to 3F7FFFh	1FB000h to 1FBFFFh
				•						•		•		(Continued

(Continued)

	_				Sec	tor a	addı	ress	;			Sector	, -,	
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)		- man occ minge
	SA67	1	1	1	1	1	1	1	0	0	Х	8/4	3F8000h to 3F9FFFh	1FC000h to 1FCFFFh
Bank	SA68	1	1	1	1	1	1	1	0	1	Х	8/4	3FA000h to 3FBFFFh	1FD000h to 1FDFFFh
1	SA69	1	1	1	1	1	1	1	1	0	Х	8/4	3FC000h to 3FDFFFh	1FE000h to 1FEFFFh
	SA70	1	1	1	1	1	1	1	1	1	Х	8/4	3FE000h to 3FFFFFh	1FF000h to 1FFFFFh

Note : The address range is A_{20} : A_{-1} if in byte mode $\overline{(BYTE}=V_{IL})$. The address range is A_{20} : A_0 if in word mode $\overline{(BYTE}=V_{IH})$.

Sector Address Table (MBM29DL323BE)

					Sec	tor a	addı	ress	;			Sector	(->	
Bank	Sec- tor		Bar	nk a	ddre	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	1	g	3
	SA70	1	1	1	1	1	1	Х	Х	Х	Х	64/32	3F0000h to 3FFFFFh	1F8000h to 1FFFFFh
	SA69	1	1	1	1	1	0	Х	Х	Х	Х	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA68	1	1	1	1	0	1	Х	Х	Х	Х	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA67	1	1	1	1	0	0	Х	Х	Х	Х	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
	SA66	1	1	1	0	1	1	Х	Х	Х	Х	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA65	1	1	1	0	1	0	Х	Х	Х	Х	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA64	1	1	1	0	0	1	Х	Х	Х	Х	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA63	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
	SA62	1	1	0	1	1	1	Х	Х	Х	Х	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA61	1	1	0	1	1	0	Х	Х	Х	Х	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
Bank	SA60	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
2	SA59	1	1	0	1	0	0	Х	Х	Х	Х	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA58	1	1	0	0	1	1	Х	Х	Х	Х	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA57	1	1	0	0	1	0	Х	Х	Х	Х	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA56	1	1	0	0	0	1	Х	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA55	1	1	0	0	0	0	Х	Х	Х	Х	64/32	300000h to 30FFFFh	180000h to 187FFFh
	SA54	1	0	1	1	1	1	Х	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
	SA53	1	0	1	1	1	0	Х	Х	Х	Х	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA52	1	0	1	1	0	1	Х	Х	Х	Х	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA51	1	0	1	1	0	0	Х	Х	Х	Х	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
	SA50	1	0	1	0	1	1	Х	Х	Х	Х	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh
	SA49	1	0	1	0	1	0	Χ	Х	Х	Χ	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh

Bank	Sec-				CCC	נטו נ	addı	622	•			Sector		
	tor		Bar	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
	101	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	Address fallge	Address fallge
	SA48	1	0	1	0	0	1	Х	Х	Х	Χ	64/32	290000h to 29FFFFh	148000h to 14FFFFh
	SA47	1	0	1	0	0	0	Х	Х	Х	Χ	64/32	280000h to 28FFFFh	140000h to 147FFFh
	SA46	1	0	0	1	1	1	Х	Х	Х	Χ	64/32	270000h to 27FFFFh	138000h to 13FFFFh
	SA45	1	0	0	1	1	0	Х	Х	Х	Χ	64/32	260000h to 26FFFFh	130000h to 137FFFh
	SA44	1	0	0	1	0	1	Х	Х	Х	Χ	64/32	250000h to 25FFFFh	128000h to 12FFFFh
	SA43	1	0	0	1	0	0	Х	Х	Х	Χ	64/32	240000h to 24FFFFh	120000h to 127FFFh
	SA42	1	0	0	0	1	1	Х	Х	Х	Χ	64/32	230000h to 23FFFFh	118000h to 11FFFFh
	SA41	1	0	0	0	1	0	Χ	Х	Х	Χ	64/32	220000h to 22FFFFh	110000h to 117FFFh
	SA40	1	0	0	0	0	1	Х	Х	Х	Х	64/32	210000h to 21FFFFh	108000h to 10FFFFh
	SA39	1	0	0	0	0	0	Χ	Х	Х	Χ	64/32	200000h to 20FFFFh	100000h to 107FFFh
	SA38	0	1	1	1	1	1	Χ	Х	Х	Χ	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFh
	SA37	0	1	1	1	1	0	Х	Х	Х	Х	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFFh
Bank	SA36	0	1	1	1	0	1	Х	Х	Х	Χ	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh
2	SA35	0	1	1	1	0	0	Χ	Х	Х	Χ	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFFh
	SA34	0	1	1	0	1	1	Х	Х	Х	Χ	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh
	SA33	0	1	1	0	1	0	Х	Х	Х	Х	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh
	SA32	0	1	1	0	0	1	Х	Х	Х	Χ	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh
	SA31	0	1	1	0	0	0	Χ	Х	Х	Χ	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh
	SA30	0	1	0	1	1	1	Х	Х	Х	Х	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh
	SA29	0	1	0	1	1	0	Х	Х	Х	Χ	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh
	SA28	0	1	0	1	0	1	Х	Х	Х	Χ	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh
	SA27	0	1	0	1	0	0	Χ	Х	Х	Χ	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh
	SA26	0	1	0	0	1	1	Х	Х	Х	Χ	64/32	130000h to 13FFFFh	098000h to 09FFFFh
	SA25	0	1	0	0	1	0	Х	Х	Х	Χ	64/32	120000h to 12FFFFh	090000h to 097FFFh
	SA24	0	1	0	0	0	1	Х	Х	Х	Х	64/32	110000h to 11FFFFh	088000h to 08FFFFh
	SA23	0	1	0	0	0	0	Χ	Х	Х	Χ	64/32	100000h to 10FFFFh	080000h to 087FFFh
	SA22	0	0	1	1	1	1	Χ	Х	Х	Χ	64/32	0F0000h to 0FFFFFh	078000h to 07FFFFh
	SA21	0	0	1	1	1	0	Χ	Х	Х	Χ	64/32	0E0000h to 0EFFFFh	070000h to 077FFFh
	SA20	0	0	1	1	0	1	Х	Х	Х	Χ	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh
Dank	SA19	0	0	1	1	0	0	Χ	Χ	Χ	Χ	64/32	0C0000h to 0CFFFFh	060000h to 067FFFh
1	SA18	0	0	1	0	1	1	Χ	Χ	Х	Χ	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh
	SA17	0	0	1	0	1	0	Χ	Х	Х	Χ	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh
	SA16	0	0	1	0	0	1	Χ	Χ	Χ	Χ	64/32	090000h to 09FFFFh	048000h to 04FFFFh
	SA15	0	0	1	0	0	0	Χ	Χ	Χ	Χ	64/32	080000h to 08FFFFh	040000h to 047FFFh

(Continued)

	nk Sec-				Sec	tor	addı	ress	;			Sector		
Bank			Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	3	3
	SA14	0	0	0	1	1	1	Х	Х	Х	Х	64/32	070000h to 07FFFFh	038000h to 03FFFFh
	SA13	0	0	0	1	1	0	Х	Х	Х	Х	64/32	060000h to 06FFFFh	030000h to 037FFFh
	SA12	0	0	0	1	0	1	Х	Х	Х	Х	64/32	050000h to 05FFFFh	028000h to 02FFFFh
	SA11	0	0	0	1	0	0	Х	Х	Х	Х	64/32	040000h to 04FFFFh	020000h to 027FFFh
	SA10	0	0	0	0	1	1	Х	Х	Х	Х	64/32	030000h to 03FFFFh	018000h to 01FFFFh
	SA9	0	0	0	0	1	0	Х	Х	Х	Х	64/32	020000h to 02FFFFh	010000h to 017FFFh
	SA8	0	0	0	0	0	1	Х	Х	Х	Х	64/32	010000h to 01FFFFh	008000h to 00FFFFh
Bank 1	SA7	0	0	0	0	0	0	1	1	1	Х	8/4	00E000h to 00FFFFh	007000h to 007FFFh
	SA6	0	0	0	0	0	0	1	1	0	Х	8/4	00C000h to 00DFFFh	006000h to 006FFFh
	SA5	0	0	0	0	0	0	1	0	1	Х	8/4	00A000h to 00BFFFh	005000h to 005FFFh
	SA4	0	0	0	0	0	0	1	0	0	Х	8/4	008000h to 009FFFh	004000h to 004FFFh
	SA3	0	0	0	0	0	0	0	1	1	Х	8/4	006000h to 007FFFh	003000h to 003FFFh
	SA2	0	0	0	0	0	0	0	1	0	Х	8/4	004000h to 005FFFh	002000h to 002FFFh
	SA1	0	0	0	0	0	0	0	0	1	Х	8/4	002000h to 003FFFh	001000h to 001FFFh
	SA0	0	0	0	0	0	0	0	0	0	X	8/4	000000h to 001FFFh	000000h to 000FFFh

Note : The address range is A_{20} : $A_{^{-1}}$ if in byte mode $(\overline{\overline{BYTE}}=V_{IL})$.

The address range is A_{20} : A_0 if in word mode ($\overline{BYTE} = V_{IH}$).

Sector Address Table (MBM29DL324TE)

	_	Sector ad Bank address									Sector			
Bank	Sec- tor	A20 A19 A18 A17 A16 A1							size (Kbytes/	(×8) Address range	(×16) Address range			
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	,go	ria anoso ranigo
	SA0	0	0	0	0	0	0	Х	Х	Х	Χ	64/32	000000h to 00FFFFh	000000h to 007FFFh
	SA1	0	0	0	0	0	1	Х	Х	Х	Х	64/32	010000h to 01FFFFh	008000h to 00FFFFh
	SA2	0	0	0	0	1	0	Х	Х	Х	Х	64/32	020000h to 02FFFFh	010000h to 017FFFh
	SA3	0	0	0	0	1	1	Х	Х	Х	Х	64/32	030000h to 03FFFFh	018000h to 01FFFFh
	SA4	0	0	0	1	0	0	Х	Х	Х	Χ	64/32	040000h to 04FFFFh	020000h to 027FFFh
	SA5	0	0	0	1	0	1	Х	Х	Х	X	64/32	050000h to 05FFFFh	028000h to 02FFFFh
	SA6	0	0	0	1	1	0	Х	Х	Х	Х	64/32	060000h to 06FFFFh	030000h to 037FFFh
	SA7	0	0	0	1	1	1	Х	Х	Х	Χ	64/32	070000h to 07FFFFh	038000h to 03FFFFh
	SA8	0	0	1	0	0	0	Х	Х	Х	Х	64/32	080000h to 08FFFFh	040000h to 047FFFh
	SA9	0	0	1	0	0	1	Х	Х	Х	Х	64/32	090000h to 09FFFFh	048000h to 04FFFFh
	SA10	0	0	1	0	1	0	Х	Х	Х	Χ	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh
	SA11	0	0	1	0	1	1	Х	Х	Х	Χ	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh
	SA12	0	0	1	1	0	0	Х	Х	Х	Х	64/32	0C0000h to 0CFFFFh	060000h to 067FFFh
	SA13	0	0	1	1	0	1	Х	Х	Х	Х	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh
	SA14	0	0	1	1	1	0	Х	Х	Х	Х	64/32	0E0000h to 0EFFFh	070000h to 077FFFh
Bank	SA15	0	0	1	1	1	1	Х	Х	Х	Х	64/32	0F0000h to 0FFFFh	078000h to 07FFFFh
2	SA16	0	1	0	0	0	0	Х	Х	Х	Х	64/32	100000h to 10FFFFh	080000h to 087FFFh
	SA17	0	1	0	0	0	1	Х	Х	Х	Х	64/32	110000h to 11FFFFh	088000h to 08FFFFh
	SA18	0	1	0	0	1	0	Х	Х	Х	Х	64/32	120000h to 12FFFFh	090000h to 097FFFh
	SA19	0	1	0	0	1	1	Х	Х	Х	Х	64/32	130000h to 13FFFFh	098000h to 09FFFFh
	SA20	0	1	0	1	0	0	Х	Х	Х	Χ	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh
	SA21	0	1	0	1	0	1	Х	Х	Х	Х	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh
	SA22	0	1	0	1	1	0	Х	Х	Х	Х	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh
	SA23	0	1	0	1	1	1	Х	Х	Х	Х	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh
	SA24	0	1	1	0	0	0	Х	Х	Х	Х	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh
	SA25	0	1	1	0	0	1	Х	Х	Х	Х	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh
	SA26	0	1	1	0	1	0	Х	Х	Х	Х	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh
	SA27	0	1	1	0	1	1	Х	Х	Х	Х	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh
	SA28	0	1	1	1	0	0	Χ	Х	Χ	Χ	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFh
	SA29	0	1	1	1	0	1	Χ	Χ	Χ	Χ	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh
	SA30	0	1	1	1	1	0	Χ	Χ	Χ	Χ	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFh
	SA31	0	1	1	1	1	1	Χ	Х	Χ	Χ	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFh

					Sec	tor	addı	ress	•			Sector	(5)	
Bank	Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)		
	SA32	1	0	0	0	0	0	Х	Х	Х	Х	64/32	200000h to 20FFFFh	100000h to 107FFFh
	SA33	1	0	0	0	0	1	Х	Х	Х	Х	64/32	210000h to 21FFFFh	108000h to 10FFFFh
	SA34	1	0	0	0	1	0	Χ	Х	Х	Х	64/32	220000h to 22FFFFh	110000h to 117FFFh
	SA35	1	0	0	0	1	1	Х	Х	Х	Х	64/32	230000h to 23FFFFh	118000h to 11FFFFh
	SA36	1	0	0	1	0	0	Х	Х	Х	Х	64/32	240000h to 24FFFFh	120000h to 127FFFh
	SA37	1	0	0	1	0	1	Х	Х	Х	Х	64/32	250000h to 25FFFFh	128000h to 12FFFFh
	SA38	1	0	0	1	1	0	Х	Х	Х	Х	64/32	260000h to 26FFFFh	130000h to 137FFFh
	SA39	1	0	0	1	1	1	Х	Х	Х	Х	64/32	270000h to 27FFFFh	138000h to 13FFFFh
	SA40	1	0	1	0	0	0	Х	Х	Х	Х	64/32	280000h to 28FFFFh	140000h to 147FFFh
	SA41	1	0	1	0	0	1	Х	Х	Х	Х	64/32	290000h to 29FFFFh	148000h to 14FFFFh
	SA42	1	0	1	0	1	0	Х	Х	Х	Х	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh
	SA43	1	0	1	0	1	1	Х	Х	Х	Х	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh
	SA44	1	0	1	1	0	0	Χ	Х	Х	Х	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
	SA45	1	0	1	1	0	1	Χ	Х	Х	Х	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA46	1	0	1	1	1	0	Х	Х	Х	Х	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA47	1	0	1	1	1	1	Χ	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
Bank	SA48	1	1	0	0	0	0	Χ	Х	Х	Х	64/32	300000h to 30FFFFh	180000h to 187FFFh
1	SA49	1	1	0	0	0	1	Χ	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA50	1	1	0	0	1	0	Χ	Х	Х	Х	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA51	1	1	0	0	1	1	Х	Х	Х	Х	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA52	1	1	0	1	0	0	Х	Х	Х	Х	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA53	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
	SA54	1	1	0	1	1	0	Х	Х	Х	Х	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
	SA55	1	1	0	1	1	1	Х	Х	Х	Х	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA56	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
	SA57	1	1	1	0	0	1	Х	Х	Х	Х	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA58	1	1	1	0	1	0	Х	Х	Х	Х	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA59	1	1	1	0	1	1	Χ	Х	Х	Χ	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA60	1	1	1	1	0	0	Χ	Х	Х	Χ	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
	SA61	1	1	1	1	0	1	Χ	Х	Х	Χ	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA62	1	1	1	1	1	0	Х	Х	Х	Χ	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA63	1	1	1	1	1	1	0	0	0	Χ	8/4	3F0000h to 3F1FFFh	1F8000h to 1F8FFFh
	SA64	1	1	1	1	1	1	0	0	1	Х	8/4	3F2000h to 3F3FFFh	1F9000h to 1F9FFFh
	SA65	1	1	1	1	1	1	0	1	0	Χ	8/4	3F4000h to 3F5FFFh	1FA000h to 1FAFFFh
	1												•	(Continued

(Continued)

					Sec	tor	addı	ress	3			Sector	4.5	(1 -)	
Bank	ank Sec- tor		Baı	nk a	ddr	ess						size (Kbytes/	(×8) Address range	(×16) Address range	
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	3		
	SA66	1	1	1	1	1	1	0	1	1	Х	8/4	3F6000h to 3F7FFFh	1FB000h to 1FBFFFh	
	SA67	1	1	1	1	1	1	1	0	0	Х	8/4	3F8000h to 3F9FFFh	1FC000h to 1FCFFFh	
Bank 1	SA68	1	1	1	1	1	1	1	0	1	Х	8/4	3FA000h to 3FBFFFh	1FD000h to 1FDFFFh	
,	SA69	1	1	1	1	1	1	1	1	0	Х	8/4	3FC000h to 3FDFFFh	1FE000h to 1FEFFFh	
	SA70	1	1	1	1	1	1	1	1	1	Χ	8/4	3FE000h to 3FFFFFh	1FF000h to 1FFFFFh	

Note : The address range is A_{20} : A_{-1} if in byte mode $(\overline{BYTE}=V_{IL})$. The address range is A_{20} : A_0 if in word mode $(\overline{BYTE}=V_{IH})$.

Sector Address Table (MBM29DL324BE)

		r Bank address		addı	ress	3			Sector	(0)	(40)			
Bank	Sec- tor			ddre	ess						size (Kbytes/	(×8) Address range	(×16) Address range	
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	3	
	SA70	1	1	1	1	1	1	Х	Х	Х	Х	64/32	3F0000h to 3FFFFFh	1F8000h to 1FFFFFh
	SA69	1	1	1	1	1	0	Х	Х	Х	Х	64/32	3E0000h to 3EFFFFh	1F0000h to 1F7FFFh
	SA68	1	1	1	1	0	1	Х	Х	Х	Х	64/32	3D0000h to 3DFFFFh	1E8000h to 1EFFFFh
	SA67	1	1	1	1	0	0	Х	Х	Х	Х	64/32	3C0000h to 3CFFFFh	1E0000h to 1E7FFFh
	SA66	1	1	1	0	1	1	Х	Х	Х	Х	64/32	3B0000h to 3BFFFFh	1D8000h to 1DFFFFh
	SA65	1	1	1	0	1	0	Х	Х	Х	Х	64/32	3A0000h to 3AFFFFh	1D0000h to 1D7FFFh
	SA64	1	1	1	0	0	1	Х	Х	Х	Х	64/32	390000h to 39FFFFh	1C8000h to 1CFFFFh
	SA63	1	1	1	0	0	0	Х	Х	Х	Х	64/32	380000h to 38FFFFh	1C0000h to 1C7FFFh
	SA62	1	1	0	1	1	1	Х	Х	Х	Х	64/32	370000h to 37FFFFh	1B8000h to 1BFFFFh
	SA61	1	1	0	1	1	0	Х	Х	Х	Х	64/32	360000h to 36FFFFh	1B0000h to 1B7FFFh
Bank 2	SA60	1	1	0	1	0	1	Х	Х	Х	Х	64/32	350000h to 35FFFFh	1A8000h to 1AFFFFh
	SA59	1	1	0	1	0	0	Х	Х	Х	Х	64/32	340000h to 34FFFFh	1A0000h to 1A7FFFh
	SA58	1	1	0	0	1	1	Х	Х	Х	Х	64/32	330000h to 33FFFFh	198000h to 19FFFFh
	SA57	1	1	0	0	1	0	Х	Х	Х	Х	64/32	320000h to 32FFFFh	190000h to 197FFFh
	SA56	1	1	0	0	0	1	Х	Х	Х	Х	64/32	310000h to 31FFFFh	188000h to 18FFFFh
	SA55	1	1	0	0	0	0	Х	Х	Х	Х	64/32	300000h to 30FFFFh	180000h to 187FFFh
	SA54	1	0	1	1	1	1	Х	Х	Х	Х	64/32	2F0000h to 2FFFFFh	178000h to 17FFFFh
	SA53	1	0	1	1	1	0	Х	Х	Х	Х	64/32	2E0000h to 2EFFFFh	170000h to 177FFFh
	SA52	1	0	1	1	0	1	Χ	Χ	Χ	Χ	64/32	2D0000h to 2DFFFFh	168000h to 16FFFFh
	SA51	1	0	1	1	0	0	Χ	Х	Χ	Χ	64/32	2C0000h to 2CFFFFh	160000h to 167FFFh
	SA50	1	0	1	0	1	1	Χ	Χ	Χ	Χ	64/32	2B0000h to 2BFFFFh	158000h to 15FFFFh

Same				Sector ad									Sector		(×16)	
SA49	Bank			Baı	nk a	ddr	ess						00	(×8)	(×16) Address range	
SA48		toi	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11		Address range	Address range	
SA47		SA49	1	0	1	0	1	0	Х	Х	Х	Χ	64/32	2A0000h to 2AFFFFh	150000h to 157FFFh	
SA46		SA48	1	0	1	0	0	1	Х	Х	Х	Χ	64/32	290000h to 29FFFFh	148000h to 14FFFFh	
SA45		SA47	1	0	1	0	0	0	Х	Х	Х	Χ	64/32	280000h to 28FFFFh	140000h to 147FFFh	
Bank 2		SA46	1	0	0	1	1	1	Х	Х	Х	Χ	64/32	270000h to 27FFFFh	138000h to 13FFFFh	
SA44		SA45	1	0	0	1	1	0	Х	Х	Х	Χ	64/32	260000h to 26FFFFh	130000h to 137FFFh	
SA43		SA44	1	0	0	1	0	1	Х	Х	Х	Χ	64/32	250000h to 25FFFFh	128000h to 12FFFFh	
SA41	_	SA43	1	0	0	1	0	0	Х	Х	Х	Χ	64/32	240000h to 24FFFFh	120000h to 127FFFh	
SA40		SA42	1	0	0	0	1	1	Х	Х	Х	Χ	64/32	230000h to 23FFFFh	118000h to 11FFFFh	
SA39		SA41	1	0	0	0	1	0	Х	Х	Х	Х	64/32	220000h to 22FFFFh	110000h to 117FFFh	
SA38		SA40	1	0	0	0	0	1	Х	Х	Х	Χ	64/32	210000h to 21FFFFh	108000h to 10FFFFh	
SA37 0		SA39	1	0	0	0	0	0	Х	Х	Х	Χ	64/32	200000h to 20FFFFh	100000h to 107FFFh	
SA36		SA38	0	1	1	1	1	1	Х	Х	Х	Х	64/32	1F0000h to 1FFFFFh	0F8000h to 0FFFFFh	
SA35 0		SA37	0	1	1	1	1	0	Х	Х	Х	Χ	64/32	1E0000h to 1EFFFFh	0F0000h to 0F7FFFh	
SA34 0		SA36	0	1	1	1	0	1	Х	Х	Х	Χ	64/32	1D0000h to 1DFFFFh	0E8000h to 0EFFFFh	
Bank 1 Bank 1		SA35	0	1	1	1	0	0	Х	Х	Х	Х	64/32	1C0000h to 1CFFFFh	0E0000h to 0E7FFFh	
Bank 1 SA32 0 1 1 0 0 0 1 X X X X 64/32 190000h to 19FFFh 0C8000h to 0CFFF SA31 0 1 1 0 0 0 0 X X X X X 64/32 180000h to 18FFFh 0C0000h to 0C7FF SA30 0 1 0 1 1 1 X X X X 64/32 170000h to 17FFFFh 0B8000h to 0BFFF SA29 0 1 0 1 1 0 1 0 X X X X 64/32 160000h to 16FFFFh 0B0000h to 0B7FF SA28 0 1 0 1 0 1 0 X X X X 64/32 150000h to 15FFFFh 0A8000h to 0A7FF SA26 0 1 0 1 0 1 1 X X X X 64/32 140000h to 14FFFFh 0A0000h to 0A7FF SA26 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFFh 098000h to 09FFFI SA25 0 1 0 0 1 1 X X X X 64/32 120000h to 13FFFFh 098000h to 09FFFI SA24 0 1 0 0 0 1 X X X X 64/32 120000h to 12FFFFh 090000h to 09FFFI SA23 0 1 0 0 0 1 X X X X 64/32 1100000h to 11FFFFh 088000h to 08FFFI SA20 0 0 1 1 1 1 X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFI SA21 0 0 1 1 1 0 0 X X X X X 64/32 0E0000h to 0FFFFFh 068000h to 07FFFI SA20 0 0 1 1 0 0 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 0FFFFI SA39 0 0 1 1 0 0 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 0FFFFI SA39 0 0 1 1 0 0 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFh 068000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFH 068000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFH 058000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFH 058000h to 0FFFFI SA39 0 0 1 1 X X X X X 64/32 0D0000h to 0FFFFFH 058000h to 0FFFFI SA39 0 0 1 0 1 0 1 0 X X X X X 64/32 0D0000h to 0FFFFFH 058000h to 0FFFFI		SA34	0	1	1	0	1	1	Х	Х	Х	Χ	64/32	1B0000h to 1BFFFFh	0D8000h to 0DFFFFh	
Bank 1 Bank 1		SA33	0	1	1	0	1	0	Х	Х	Х	Χ	64/32	1A0000h to 1AFFFFh	0D0000h to 0D7FFFh	
SA30		SA32	0	1	1	0	0	1	Х	Х	Х	Х	64/32	190000h to 19FFFFh	0C8000h to 0CFFFFh	
Bank 1 SA29 0 1 0 1 0 1 1 0 X X X X 64/32 160000h to 16FFFh 0B0000h to 0B7FF SA28 0 1 0 1 0 1 X X X X 64/32 150000h to 15FFFh 0A8000h to 0A7FF SA27 0 1 0 1 0 0 X X X X X 64/32 140000h to 14FFFh 0A0000h to 0A7FF SA26 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFh 098000h to 09FFFh SA25 0 1 0 0 1 1 X X X X 64/32 130000h to 13FFFFh 098000h to 09FFFh SA24 0 1 0 0 0 1 X X X X 64/32 120000h to 12FFFFh 090000h to 09FFFh SA23 0 1 0 0 0 0 X X X X X 64/32 110000h to 11FFFFh 088000h to 08FFFh SA23 0 1 0 0 0 0 X X X X X 64/32 110000h to 10FFFFh 080000h to 08FFFh SA20 0 0 1 1 1 X X X X X 64/32 0F0000h to 0FFFFFh 078000h to 07FFFh SA20 0 0 1 1 0 1 X X X X X 64/32 0E0000h to 0EFFFFh 070000h to 07FFFh SA20 0 0 1 1 0 0 X X X X X 64/32 0D0000h to 0DFFFFh 068000h to 06FFFH SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FFFFH SA18 0 0 1 0 1 0 X X X X X 64/32 0B0000h to 0BFFFFh 058000h to 05FFFFH SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFFh 050000h to 05FFFFH		SA31	0	1	1	0	0	0	Х	Х	Х	Χ	64/32	180000h to 18FFFFh	0C0000h to 0C7FFFh	
Bank 1 SA28 0 1 0 1 X X X X X A 64/32 150000h to 15FFFh 0A8000h to 0AFFF SA27 0 1 0 1 0 0 X X X A 64/32 140000h to 14FFFh 0A0000h to 0A7FF SA26 0 1 0 0 1 1 X X X A 64/32 130000h to 13FFFh 098000h to 09FFFh SA25 0 1 0 0 1 X X X X 64/32 120000h to 12FFFFh 098000h to 09FFFh SA24 0 1 0 0 0 X X X 64/32 110000h to 11FFFFh 088000h to 08FFFh SA23 0 1 0 0 0 X X X 64/32 100000h to 0FFFFh 078000h to 07FFh SA21 0 0 1 1 1 X X		SA30	0	1	0	1	1	1	Х	Х	Х	Χ	64/32	170000h to 17FFFFh	0B8000h to 0BFFFFh	
Bank 1 SA27 0 1 0 1 0 0 X X X X 64/32 140000h to 14FFFh 0A0000h to 0A7FF SA26 0 1 0 0 1 1 X X X 4/32 130000h to 13FFFh 098000h to 09FFFh SA25 0 1 0 0 1 X X X 64/32 120000h to 12FFFh 090000h to 097FFh SA24 0 1 0 0 1 X X X 64/32 110000h to 11FFFh 088000h to 08FFFh SA23 0 1 0 0 0 X X X 64/32 100000h to 10FFFFh 080000h to 087FFh SA22 0 0 1 1 X X X 64/32 0F0000h to 0FFFFh 078000h to 077FFh SA20 0 1 1 0 X X X 64/32 0D0000h to 0FFFFh 068000h to 06FFFh		SA29	0	1	0	1	1	0	Х	Х	Х	Χ	64/32	160000h to 16FFFFh	0B0000h to 0B7FFFh	
1		SA28	0	1	0	1	0	1	Х	Х	Х	Χ	64/32	150000h to 15FFFFh	0A8000h to 0AFFFFh	
SA25 0 1 0 0 1 0 X X X X 64/32 120000h to 12FFFh 090000h to 097FFl SA24 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFh 088000h to 08FFFl SA23 0 1 0 0 0 0 X X X X X 64/32 100000h to 10FFFh 080000h to 087FFl SA22 0 0 1 1 1 1 X X X X 64/32 0F0000h to 0FFFFh 078000h to 07FFFl SA21 0 0 1 1 1 0 X X X X 64/32 0E0000h to 0EFFFh 070000h to 07FFFl SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FFFl SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0CFFFh 060000h to 067FFl SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFFl SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFl		SA27	0	1	0	1	0	0	Х	Х	Х	Χ	64/32	140000h to 14FFFFh	0A0000h to 0A7FFFh	
SA24 0 1 0 0 0 1 X X X X 64/32 110000h to 11FFFh 088000h to 08FFF SA23 0 1 0 0 0 X X X X X 64/32 100000h to 10FFFh 080000h to 087FF SA22 0 0 1 1 1 1 X X X X 64/32 0F0000h to 0FFFFh 078000h to 07FFF SA21 0 0 1 1 1 0 X X X X 64/32 0E0000h to 0EFFFh 070000h to 07FFF SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FFF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0FFFFh 068000h to 06FFF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0BFFFh 058000h to 05FFF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFF		SA26	0	1	0	0	1	1	Х	Х	Х	Χ	64/32	130000h to 13FFFFh	098000h to 09FFFFh	
SA23		SA25	0	1	0	0	1	0	Х	Х	Х	Χ	64/32	120000h to 12FFFFh	090000h to 097FFFh	
SA22 0 0 1 1 1 1 X X X X 64/32 0F0000h to 0FFFFh 078000h to 07FFF SA21 0 0 1 1 1 0 X X X X 64/32 0E0000h to 0EFFFh 070000h to 077FF SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FFF SA19 0 0 1 1 0 0 X X X X X 64/32 0C0000h to 0CFFFh 060000h to 067FF SA18 0 0 1 0 1 1 X X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFF SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FF		SA24	0	1	0	0	0	1	Х	Х	Х	Χ	64/32	110000h to 11FFFFh	088000h to 08FFFFh	
SA21 0 0 1 1 1 0 X X X X 64/32 0E0000h to 0EFFFh 070000h to 077FFl SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FFFl SA19 0 0 1 1 0 0 X X X X 64/32 0C0000h to 0CFFFh 060000h to 067FFl SA18 0 0 1 0 1 1 X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFFl SA17 0 0 1 0 1 0 X X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFl		SA23	0	1	0	0	0	0	Х	Х	Х	Х	64/32	100000h to 10FFFFh	080000h to 087FFFh	
SA20 0 0 1 1 0 1 X X X X 64/32 0D0000h to 0DFFFh 068000h to 06FFFh SA19 0 0 1 1 0 0 X X X X 64/32 0C0000h to 0CFFFh 060000h to 067FFh SA18 0 0 1 0 1 1 X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFFh SA17 0 0 1 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFh		SA22	0	0	1	1	1	1	Х	Х	Х	Χ	64/32	0F0000h to 0FFFFh	078000h to 07FFFFh	
SA19 0 0 1 1 0 0 X X X X 64/32 0C0000h to 0CFFFh 060000h to 067FFh SA18 0 0 1 0 1 1 X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFFh SA17 0 0 1 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFh		SA21	0	0	1	1	1	0	Х	Х	Х	Χ	64/32	0E0000h to 0EFFFFh	070000h to 077FFFh	
SA18 0 0 1 0 1 1 X X X X 64/32 0B0000h to 0BFFFh 058000h to 05FFFh SA17 0 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFh		SA20	0	0	1	1	0	1	Х	Х	Х	Х	64/32	0D0000h to 0DFFFFh	068000h to 06FFFFh	
SA17 0 0 1 0 1 0 X X X X 64/32 0A0000h to 0AFFFh 050000h to 057FFl		SA19	0	0	1	1	0	0	Χ	Х	Х	Χ	64/32	0C0000h to 0CFFFFh	060000h to 067FFFh	
		SA18	0	0	1	0	1	1	X	X	Х	Χ	64/32	0B0000h to 0BFFFFh	058000h to 05FFFFh	
SA16 0 0 1 0 0 1 X X X X 64/32 090000h to 09FFFFh 048000h to 04FFF		SA17	0	0	1	0	1	0	Х	Х	Х	Χ	64/32	0A0000h to 0AFFFFh	050000h to 057FFFh	
		SA16	0	0	1	0	0	1	Х	Х	Х	Χ	64/32	090000h to 09FFFFh	048000h to 04FFFFh	

(Continued)

	nk Sec-				Sec	tor	addı	ress	1			Sector		
Bank	tor		Baı	nk a	ddre	ess						size (Kbytes/	(×8) Address range	(×16) Address range
		A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	A 11	Kwords)	• • • • • • • • • • • • • • • • • • •	3
	SA15	0	0	1	0	0	0	Х	Χ	Х	Х	64/32	080000h to 08FFFFh	040000h to 047FFFh
	SA14	0	0	0	1	1	1	Х	Х	Х	Х	64/32	070000h to 07FFFh	038000h to 03FFFFh
	SA13	0	0	0	1	1	0	Х	Х	Х	Х	64/32	060000h to 06FFFFh	030000h to 037FFFh
	SA12	0	0	0	1	0	1	Х	Χ	Х	Х	64/32	050000h to 05FFFFh	028000h to 02FFFFh
	SA11	0	0	0	1	0	0	Х	Х	Х	Х	64/32	040000h to 04FFFFh	020000h to 027FFFh
	SA10	0	0	0	0	1	1	Х	Х	Х	Х	64/32	030000h to 03FFFFh	018000h to 01FFFFh
	SA9	0	0	0	0	1	0	Х	Х	Х	Х	64/32	020000h to 02FFFFh	010000h to 017FFFh
Bank	SA8	0	0	0	0	0	1	Х	Х	Х	Х	64/32	010000h to 01FFFFh	008000h to 00FFFFh
1	SA7	0	0	0	0	0	0	1	1	1	Х	8/4	00E000h to 00FFFFh	007000h to 007FFFh
	SA6	0	0	0	0	0	0	1	1	0	Х	8/4	00C000h to 00DFFFh	006000h to 006FFFh
	SA5	0	0	0	0	0	0	1	0	1	Х	8/4	00A000h to 00BFFFh	005000h to 005FFFh
	SA4	0	0	0	0	0	0	1	0	0	Х	8/4	008000h to 009FFFh	004000h to 004FFFh
	SA3	0	0	0	0	0	0	0	1	1	Х	8/4	006000h to 007FFFh	003000h to 003FFFh
	SA2	0	0	0	0	0	0	0	1	0	Х	8/4	004000h to 005FFFh	002000h to 002FFFh
	SA1	0	0	0	0	0	0	0	0	1	Х	8/4	002000h to 003FFFh	001000h to 001FFFh
	SA0	0	0	0	0	0	0	0	0	0	Х	8/4	000000h to 001FFFh	000000h to 000FFFh

Note : The address range is A_{20} : $A_{\text{-1}}$ if in byte mode $(\overline{\mbox{BYTE}} = V_{IL})$. The address range is A_{20} : A_0 if in word mode $(\overline{\mbox{BYTE}} = V_{IH})$

Sector Group Addresses (MBM29DL32XTE) (Top Boot Block)

Sector group	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	Sectors
SGA0	0	0	0	0	0	0	Х	Х	Х	SA0
					0	1				
SGA1	0	0	0	0	1	0	Х	Χ	Χ	SA1 to SA3
					1	1				
SGA2	0	0	0	1	Х	Х	Х	Χ	Χ	SA4 to SA7
SGA3	0	0	1	0	Х	Х	Х	Х	Х	SA8 to SA11
SGA4	0	0	1	1	Х	Х	Х	Х	Х	SA12 to SA15
SGA5	0	1	0	0	Х	Х	Х	Х	Х	SA16 to SA19
SGA6	0	1	0	1	Х	Х	Х	Х	Х	SA20 to SA23
SGA7	0	1	1	0	Х	Х	Х	Χ	Χ	SA24 to SA27
SGA8	0	1	1	1	Х	Х	Х	Х	Х	SA28 to SA31
SGA9	1	0	0	0	Х	Х	Х	Χ	Χ	SA32 to SA35
SGA10	1	0	0	1	Х	Х	Х	Χ	Х	SA36 to SA39
SGA11	1	0	1	0	Х	Х	Х	Χ	Х	SA40 to SA43
SGA12	1	0	1	1	Х	Х	Х	Χ	Х	SA44 to SA47
SGA13	1	1	0	0	Х	Х	Х	Х	Х	SA48 to SA51
SGA14	1	1	0	1	Х	Х	Х	Х	Х	SA52 to SA55
SGA15	1	1	1	0	Х	Х	Х	Х	Х	SA56 to SA59
					0	0				
SGA16	1	1	1	1	0	1	Х	Χ	Χ	SA60 to SA62
					1	0				
SGA17	1	1	1	1	1	1	0	0	0	SA63
SGA18	1	1	1	1	1	1	0	0	1	SA64
SGA19	1	1	1	1	1	1	0	1	0	SA65
SGA20	1	1	1	1	1	1	0	1	1	SA66
SGA21	1	1	1	1	1	1	1	0	0	SA67
SGA22	1	1	1	1	1	1	1	0	1	SA68
SGA23	1	1	1	1	1	1	1	1	0	SA69
SGA24	1	1	1	1	1	1	1	1	1	SA70

Sector Group Addresses (MBM29DL32XBE) (Bottom Boot Block)

Sector group	A 20	A 19	A 18	A 17	A 16	A 15	A 14	A 13	A 12	Sectors
SGA0	0	0	0	0	0	0	0	0	0	SA0
SGA1	0	0	0	0	0	0	0	0	1	SA1
SGA2	0	0	0	0	0	0	0	1	0	SA2
SGA3	0	0	0	0	0	0	0	1	1	SA3
SGA4	0	0	0	0	0	0	1	0	0	SA4
SGA5	0	0	0	0	0	0	1	0	1	SA5
SGA6	0	0	0	0	0	0	1	1	0	SA6
SGA7	0	0	0	0	0	0	1	1	1	SA7
					0	1				
SGA8	0	0	0	0	1	0	Х	Х	Х	SA8 to SA10
					1	1				
SGA9	0	0	0	1	Х	Х	Х	Х	Х	SA11 to SA14
SGA10	0	0	1	0	Х	Х	Х	Х	Х	SA15 to SA18
SGA11	0	0	1	1	Х	Х	Х	Х	Х	SA19 to SA22
SGA12	0	1	0	0	Х	Х	Х	Х	Х	SA23 to SA26
SGA13	0	1	0	1	Х	Х	Х	Х	Х	SA27 to SA30
SGA14	0	1	1	0	Х	Х	Х	Х	Х	SA31 to SA34
SGA15	0	1	1	1	Х	Х	Х	Х	Х	SA35 to SA38
SGA16	1	0	0	0	Х	Х	Х	Х	Х	SA39 to SA42
SGA17	1	0	0	1	Х	Х	Х	Х	Х	SA43 to SA46
SGA18	1	0	1	0	Х	Х	Х	Х	Х	SA47 to SA50
SGA19	1	0	1	1	Х	Х	Х	Х	Х	SA51 to SA54
SGA20	1	1	0	0	Х	Х	Х	Х	Х	SA55 to SA58
SGA21	1	1	0	1	Х	Х	Х	Х	Х	SA59 to SA62
SGA22	1	1	1	0	Х	Х	Х	Х	Х	SA63 to SA66
					0	0				
SGA23	1	1	1	1	0	1	Х	Х	Х	SA67 to SA69
					1	0]			
SGA24	1	1	1	1	1	1	Х	Х	Х	SA70

Common Flash Memory Interface Code

Description	A ₀ to A ₆	DQ ₀ to DQ ₁₅
Query-unique ASCII string "QRY"	10h 11h 12h	0051h 0052h 0059h
Primary OEM Command Set 02h : AMD/FJ standard type	13h 14h	0002h 0000h
Address for Primary Extended Table	15h 16h	0040h 0000h
Alternate OEM Command Set (00h = not applicable)	17h 18h	0000h 0000h
Address for Alternate OEM Extended Table	19h 1Ah	0000h 0000h
Vcc Min (write/erase) DQ7 to DQ4: 1 V, DQ3 to DQ0: 100 mV	1Bh	0027h
Vcc Max (write/erase) DQ7 to DQ4: 1 V, DQ3 to DQ0: 100 mV	1Ch	0036h
V _{PP} Min voltage	1Dh	0000h
V _{PP} Max voltage	1Eh	0000h
Typical timeout per single byte/word write 2 ^N μs	1Fh	0004h
Typical timeout for Min size buffer write 2 ^N μs	20h	0000h
Typical timeout per individual sector erase 2 ^N ms	21h	000Ah
Typical timeout for full chip erase 2 ^N ms	22h	0000h
Max timeout for byte/word write 2 ^N times typical	23h	0005h
Max timeout for buffer write 2 ^N times typical	24h	0000h
Max timeout per individual sector erase 2 ^N times typical	25h	0004h
Max timeout for full chip erase 2 ^N times typical	26h	0000h
Device Size = 2 ^N byte	27h	0016h
Flash Device Interface description 02h : ×8/×16	28h 29h	0002h 0000h
Max number of byte in multi-byte write = 2 ^N	2Ah 2Bh	0000h 0000h
Number of Erase Block Regions within device	2Ch	0002h
Erase Block Region 1 Information bit 15 to bit 0 : y = number of sectors bit 31 to bit 16 : z = size (z × 256 bytes)	2Dh 2Eh 2Fh 30h	0007h 0000h 0020h 0000h
Erase Block Region 2 Information bit 15 to bit 0 : y = number of sectors bit 31 to bit 16 : z = size (z × 256 bytes)	31h 32h 33h 34h	003Eh 0000h 0000h 0001h

(Continued)

Description	A ₀ to A ₆	DQ ₀ to DQ ₁₅
Query-unique ASCII string "PRI"	40h 41h 42h	0050h 0052h 0049h
Major version number, ASCII	43h	0031h
Minor version number, ASCII	44h	0032h
Address Sensitive Unlock 00h = Required	45h	0000h
Erase Suspend 02h = To Read & Write	46h	0002h
Sector Protection 00h = Not Supported X = Number of sectors in per group	47h	0001h
Sector Temporary Unprotection 01h = Supported	48h	0001h
Sector Protection Algorithm	49h	0004h
Number of Sector for Bank 2 00h = Not Supported 38h = MBM29DL322TE 30h = MBM29DL323TE 20h = MBM29DL324TE 38h = MBM29DL322BE 30h = MBM29DL323BE 20h = MBM29DL324BE	4Ah	00XXh
Burst Mode Type 00h = Not Supported	4Bh	0000h
Page Mode Type 00h = Not Supported	4Ch	0000h
V _{ACC} (Acceleration) Supply Minimum DQ7 to DQ4: 1 V, DQ3 to DQ0: 100 mV	4Dh	0085h
V_{ACC} (Acceleration) Supply Maximum DQ_7 to DQ_4 : 1 V, DQ_3 to DQ_0 : 100 mV	4Eh	0095h
Boot Type 02h = MBM29DL32XBE 03h = MBM29DL32XTE	4Fh	00XXh
Program Suspend 01h = Supported	50h	0001h

■ FUNCTIONAL DESCRIPTION

Simultaneous Operation

MBM29DL32XTE/BE have feature, which is capability of reading data from one bank of memory while a program or erase operation is in progress in the other bank of memory (simultaneous operation), in addition to the conventional features (read, program, erase, erase-suspend read, and erase-suspend program). The bank selection can be selected by bank address (A_{20} to A_{15}) with zero latency.

The MBM29DL322TE/BE have two banks which contain

Bank 1 (8 KB \times eight sectors, 64 KB \times seven sectors) and Bank 2 (64 KB \times fifty-six sectors).

The MBM29DL323TE/BE have two banks which contain

Bank 1 (8 KB × eight sectors, 64 KB × fifteen sectors) and Bank 2 (64 KB × forty-eight sectors) .

The MBM29DL324TE/BE have two banks which contain

Bank 1 (8 KB × eight sectors, 64 KB × thirty-one sectors) and Bank 2 (64 KB × thirty-two sectors) .

The simultaneous operation can not execute multi-function mode in the same bank. "Simultaneous Operation" in "■ FUNCTIONAL DESCRIPTION" shows combination to be possible for simultaneous operation. (Refer to the "Bank-to-bank Read/Write Timing Diagram" in "■ TIMING DIAGRAM".)

Simultaneous Operation

Case	Bank 1 status	Bank 2 status
1	Read Mode	Read Mode
2	Read Mode	Autoselect Mode
3	Read Mode	Program Mode
4	Read Mode	Erase Mode *
5	Autoselect Mode	Read Mode
6	Program Mode	Read Mode
7	Erase Mode *	Read Mode

^{*:} By writing erase suspend command on the bank address of sector being erased, the erase operation gets suspended so that it enables reading from or programming the remaining sectors.

• Read Mode

The MBM29DL32XTE/BE have two control functions which must be satisfied in order to obtain data at the outputs. $\overline{\text{CE}}$ is the power control and should be used for a device selection. $\overline{\text{OE}}$ is the output control and should be used to gate data to the output pins if a device is selected.

Address access time (tacc) is equal to the delay from stable addresses to valid output data. The chip enable access time (tce) is the delay from stable addresses and stable $\overline{\text{CE}}$ to valid data at the output pins. The output enable access time is the delay from the falling edge of $\overline{\text{OE}}$ to valid data at the output pins (Assuming the addresses have been stable for at least tacc-toe time). When reading out a data without changing addresses after power-up, it is necessary to input hardware reset or to change $\overline{\text{CE}}$ pin from "H" or "L"

Standby Mode

There are two ways to implement the standby mode on the MBM29DL32XTE/BE devices, one using both the CE and RESET pins; the other via the RESET pin only.

When using both pins, a CMOS standby mode is achieved with $\overline{\text{CE}}$ and $\overline{\text{RESET}}$ inputs both held at $V_{\text{CC}} \pm 0.3 \text{ V}$. Under this condition the current consumed is less than 5 μ A Max During Embedded Algorithm operation, V_{CC}

active current (Icc2) is required even \overline{CE} = "H". The device can be read with standard access time (tcE) from either of these standby modes.

When using the $\overline{\text{RESET}}$ pin only, a CMOS standby mode is achieved with $\overline{\text{RESET}}$ input held at $V_{SS} \pm 0.3 \text{ V}$ ($\overline{\text{CE}} =$ "H" or "L") . Under this condition the current is consumed is less than 5 μ A Max Once the $\overline{\text{RESET}}$ pin is taken high, the device requires t_{RH} of wake up time before outputs are valid for read access.

In the standby mode the outputs are in the high impedance state, independent of the $\overline{\text{OE}}$ input.

• Automatic Sleep Mode

There is a function called automatic sleep mode to restrain power consumption during read-out of MBM29DL32XTE/BE data. This mode can be used effectively with an application requested low power consumption such as handy terminals.

To activate this mode, MBM29DL32XTE/BE automatically switch themselves to low power mode when MBM29DL32XTE/BE addresses remain stably during access fine of 150 ns. It is not necessary to control $\overline{\text{CE}}$, $\overline{\text{WE}}$, and $\overline{\text{OE}}$ on the mode. Under the mode, the current consumed is typically 1 μA (CMOS Level) .

During simultaneous operation, Vcc active current (Icc2) is required.

Since the data are latched during this mode, the data are read-out continuously. If the addresses are changed, the mode is canceled automatically and MBM29DL32XTE/BE read-out the data for changed addresses.

Output Disable

With the $\overline{\text{OE}}$ input at a logic high level (V_{IH}), output from the devices are disabled. This will cause the output pins to be in a high impedance state.

Autoselect

The autoselect mode allows the reading out of a binary code from the devices and will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the devices to be programmed with its corresponding programming algorithm. This mode is functional over the entire temperature range of the devices.

To activate this mode, the programming equipment must force V_{ID} (11.5 V to 12.5 V) on address pin A_9 . Two identifier bytes may then be sequenced from the devices outputs by toggling address A_0 from V_{IL} to V_{IH} . All addresses are DON'T CARES except A_0 , A_1 , and A_6 (A-1). (See "MBM29DL32XTE/BE User Bus Operations ($\overline{BYTE} = V_{IL}$)" and "MBM29DL32XTE/BE User Bus Operations ($\overline{BYTE} = V_{IL}$)" in " \blacksquare DEVICE BUS OPERATION".)

The manufacturer and device codes may also be read via the command register, for instances when the MBM29DL32XTE/BE are erased or programmed in a system without access to high voltage on the A₉ pin. The command sequence is illustrated in "MBM29DL32XTE/BE Command Definitions" in "■ DEVICEBUS OPERATION". (Refer to Autoselect Command section.)

Byte 0 ($A_0 = V_{IL}$) represents the manufacturer's code (Fujitsu = 04h) and word 1 ($A_0 = V_{IH}$) represents the device identifier code (MBM29DL322TE = 55h and MBM29DL322BE = 56h for ×8 mode; MBM29DL322TE = 2255h and MBM29DL322BE = 2256h for ×16 mode) . (MBM29DL323TE = 50h and MBM29DL323BE = 53h for ×8 mode; MBM29DL323TE = 2250h and MBM29DL323BE = 2253h for ×16

mode) . (MBM29DL324TE = 5Ch and MBM29DL324BE = 5Fh for ×8 mode; MBM29DL324TE = 225Ch and MBM29DL324BE = 225Fh for ×16 mode) . These two bytes/words are given in "MBM29DL322/323/324TE/BE Sector Group Protection Verify Autoselect Codes Tables", "Extended Autoselect Code Tables" in "■ DEVICE BUS OPERATION". All identifiers for manufactures and device will exhibit odd parity with DQ7 defined as the parity bit. In order to read the proper device codes when executing the autoselect, A₁ must be V₁L. (See "MBM29DL322/323/324TE/BE Sector Group Protection Verify Autoselect Codes Tables", "Extended Autoselect Code Tables" in "■ DEVICE BUS OPERATION".)

Write

Device erasure and programming are accomplished via the command register. The contents of the register serve as inputs to the internal state machine. The state machine outputs dictate the function of the device.

The command register itself does not occupy any addressable memory location. The register is a latch used to store the commands, along with the address and data information needed to execute the command. The command register is written by bringing \overline{WE} to V_{IL} , while \overline{CE} is at V_{IL} and \overline{OE} is at V_{IH} . Addresses are latched on the falling edge of \overline{WE} or \overline{CE} , whichever happens later; while data is latched on the rising edge of \overline{WE} or \overline{CE} , whichever happens first. Standard microprocessor write timings are used.

Refer to AC Write Characteristics and the Erase/Programming Waveforms for specific timing parameters.

Sector Group Protection

The MBM29DL32XTE/BE feature hardware sector group protection. This feature will disable both program and erase operations in any combination of twenty five sector groups of memory. (See "Sector Group Addresses (MBM29DL32XTE) (Top Boot Block)" and "Sector Group Addresses (MBM29DL32XBE) (Bottom Boot Block)" in "

FLEXIBLE SECTOR-ERASE ARCHITECTURE"). The sector group protection feature is enabled using programming equipment at the user's site. The device is shipped with all sector groups unprotected.

To activate this mode, the programming equipment must force V_{ID} on address pin A₉ and control pin \overline{OE} , (suggest V_{ID} = 11.5 V), \overline{CE} = V_{IL} and A₆ = A₀ = V_{IL}, A₁ = V_{IH}. The sector group addresses (A₂₀, A₁₉, A₁₈, A₁₇, A₁₆, A₁₅, A₁₄, A₁₃, and A₁₂) should be set to the sector to be protected. "Sector Address Table (MBM29DL322TE)", "Sector Address Table (MBM29DL323TE)", "Sector Address Table (MBM29DL323TE)", "Sector Address Table (MBM29DL323TE)", "Sector Address Table (MBM29DL323TE)" and "Sector Address Table (MBM29DL324 BE)" in "■ FLEXIBLE SECTOR-ERASE ARCHITECTURE" define the sector address for each of the seventy one (71) individual sectors, and "Sector Group Addresses (MBM29DL32XTE) (Top Boot Block)" and "Sector Group Addresses (MBM29DL32XBE) (Bottom Boot Block)" in "■ FLEXIBLE SECTOR-ERASE ARCHITECTURE" define the sector group address for each of the twenty five (25) individual group sectors. Programming of the protection circuitry begins on the falling edge of the WE pulse and is terminated with the rising edge of the same. Sector group addresses must be held constant during the WE pulse. See "Sector Group Protection Timing Diagram" in "■ TIMING DIAGRAM" and "Sector Group Protection Algorithm" in "■ FLOW CHART" for sector group protection waveforms and algorithm.

To verify programming of the protection circuitry, the programming equipment must force V_{ID} on address pin A_9 with \overline{CE} and \overline{OE} at V_{IL} and \overline{WE} at V_{IH} . Scanning the sector group addresses (A_{20} , A_{19} , A_{18} , A_{17} , A_{16} , A_{15} , A_{14} , A_{13} , and A_{12}) while (A_6 , A_1 , A_0) = (0, 1, 0) will produce a logical "1" code at device output DQ $_0$ for a protected sector. Otherwise the device will produce "0" for unprotected sector. In this mode, the lower order addresses, except for A_0 , A_1 , and A_6 are DON'T CARES. Address locations with $A_1 = V_{IL}$ are reserved for Autoselect manufacturer and device codes. A_{-1} requires to apply to V_{IL} on byte mode.

Temporary Sector Group Unprotection

This feature allows temporary unprotection of previously protected sector groups of the MBM29DL32XTE/BE devices in order to change data. The Sector Group Unprotection mode is activated by setting the $\overline{\text{RESET}}$ pin to high voltage (V_{ID}). During this mode, formerly protected sector groups can be programmed or erased by selecting the sector group addresses. Once the V_{ID} is taken away from the $\overline{\text{RESET}}$ pin, all the previously protected sector groups will be protected again. Refer to "Temporary Sector Group Unprotection Timing Diagram" in " \blacksquare TIMING DIAGRAM" and "Temporary Sector Group Unprotection Algorithm" in " \blacksquare FLOW CHART".

• RESET

Hardware Reset

The MBM29DL32XTE/BE devices may be reset by driving the RESET pin to V_{IL}. The RESET pin has a pulse requirement and has to be kept low (V_{IL}) for at least "t_{RP}" in order to properly reset the internal state machine. Any operation in the process of being executed will be terminated and the internal state machine will be reset to the read mode "t_{READY}" after the RESET pin is driven low. Furthermore, once the RESET pin goes high, the devices require an additional "t_{RH}" before it will allow read access. When the RESET pin is low, the devices will be in the standby mode for the duration of the pulse and all the data output pins will be tri-stated. If a hardware reset occurs during a program or erase operation, the data at that particular location will be corrupted. Please note that the RY/BY output signal should be ignored during the RESET pulse. See "RESET, RY/BY Timing Diagram" in "■ TIMING DIAGRAM" for the timing diagram. Refer to Temporary Sector Group Unprotection for additional functionality.

• Byte/Word Configuration

The BYTE pin selects the byte (8-bit) mode or word (16-bit) mode for the MBM29DL32XTE/BE devices. When this pin is driven high, the devices operate in the word (16-bit) mode. The data is read and programmed at DQ₀ to DQ₁₅. When this pin is driven low, the devices operate in byte (8-bit) mode. Under this mode, the DQ₁₅/A-₁ pin becomes the lowest address bit and DQ₀ to DQ₁₄ bits are tri-stated. However, the command bus cycle is always an 8-bit operation and hence commands are written at DQ₀ to DQ₁₅ and the DQ₀ to DQ₁₅ bits are ignored. Refer to "Timing Diagram for Word Mode Configuration", "Timing Diagram for Byte Mode Configuration" and "BYTE Timing Diagram for Write Operations" in "■ TIMING DIAGRAM" for the timing diagram.

Boot Block Sector Protection

The Write Protection function provides a hardware method of protecting certain boot sectors without using V_{ID} . This function is one of two provided by the \overline{WP}/ACC pin.

If the system asserts V_{IL} on the $\overline{\text{WP}}/\text{ACC}$ pin, the device disables program and erase functions in the two "outermost" 8 Kbyte boot sectors (MBM29DL32XTE : SA69 and SA70, MBM29DL32XBE : SA0 and SA1) independently of whether those sectors were protected or unprotected using the method described in "Sector Group Protection". The two outermost 8 Kbyte boot sectors are the two sectors containing the lowest addresses in a bottom-boot-configured device, or the two sectors containing the highest addresses in a top-boot-configured device

If the system asserts V_H on the \overline{WP}/ACC pin, the device reverts to whether the two outermost 8 Kbyte boot sectors were last set to be protected or unprotected. That is, sector group protection or unprotection for these two sectors depends on whether they were last protected or unprotected using the method described in "Sector Group Protection".

Accelerated Program Operation

MBM29DL32XTE/BE offers accelerated program operation which enables the programming in high speed. If the system asserts Vacc to the \overline{WP}/ACC pin, the device automatically enters the acceleration mode and the time required for program operation will reduce to about 60%. This function is primarily intended to allow high speed program, so caution is needed as the sector group will temporarily be unprotected.

The system would use a fact program command sequence when programming during acceleration mode. Set command to fast mode and reset command from fast mode are not necessary. When the device enters the acceleration mode, the device automatically set to fast mode. Therefore, the present sequence could be used for programming and detection of completion during acceleration mode.

Removing Vacc from the WP/ACC pin returns the device to normal operation. Do not remove Vacc from WP/ACC pin while programming. See "Accelerated Program Timing Diagram" in "■ TIMING DIAGRAM". Erase operation during Accelerated Program Operation is strictly prohibited.

■ COMMAND DEFINITIONS

Device operations are selected by writing specific address and data sequences into the command register. Some commands are required Bank Address (BA) input. When command sequences are inputted to bank being read, the commands have priority than reading. "MBM29DL32XTE/BE Command Definitions" in " DEVICEBUS OPERATION" defines the valid register command sequences. Note that the Erase Suspend (B0h) and Erase Resume (30h) commands are valid only while the Sector Erase operation is in progress. Also the Program Suspend (B0h) and Program Resume (30h) commands are valid only while the Program operation is in progress. Moreover both Read/Reset commands are functionally equivalent, resetting the device to the read mode. Please note that commands are always written at DQ0 to DQ7 and DQ8 to DQ15 bits are ignored.

Read/Reset Command

In order to return from Autoselect mode or Exceeded Timing Limits ($DQ_5 = 1$) to Read/Reset mode, the Read/Reset operation is initiated by writing the Read/Reset command sequence into the command register. Microprocessor read cycles retrieve array data from the memory. The devices remain enabled for reads until the command register contents are altered.

The devices will automatically power-up in the Read/Reset state. In this case, a command sequence is not required to read data. Standard microprocessor read cycles will retrieve array data. This default value ensures that no spurious alteration of the memory content occurs during the power transition. Refer to the AC Read Characteristics and Waveforms for the specific timing parameters.

Autoselect Command

Flash memories are intended for use in applications where the local CPU alters memory contents. As such, manufacture and device codes must be accessible while the devices reside in the target system. PROM programmers typically access the signature codes by raising A_{θ} to a high voltage. However, multiplexing high voltage onto the address lines is not generally desired system design practice.

The device contains an Autoselect command operation to supplement traditional PROM programming methodology. The operation is initiated by writing the Autoselect command sequence into the command register.

The Autoselect command sequence is initiated by first writing two unlock cycles. This is followed by a third write cycle that contains the bank address (BA) and the Autoselect command. Then the manufacture and device codes can be read from the bank, and an actual data of memory cell can be read from the another bank.

Following the command write, a read cycle from address (BA) 00h retrieves the manufacture code of 04h. A read cycle from address (BA) 01h for \times 16 ((BA) 02h for \times 8) returns the device code (MBM29DL322TE = 55h and MBM29DL322BE = 56h for \times 8 mode; MBM29DL322TE = 2255h and MBM29DL322BE = 2256h for \times 16 mode) . (MBM29DL323TE = 50h and MBM29DL323BE = 53h for \times 8 mode; MBM29DL323TE = 2250h and MBM29DL323BE = 2253h for \times 16 mode) . (MBM29DL324TE = 5Ch and MBM29DL324BE = 5Fh for \times 8 mode; MBM29DL324TE = 225Ch and MBM29DL324BE = 225Fh for \times 16

mode) . (See "MBM29DL322/323/324TE/BE Sector Group Protection Verify Autoselect Codes Tables", "Extended Autoselect Code Tables" in "■ DEVICE BUS OPERATION".)

All manufacturer and device codes will exhibit odd parity with DQ7 defined as the parity bit. Sector state (protection or unprotection) will be informed by address (BA) 02h for \times 16 ((BA) 04h for \times 8) . Scanning the sector group addresses (A20, A19, A18, A17, A16, A15, A14, A13, and A12) while (A6, A1, A0) = (0, 1, 0) will produce a logical "1" at device output DQ0 for a protected sector group. The programming verification should be performed by verify sector group protection on the protected sector. (See "Sector Address Table (MBM29DL324TE) ", "Sector Address Table (MBM29DL324BE) ", "Sector Group Addresses (MBM29DL32XTE) (Top Boot Block) " and "Sector Group Addresses (MBM29DL32XBE) (Bottom Boot Block) " in " FLEXIBLE SECTOR-ERASE ARCHITECTURE".)

The manufacture and device codes can be allowed reading from selected bank. To read the manufacture and device codes and sector group protection status from non-selected bank, it is necessary to write Read/Reset command sequence into the register and then Autoselect command should be written into the bank to be read.

If the software (program code) for Autoselect command is stored into the Flash memory, the device and manufacture codes should be read from the other bank where is not contain the software.

To terminate the operation, it is necessary to write the Read/Reset command sequence into the register, and also to write the Autoselect command during the operation, execute it after writing Read/Reset command sequence.

Byte/Word Programming

The devices are programmed on a byte-by-byte (or word-by-word) basis. Programming is a four bus cycle operation. There are two "unlock" write cycles. These are followed by the program set-up command and data write cycles. Addresses are latched on the falling edge of \overline{CE} or \overline{WE} , whichever happens later and the data is latched on the rising edge of \overline{CE} or \overline{WE} , whichever happens first. The rising edge of \overline{CE} or \overline{WE} (whichever happens first) begins programming. Upon executing the Embedded Program Algorithm command sequence, the system is not required to provide further controls or timings. The device will automatically provide adequate internally generated program pulses and verify the programmed cell margin.

The system can determine the status of the program operation by using DQ7 (Data Polling), DQ6 (Toggle Bit), or RY/BY. The Data Polling and Toggle Bit must be performed at the memory location which is being programmed.

The automatic programming operation is completed when the data on DQ₇ is equivalent to data written to this bit at which time the devices return to the read mode and addresses are no longer latched. (See "Hardware Sequence Flags" in "■ COMMAND DEFINITIONS", Hardware Sequence Flags.) Therefore, the devices require that a valid address to the devices be supplied by the system at this particular instance of time. Hence, Data Polling must be performed at the memory location which is being programmed.

If hardware reset occurs during the programming operation, it is impossible to guarantee the data are being written.

Programming is allowed in any sequence and across sector boundaries. Beware that a data "0" cannot be programmed back to a "1". Attempting to do so may either hang up the device or result in an apparent success according to the data polling algorithm but a read from Read/Reset mode will show that the data is still "0". Only erase operations can convert "0"s to "1"s.

"Embedded Program™ Algorithm" in "■ FLOW CHART" illustrates the Embedded Program™ Algorithm using typical command strings and bus operations.

• Program Suspend/Resume

The Profram Suspend command allows the system to interrupt a program operation so that data can be read from any address. Writing the Program Suspend command (B0h) during the Embedded Program operation immediately suspends the programming. The Program Suspend command may also be issued during a programming operation while an erase is suspended. The bank addresses of sector being programmed should be set when writing the Program Suspend command.

When the Program Suspend command is written during a process, the device halts the program operation within 1 us and updates the state bits.

After the program operation has been suspended, the system can read data from any address. The data at program-suspended address is not valid. Normal read timing and command definitions apply.

After Program Resume command (30h) is written, the device reverts to programming. The bank address of sectors being suspended should be set when writing the Program Resume command. The system can determine the program operation status using the DQ_7 or DQ_6 status bits, just as in the standard program operation. See "Write Operation Status" for more information.

The system may also write Autoselect command sequence when the device in the Program Suspend mode. The device allows reading Autoselect codes at the addresses within programming sectors, since the codes are not stored in the memory. When the device exits form the Autoselect mode, the device reverts to the Program

Suspend mode, and is ready for another valid operation. See "Autoselect Command Sequence" for more information.

The system must write the Program Resume command (address bits are "Bank Address") to exit from the Program Suspend mode and continue programming operation. Further writes of the Resume command are ignored. Another Program Suspend command can be written after the device resumes programming.

• Chip Erase

Chip erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the chip erase command.

Chip erase does not require the user to program the device prior to erase. Upon executing the Embedded Erase Algorithm command sequence the devices will automatically program and verify the entire memory for an all zero data pattern prior to electrical erase (Preprogram function) . The system is not required to provide any controls or timings during these operations.

The system can determine the status of the erase operation by using DQ_7 (\overline{Data} Polling), DQ_6 (Toggle Bit), or RY/BY. The chip erase begins on the rising edge of the last \overline{CE} or \overline{WE} , whichever happens first in the command sequence and terminates when the data on DQ_7 is "1" (See Write Operation Status section.) at which time the device returns to read the mode.

Chip Erase Time; Sector Erase Time × All sectors + Chip Program Time (Preprogramming)

"Embedded Erase™ Algorithm" in "■ FLOW CHART" illustrates the Embedded Erase™ Algorithm using typical command strings and bus operations.

Sector Erase

Sector erase is a six bus cycle operation. There are two "unlock" write cycles. These are followed by writing the "set-up" command. Two more "unlock" write cycles are then followed by the Sector Erase command. The sector address (any address location within the desired sector) is latched on the falling edge of \overline{CE} or \overline{WE} whichever happens later, while the command (Data = 30h) is latched on the rising edge of \overline{CE} or \overline{WE} which happens first. After time-out of "trow" from the rising edge of the last sector erase command, the sector erase operation will begin.

Multiple sectors may be erased concurrently by writing the six bus cycle operations on "MBM29DL32XTE/BE Command Definitions" in " DEVICEBUS OPERATION". This sequence is followed with writes of the Sector Erase command to addresses in other sectors desired to be concurrently erased. The time between writes must be less than " t_{TOW} " otherwise that command will not be accepted and erasure will start. It is recommended that processor interrupts be disabled during this time to guarantee this condition. The interrupts can be re-enabled after the last Sector Erase command is written. A time-out of " t_{TOW} " from the rising edge of last \overline{CE} or \overline{WE} whichever happens first will initiate the execution of the Sector Erase command (s) . If another falling edge of \overline{CE} or \overline{WE} , whichever happens first occurs within the " t_{TOW} " time-out window the timer is reset. (Monitor DQ_3 to determine if the sector erase timer window is still open, see section DQ_3 , Sector Erase Timer.) Resetting the devices once execution has begun will corrupt the data in the sector. In that case, restart the erase on those sectors and allow them to complete. (Refer to the Write Operation Status section for Sector Erase Timer operation.) Loading the sector erase buffer may be done in any sequence and with any number of sectors (0 to 38) .

Sector erase does not require the user to program the devices prior to erase. The devices automatically program all memory locations in the sector (s) to be erased prior to electrical erase (Preprogram function). When erasing a sector or sectors the remaining unselected sectors are not affected. The system is not required to provide any controls or timings during these operations.

The system can determine the status of the erase operation by using DQ_7 (\overline{Data} Polling), DQ_6 (Toggle Bit), or RY/ \overline{BY} .

The sector erase begins after the " t_{TOW} " time out from the rising edge of \overline{CE} or \overline{WE} whichever happens first for the last sector erase command pulse and terminates when the data on DQ_7 is "1" (See Write Operation Status

section.) at which time the devices return to the read mode. Data polling and Toggle Bit must be performed at an address within any of the sectors being erased.

 $\label{eq:multiple Sector Erase Time} \ \ \text{Multiple Sector Erase Time} + \ \ \text{Sector Program Time} \ \ \ \ \text{(Preprogramming)} \] \times \ \ \text{Number of Sector Erase}$

In case of multiple sector erase across bank boundaries, a read from bank (read-while-erase) can not perform.

"Embedded Erase™ Algorithm" in "■ FLOW CHART" illustrates the Embedded Erase™ Algorithm using typical command strings and bus operations.

• Erase Suspend/Resume

The Erase Suspend command allows the user to interrupt a Sector Erase operation and then perform data reads from or programs to a sector not being erased. This command is applicable ONLY during the Sector Erase operation which includes the time-out period for sector erase. Writing the Erase Suspend command (B0h) during the Sector Erase time-out results in immediate termination of the time-out period and suspension of the erase operation.

Writing the Erase Resume command (30h) resumes the erase operation. The bank addresses of sector being erasing or suspending should be set when writing the Erase Suspend or Erase Resume command.

When the Erase Suspend command is written during the Sector Erase operation, the device will take a maximum of " t_{SPD} " to suspend the erase operation. When the devices have entered the erase-suspended mode, the RY/\overline{BY} output pin will be at high impedence state and the DQ_7 bit will be at logic "1", and DQ_6 will stop toggling. The user must use the address of the erasing sector for reading DQ_6 and DQ_7 to determine if the erase operation has been suspended. Further writes of the Erase Suspend command are ignored.

When the erase operation has been suspended, the devices default to the erase-suspend-read mode. Reading data in this mode is the same as reading from the standard read mode except that the data must be read from sectors that have not been erase-suspended. Successively reading from the erase-suspended sector while the device is in the erase-suspend-read mode will cause DQ₂ to toggle. (See the section on DQ₂.)

After entering the erase-suspend-read mode, the user can program the device by writing the appropriate command sequence for Program. This program mode is known as the erase-suspend-program mode. Again, programming in this mode is the same as programming in the regular Program mode except that the data must be programmed to sectors that are not erase-suspended. Successively reading from the erase-suspended sector while the devices are in the erase-suspend-program mode will cause DQ_2 to toggle. The end of the erase-suspended Program operation is detected by the RY/BY output pin, \overline{D} at polling of DQ_7 or by the Toggle Bit I (DQ_6) which is the same as the regular Program operation. Note that DQ_7 must be read from the Program address while DQ_6 can be read from any address within bank being erase-suspended.

To resume the operation of Sector Erase, the Resume command (30h) should be written to the bank being erase suspended. Any further writes of the Resume command at this point will be ignored. Another Erase Suspend command can be written after the chip has resumed erasing.

Extended Command

(1) Fast Mode

MBM29DL32XTE/BE has Fast Mode function. This mode dispenses with the initial two unclock cycles required in the standard program command sequence by writing Fast Mode command into the command register. In this mode, the required bus cycle for programming is two cycles instead of four bus cycles in standard program command. (Do not write erase command in this mode.) The read operation is also executed after exiting this mode. To exit this mode, it is necessary to write Fast Mode Reset command into the command register. The first cycle must contain the bank address. (Refer to the "Extended Sector Group Protection Algorithm" in "■ FLOW CHART".) The Vcc active current is required even $\overline{CE} = V_{IH}$ during Fast Mode.

(2) Fast Programming

During Fast Mode, the programming can be executed with two bus cycles operation. The Embedded Program Algorithm is executed by writing program set-up command (A0h) and data write cycles (PA/PD). (Refer to the "Extended Sector Group Protection Algorithm" in "■ FLOW CHART".)

(3) Extended Sector Group Protection

(4) CFI (Common Flash Memory Interface)

The CFI (Common Flash Memory Interface) specification outlines device and host system software interrogation handshake which allows specific vendor-specified software algorithms to be used for entire families of devices. This allows device-independent, JEDEC ID-independent, and forward-and backward-compatible software support for the specified flash device families. Refer to CFI specification in detail.

The operation is initiated by writing the query command (98h) into the command register. The bank address should be set when writing this command. Then the device information can be read from the bank, and an actual data of memory cell be read from the another bank. Following the command write, a read cycle from specific address retrieves device information. Please note that output data of upper byte (DQ₁₅ to DQ₃) is "0" in word mode (16 bit) read. Refer to the CFI code table. To terminate operation, it is necessary to write the read/reset command sequence into the register. (See "Common Flash Memory Interface Code" in "■ FLEXIBLE SECTOR-ERASE ARCHITECTURE".)

HiddenROM Region

The HiddenROM feature provides a Flash memory region that the system may access through a new command sequence. This is primarily intended for customers who wish to use an Electronic Serial Number (ESN) in the device with the ESN protected against modification. Once the HiddenROM region is protected, any further modification of that region is impossible. This ensures the security of the ESN once the product is shipped to the field.

The HiddenROM region is 64 Kbytes in length and is stored at the same address of the 8 KB \times 8 sectors. The MBM29DL32XTE occupies the address of the byte mode 3F0000h to 3FFFFFh (word mode 1F8000h to 1FFFFh) and the MBM29DL32XBE type occupies the address of the byte mode 000000h to 00FFFFh (word mode 000000h to 007FFFh) . After the system has written the Enter HiddenROM command sequence, the system may read the HiddenROM region by using the addresses normally occupied by the boot sectors. That is, the device sends all commands that would normally be sent to the boot sectors to the HiddenROM region. This mode of operation continues until the system issues the Exit HiddenROM command sequence, or until power is removed from the device. On power-up, or following a hardware reset, the device reverts to sending commands to the boot sectors.

When reading the HiddenROM region, either change addresses or change $\overline{\text{CE}}$ pin from "H" to "L". The same procedure should be taken (changing addresses or $\overline{\text{CE}}$ pin from "H" to "L") after the system issues the Exit HiddenROM command sequence to read actual data of memory cell.

HiddenROM Entry Command

MBM29DL32XTE/BE has a HiddenROM area with One Time Protect function. This area is to enter the security code and to unable the change of the code once set. Program/erase is possible in this area until it is protected. However, once it is protected, it is impossible to unprotect, so please use this with caution.

HiddenROM area is 64 KByte and in the same address area of 8 KB sector. The address of top boot is 3F0000h to 3FFFFFh at byte mode (1F8000h to 1FFFFFh at word mode) and the bottom boot is 000000h to 00FFFFh at byte mode (000000h to 007FFFh at word mode) . These areas are normally the boot block area (8 KB \times 8 sector) . Therefore, write the HiddenROM entry command sequence to enter the HiddenROM area. It is called as HiddenROM mode when the HiddenROM area appears.

Sector other than the boot block area could be read during HiddenROM mode. Read/program/erase of the HiddenROM area is possible during HiddenROM mode. Write the HiddenROM reset command sequence to exit the HiddenROM mode. The bank address of the HiddenROM should be set on the third cycle of this reset command sequence.

HiddenROM Program Command

To program the data to the HiddenROM area, write the HiddenROM program command sequence during HiddenROM mode. This command is same as the program command in the past except to write the command during HiddenROM mode. Therefore the detection of completion method is the same as in the past, using the DQ $_7$ data poling, DQ $_6$ toggle bit and RY/ \overline{BY} pin. Need to pay attention to the address to be programmed. If the address other than the HiddenROM area is selected to program, the data of the address will be changed.

• HiddenROM Erase Command

To erase the HiddenROM area, write the HiddenROM erase command sequence during HiddenROM mode. This command is same as the sector erase command in the past except to write the command during HiddenROM mode. Therefore the detection of completion method is the same as in the past, using the DQ $_7$ data poling, DQ $_6$ toggle bit and RY/ \overline{BY} pin. Need to pay attention to the sector address to be erased. If the sector address other than the HiddenROM area is selected, the data of the sector will be changed.

HiddenROM Protect Command

There are two methods to protect the HiddenROM area. One is to write the sector group protect setup command (60h), set the sector address in the HiddenROM area and $(A_6, A_1, A_0) = (0, 1, 0)$, and write the sector group protect command (60h) during the HiddenROM mode. The same command sequence could be used because except that it is in the HiddenROM mode and that it does not apply high voltage to \overline{RESET} pin, it is the same as the extension sector group protect in the past. Please refer to "Function Explanation **Extended Command** (3) Extended Sector Group Protection" for details of extension sector group protect setting.

The other is to apply high voltage (V_{ID}) to A_{9} and \overline{OE} , set the sector address in the HiddenROM area and (A_{6} , A_{1} , A_{0}) = (0, 1, 0), and apply the write pulse during the HiddenROM mode. To verify the protect circuit, apply high voltage (V_{ID}) to A_{9} , specify (A_{6} , A_{1} , A_{0}) = (0, 1, 0) and the sector address in the HiddenROM area, and read. When "1" appears to DQ_{0} , the protect setting is completed. "0" will appear to DQ_{0} if it is not protected. Please apply write pulse again. The same command sequence could be used for the above method because other than the HiddenROM mode, it is the same as the sector group protect in the past. Please refer to "Function Explanation **Sector Group Protection**" for details of sector group protect setting

Other sector group will be effected if the address other than the HiddenROM area is selected for the sector group address, so please be careful. Once it is protected, protection can not be cancelled, so please pay closest attention.

Write Operation Status

Detailed in "Hardware Sequence Flags" in "

COMMAND DEFINITIONS" are all the status flags that can determine the status of the bank for the current mode operation. The read operation from the bank where is not operate Embedded Algorithm returns a data of memory cell. These bits offer a method for determining whether a Embedded Algorithm is completed properly. The information on DQ2 is address sensitive. This means that if an address from an erasing sector is consecutively read, then the DQ2 bit will toggle. However, DQ2 will not toggle if an address from a non-erasing sector is consecutively read. This allows the user to determine which sectors are erasing and which are not.

The status flag is not output from bank (non-busy bank) not executing Embedded Algorithm. For example, there is bank (busy bank) which is now executing Embedded Algorithm. When the read sequence is [1] < busy bank > , [2] < non-busy bank > , [3] < busy bank > , the DQ $_6$ is toggling in the case of [1] and [3]. In case of [2], the data of memory cell is outputted. In the erase-suspend read mode with the same read sequence, DQ $_6$ will not be toggled in the [1] and [3].

In the erase suspend read mode, DQ₂ is toggled in the [1] and [3]. In case of [2], the data of memory cell is outputted.

Hardware Sequence Flags

		Status	DQ ₇	DQ ₆	DQ ₅	DQ₃	DQ_2
	Embedded F	Program Algorithm	DQ ₇	Toggle	0	0	1
	Embedded Erase Algorithm			Toggle	0	1	Toggle*1
	-	Erase Suspend Read (Erase Suspended Sector)	1	1	0	0	Toggle
In Progress	Erase Suspended Mode	Erase Suspend Read (Non-Erase Suspended Sector)	Data	Data	Data	Data	Data
in riogress inc		Erase Suspend Program (Non-Erase Suspended Sector)	ŪQ ₇	Toggle	0	0	1*2
	Program Suspended	Program Suspend Read (Program Suspended Sector)	Data	Data	Data	Data	Data
	Mode	Program Suspend Read (Non-Program Suspended Sector)	Data	Data	Data	Data	Data
	Embedded F	Program Algorithm	ŪQ ₇	Toggle	1	0	1
Exceeded	Embedded E	rase Algorithm	0	Toggle	1	1	N/A
Time Limits	Erase Suspended Mode	Erase Suspend Program (Non-Erase Suspended Sector)	ŪQ ₇	Toggle	1	0	N/A

^{*1:} Successive reads from the erasing or erase-suspend sector causes DQ2 to toggle.

• DQ7

Data Polling

The MBM29DL32XTE/BE devices feature Data Polling as a method to indicate to the host that the Embedded Algorithms are in progress or completed. During the Embedded Program Algorithm an attempt to read the devices will produce the complement of the data last written to DQ7. Upon completion of the Embedded Program Algorithm, an attempt to read the device will produce the true data last written to DQ7. During the Embedded Erase Algorithm, an attempt to read the device will produce a "0" at the DQ7 output. Upon completion of the

^{*2:} Reading from non-erase suspend sector address will indicate logic "1" at the DQ2 bit.

Embedded Erase Algorithm an attempt to read the device will produce a "1" at the DQ₇ output. The flowchart for Data Polling (DQ₇) is shown in "Data Polling Algorithm" in "■ FLOW CHART".

For programming, the $\overline{\text{Data}}$ Polling is valid after the rising edge of fourth write pulse in the four write pulse sequence.

For chip erase and sector erase, the Data Polling is valid after the rising edge of the sixth write pulse in the six write pulse sequence. Data Polling also works as a flag to indicate whether the device is in erase-suspended mode. DQ7 goes from "0" to "1" during erase-suspended mode. Notice that to determine DQ7 entering erase-suspended mode, indicate the sector adress of sector being erased. Data Polling must be performed at sector address within any of the sectors being erased and not a protected sector. Otherwise, the status may not be valid.

If a program address falls within a protected sector, $\overline{\text{Data}}$ Polling on DQ₇ is active for approximately 1 μs , then that bank returns to the read mode. After an erase command sequence is written, if all sectors selected for erasing are protected, $\overline{\text{Data}}$ Polling on DQ₇ is active for approximately 400 μs , then the bank returns to read mode.

Once the Embedded Algorithm operation is close to being completed, the MBM29DL32XTE/BE data pins (DQ $_7$) may change asynchronously while the output enable (\overline{OE}) is asserted low. This means that the devices are driving status information on DQ $_7$ at one instant of time and then that byte's valid data at the next instant of time. Depending on when the system samples the DQ $_7$ output, it may read the status or valid data. Even if the device has completed the Embedded Algorithm operation and DQ $_7$ has a valid data, the data outputs on DQ $_0$ to DQ $_6$ may be still invalid. The valid data on DQ $_0$ to DQ $_7$ will be read on the successive read attempts.

The Data Polling feature is only active during the Embedded Programming Algorithm, Embedded Erase Algorithm or sector erase time-out. (See "Hardware Sequence Flags" in "■ COMMAND DEFINITIONS".)

See "Data Polling during Embedded Algorithm Operation Timing Diagram" in "■ TIMING DIAGRAM" for the Data Polling timing specifications and diagrams.

• DQ₆

Toggle Bit I

The MBM29DL32XTE/BE also feature the "Toggle Bit I" as a method to indicate to the host system that the Embedded Algorithms are in progress or completed.

During an Embedded Program or Erase Algorithm cycle, successive attempts to read (\overline{OE} toggling) data from the devices will result in DQ $_6$ toggling between one and zero. Once the Embedded Program or Erase Algorithm cycle is completed, DQ $_6$ will stop toggling and valid data will be read on the next successive attempts. During programming, the Toggle Bit I is valid after the rising edge of the fourth write pulse in the four write pulse sequence. For chip erase and sector erase, the Toggle Bit I is valid after the rising edge of the sixth write pulse in the six write pulse sequence. The Toggle Bit I is active during the sector time out.

In programming, if the sector being written to is protected, the toggle bit will toggle for about 1 μ s and then stop toggling without the data having changed. In erase, the devices will erase all the selected sectors except for the ones that are protected. If all selected sectors are protected, the chip will toggle the toggle bit for about 400 μ s and then drop back into read mode, having changed none of the data.

Either $\overline{\text{CE}}$ or $\overline{\text{OE}}$ toggling will cause the DQ6 to toggle. In addition, an Erase Suspend/Resume command will cause the DQ6 to toggle.

The system can use DQ_6 to determine whether a sector is actively erasing or is erase-suspended. When a bank is actively erasing (that is, the Embedded Erase Algorithm is in progress), DQ_6 toggles. When a bank enters the Erase Suspend mode, DQ_6 stops toggling. Successive read cycles during the erase-suspend-program cause DQ_6 to toggle.

To operate toggle bit function properly, $\overline{\mathsf{CE}}$ or $\overline{\mathsf{OE}}$ must be high when bank address is changed.

See "Toggle Bit I during Embedded Algorithm Operation Timing Diagram" in "■ TIMING DIAGRAM" for the Toggle Bit I timing specifications and diagrams.

• DQ5

Exceeded Timing Limits

 DQ_5 will indicate if the program or erase time has exceeded the specified limits (internal pulse count) . Under these conditions DQ_5 will produce a "1". This is a failure condition which indicates that the program or erase cycle was not successfully completed. \overline{Data} Polling is the only operating function of the devices under this condition. The \overline{CE} circuit will partially power down the device under these conditions (to approximately 2 mA) . The \overline{OE} and \overline{WE} pins will control the output disable functions as described in "MBM29DL32XTE/BE User Bus Operations ($\overline{BYTE} = V_{IH}$)" and "MBM29DL32XTE/BE User Bus Operations ($\overline{BYTE} = V_{IL}$)" in " \blacksquare DEVICE BUS OPERATION".

The DQ_5 failure condition may also appear if a user tries to program a non blank location without erasing. In this case the devices lock out and never complete the Embedded Algorithm operation. Hence, the system never reads a valid data on DQ_7 bit and DQ_6 never stops toggling. Once the devices have exceeded timing limits, the DQ_5 bit will indicate a "1." Please note that this is not a device failure condition since the devices were incorrectly used. If this occurs, reset the device with command sequence.

DQ3

Sector Erase Timer

After the completion of the initial sector erase command sequence the sector erase time-out will begin. DQ3 will remain low until the time-out is complete. Data Polling and Toggle Bit are valid after the initial sector erase command sequence.

If \overline{Data} Polling or the Toggle Bit I indicates the device has been written with a valid erase command, DQ₃ may be used to determine if the sector erase timer window is still open. If DQ₃ is high ("1") the internally controlled erase cycle has begun. If DQ₃ is low ("0") the device will accept additional sector erase commands. To insure the command has been accepted, the system software should check the status of DQ₃ prior to and following each subsequent Sector Erase command. If DQ₃ were high on the second status check, the command may not have been accepted.

See "Hardware Sequence Flags" in "■ COMMAND DEFINITIONS": Hardware Sequence Flags.

• DQ2

Toggle Bit II

This toggle bit II, along with DQ6, can be used to determine whether the devices are in the Embedded Erase Algorithm or in Erase Suspend.

Successive reads from the erasing sector will cause DQ_2 to toggle during the Embedded Erase Algorithm. If the devices are in the erase-suspended-read mode, successive reads from the erase-suspended sector will cause DQ_2 to toggle. When the devices are in the erase-suspended-program mode, successive reads from the byte address of the non-erase suspended sector will indicate a logic "1" at the DQ_2 bit.

 DQ_6 is different from DQ_2 in that DQ_6 toggles only when the standard program or Erase, or Erase Suspend Program operation is in progress. The behavior of these two status bits, along with that of DQ_7 , is summarized as follows:

For example, DQ₂ and DQ₆ can be used together to determine if the erase-suspend-read mode is in progress. (DQ₂ toggles while DQ₆ does not.) See also "Toggle Bit Status" in "■ COMMAND DEFINITIONS" and "DQ₂ vs. DQ₆" in "■ TIMING DIAGRAM".

Furthermore, DQ₂ can also be used to determine which sector is being erased. When the device is in the erase mode, DQ₂ toggles if this bit is read from an erasing sector.

To operate toggle bit function properly, $\overline{\mathsf{CE}}$ or $\overline{\mathsf{OE}}$ must be high when bank address is changed.

Reading Toggle Bits DQ6/DQ2

Whenever the system initially begins reading toggle bit status, it must read DQ_7 to DQ_0 at least twice in a row to determine whether a toggle bit is toggling. Typically a system would note and store the value of the toggle bit after the first read. After the second read, the system would compare the new value of the toggle bit with the first. If the toggle bit is not toggling, the device has completed the program or erase operation. The system can read array data on DQ_7 to DQ_0 on the following read cycle.

However, if, after the initial two read cycles, the system determines that the toggle bit is still toggling, the system also should note whether the value of DQ_5 is high (see the section on DQ_5). If it is, the system should then determine again whether the toggle bit is toggling, since the toggle bit may have stopped toggling just as DQ_5 went high. If the toggle bit is no longer toggling, the device has successfully completed the program or erase operation. If it is still toggling, the device did not complete the operation successfully, and the system must write the reset command to return to reading array data.

The remaining scenario is that the system initially determines that the toggle bit is toggling and DQ₅ has not gone high. The system may continue to monitor the toggle bit and DQ₅ through successive read cycles, determining the status as described in the previous paragraph. Alternatively, it may choose to perform other system tasks. In this case, the system must start at the begining of the algorithm when it returns to determine the status of the operation. (Refer to "Toggle Bit Algorithm" in "■ FLOW CHART".)

Mode DQ₇ DQ_6 DQ_2 \overline{DQ}_7 **Program** Toggle 0 **Erase** Toggle Toggle*1 Erase-Suspend Read 1 1 Toggle (Erase-Suspended Sector) \overline{DQ}_7 1*2 Erase-Suspend Program Toggle

Toggle Bit Status

• RY/BY

Ready/Busy

The MBM29DL32XTE/BE provide a RY/BY open-drain output pin as a way to indicate to the host system that the Embedded Algorithms are either in progress or has been completed. If the output is low, the devices are busy with either a program or erase operation. If the output is high, the devices are ready to accept any read/write or erase operation. If the MBM29DL32XTE/BE are placed in an Erase Suspend mode, the RY/BY output will be high.

During programming, the RY/ \overline{BY} pin is driven low after the rising edge of the fourth write pulse. During an erase operation, the RY/ \overline{BY} pin is driven low after the rising edge of the sixth write pulse. The RY/ \overline{BY} pin will indicate a busy condition during the \overline{RESET} pulse. Refer to "RY/ \overline{BY} Timing Diagram during Program/Erase Operations" and " \overline{RESET} , RY/ \overline{BY} Timing Diagram" for a detailed timing diagram. The RY/ \overline{BY} pin is pulled high in standby mode.

Since this is an open-drain output, the pull-up resistor needs to be connected to V_{CC} ; multiples of devices may be connected to the host system via more than one RY/ \overline{BY} pin in parallel.

^{*1 :} Successive reads from the erasing or erase-suspend sector will cause DQ₂ to toggle.

^{*2:} Reading from the non-erase suspend sector address will indicate logic "1" at the DQ2 bit.

Data Protection

The MBM29DL32XTE/BE are designed to offer protection against accidental erasure or programming caused by spurious system level signals that may exist during power transitions. During power up the devices automatically reset the internal state machine in the Read mode. Also, with its control register architecture, alteration of the memory contents only occurs after successful completion of specific multi-bus cycle command sequences.

The devices also incorporate several features to prevent inadvertent write cycles resulting form Vcc power-up and power-down transitions or system noise.

• Low Vcc Write Inhibit

To avoid initiation of a write cycle during V_{CC} power-up and power-down, a write cycle is locked out for V_{CC} less than V_{LKO} (Min) . If $V_{\text{CC}} < V_{\text{LKO}}$, the command register is disabled and all internal program/erase circuits are disabled. Under this condition the device will reset to the read mode. Subsequent writes will be ignored until the V_{CC} level is greater than V_{LKO} . It is the users responsibility to ensure that the control pins are logically correct to prevent unintentional writes when V_{CC} is above V_{LKO} (Min) .

If Embedded Erase Algorithm is interrupted, there is possibility that the erasing sector (s) cannot be used.

• Write Pulse "Glitch" Protection

Noise pulses of less than 3 ns (typical) on \overline{OE} , \overline{CE} , or \overline{WE} will not initiate a write cycle.

Logical Inhibit

Writing is inhibited by holding any one of $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IH}$, or $\overline{WE} = V_{IH}$. To initiate a write cycle \overline{CE} and \overline{WE} must be a logical zero while \overline{OE} is a logical one.

• Power-Up Write Inhibit

Power-up of the devices with $\overline{WE} = \overline{CE} = V_{\parallel}$ and $\overline{OE} = V_{\parallel}$ will not accept commands on the rising edge of \overline{WE} . The internal state machine is automatically reset to the read mode on power-up.

Sector Group Protection

Device user is able to protect each sector group individually to store and protect data. Protection circuit voids both write and erase commands that are addressed to protected sectors.

Any commands to write or erase addressed to protected sector are ignored (see "

FUNCTIONAL DESCRIPTION Sector Group Protection")

■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Rat	ing	Unit
raiametei	Syllibol	Min	Max	Oille
Storage Temperature	T _{stg}	–55	+125	°C
Ambient Temperature with Power Applied	TA	-40	+85	°C
Voltage with Respect to Ground All pins except A ₉ , OE, RESET *1, *2	VIN, VOUT	-0.5	Vcc + 0.5	V
Power Supply Voltage *1	Vcc	-0.5	+4.0	V
A ₉ , $\overline{\text{OE}}$, and $\overline{\text{RESET}}$ *1, *3	Vin	-0.5	+13.0	V
WP/ACC *1, *4	Vacc	-0.5	+10.5	V

^{*1:} Voltage is defined on the basis of Vss = GND = 0 V.

- *2 : Minimum DC voltage on input or I/O pins is -0.5 V. During voltage transitions, input or I/O pins may undershoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input or I/O pins is Vcc + 0.5 V. During voltage transitions, input or I/O pins may overshoot to Vcc + 2.0 V for periods of up to 20 ns.
- *3: Minimum DC input voltage on A₉, \overline{OE} and \overline{RESET} pins is -0.5 V. During voltage transitions, A₉, \overline{OE} and \overline{RESET} pins may undershoot V_{SS} to -2.0 V for periods of up to 20 ns. Voltage difference between input and supply voltage (V_{IN} V_{CC}) does not exceed +9.0 V. Maximum DC input voltage on A₉, \overline{OE} and \overline{RESET} pins is +13.0 V which may overshoot to +14.0 V for periods of up to 20 ns.
- *4: Minimum DC input voltage on WP/ACC pin is -0.5 V. During voltage transitions, WP/ACC pin may undershoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC input voltage on WP/ACC pin is +10.5 V which may overshoot to +12.0 V for periods of up to 20 ns when Vcc is applied.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions	Val	Unit	
Parameter	Parameter Symbol		Min	Max	Offic
Ambient Temperature	TA	MBM29DL32XTE/BE80/90	-40	+85	°C
		MBM29DL32XTE/BE80	+3.0	+3.6	V
Power Supply Voltage*	VCC	MBM29DL32XTE/BE90	+2.7	+3.6	V

^{*:} Voltage is defined on the basis of Vss = GND = 0 V.

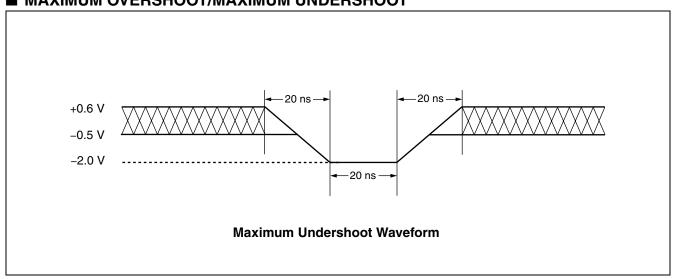
Note: Operating ranges define those limits between which the functionality of the devices are guaranteed.

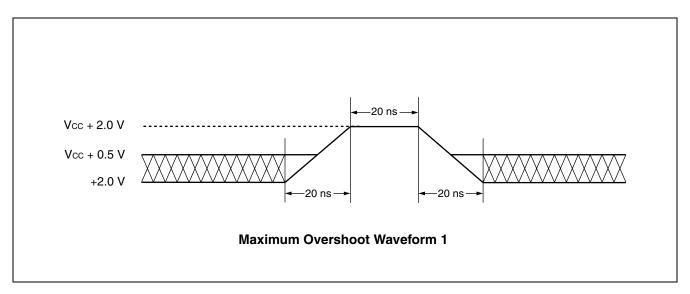
WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

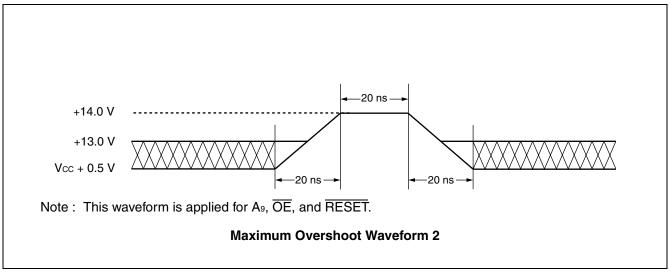
Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ MAXIMUM OVERSHOOT/MAXIMUM UNDERSHOOT







■ DC CHARACTERISTICS

Doromotor	Symbol	Conditions			Value		Unit
Parameter	Symbol	Conditions		Min	Тур	Max	Unit
Input Leakage Current	lu	$V_{IN} = V_{SS}$ to V_{CC} , $V_{CC} = V_{CC}$	-1.0		+1.0	μА	
Output Leakage Current	ILO	$V_{OUT} = V_{SS} \text{ to } V_{CC}, V_{CC} = V_{CC}$	cc Max	-1.0		+1.0	μА
A ₉ , OE, RESET Inputs Leakage Current	Ішт	$V_{CC} = V_{CC} Max,$ $A_9, \overline{OE}, \overline{RESET} = 12.5 V$			_	+35	μА
WP/ACC Accelerated Program Current	ILIA	Vcc = Vcc Max, WP/ACC = Vacc Max			_	20	mA
		$\overline{CE} = V_{IL}, \overline{OE} = V_{IH},$	Byte			16	mA
Vcc Active Current *1	Icc ₁	f = 5 MHz	Word			18	IIIA
Vec Active Current	ICC1	$\overline{CE} = V_{IL}, \overline{OE} = V_{IH},$	Byte			7	mA
		f = 1 MHz	Word			7	шл
Vcc Active Current *2	Icc2	CE = VIL, OE = VIH		_		35	mA
Vcc Current (Standby)	Іссз	$ \begin{array}{l} \text{Vcc} = \text{Vcc Max}, \ \overline{\text{CE}} = \text{Vcc} \\ \text{V}, \ \overline{\text{RESET}} = \text{Vcc} \pm 0.3 \ \text{V}, \\ \overline{\text{WP}}/\text{ACC} = \text{Vcc} \pm 0.3 \ \text{V} \\ \end{array} $	$V_{CC} = V_{CC} \text{ Max}, \overline{CE} = V_{CC} \pm 0.3$ V, $\overline{RESET} = V_{CC} \pm 0.3 \text{ V},$		1	5	μА
Vcc Current (Standby, Reset)	Icc4	Vcc = Vcc Max, RESET = Vss ± 0.3 V	•			5	μА
Vcc Current (Automatic Sleep Mode) *5	Icc5	$\overline{RESET} = Vcc \pm 0.3 V,$	$V_{CC} = V_{CC} Max$, $\overline{CE} = V_{SS} \pm 0.3 V$, $\overline{RESET} = V_{CC} \pm 0.3 V$, $V_{IN} = V_{CC} \pm 0.3 V$ or $V_{SS} \pm 0.3 V$		1	5	μА
Vcc Active Current *6	1	$\overline{CE} = V_{IL}, \overline{OE} = V_{IH}$	Byte	_		51	m 1
(Read-While-Program)	Icc ₆		Word		_	53	mA
Vcc Active Current *6	Icc7	CE = VIL, OE = VIH	Byte	_	_	51	mA
(Read-While-Erase)	ICC7		Word	_		53	IIIA
Vcc Active Current (Erase-Suspend-Program)	Iccs	$\overline{CE} = V_{IL}, \ \overline{OE} = V_{IH}$			_	35	mA
Input Low Voltage	VIL	_		-0.5	_	+ 0.6	V
Input High Voltage	VIH	_		2.0	_	Vcc + 0.3	\
Voltage for Autoselect and Sector Group Protection (A ₉ , OE, RESET) *3, *4	VID	_		11.5	12	12.5	٧
Voltage for WP/ACC Sector Group Protection/ Unprotection and Program Acceleration *4	VACC	_		8.5	9.0	9.5	V
Output Low Voltage	Vol	$I_{OL} = 4.0 \text{ mA}, V_{CC} = V_{CC} \text{ M}$	in	_	_	0.45	V
	V _{OH1}	Iон = -2.0 mA, V сс = V сс I	Min	2.4	_	_	V
Output High Voltage	V _{OH2}	Іон = -100 μΑ		Vcc - 0.4	_		٧
Low Vcc Lock-Out Voltage	VLKO	_		2.3	2.4	2.5	٧

^{*1 :} The lcc current listed includes both the DC operating current and the frequency dependent component.

^{*2 :} Icc active while Embedded Algorithm (program or erase) is in progress.

^{*3 :} This timing is only for Sector Group Protection operation and Autoselect mode.

^{*4 :} Applicable for only Vcc.

^{*5 :} Automatic sleep mode enables the low power mode when address remain stable for 150 ns.

^{*6 :} Embedded Algorithm (program or erase) is in progress. (@5 MHz)

■ AC CHARACTERISTICS

	Cum	ah al			Unit			
Parameter	Symbol		Test setup	80		90		
	JEDEC	Standard	4.000	Min	Max	Min	Max	
Read Cycle Time	tavav	t RC		80	—	90	—	ns
Address to Output Delay	tavqv	tacc	CE = VIL OE = VIL	_	80	_	90	ns
Chip Enable to Output Delay	telqv	t ce	$\overline{OE} = V_{IL}$	_	80	_	90	ns
Output Enable to Output Delay	t GLQV	t oe		_	30	_	35	ns
Chip Enable to Output High-Z	t EHQZ	tof			25		30	ns
Output Enable to Output High-Z	tgнqz	tof			25		30	ns
Output Hold Time from Addresses, CE or OE, Whichever Occurs First	taxqx	tон	_	0	_	0	_	ns
RESET Pin Low to Read Mode	_	tready		_	20	_	20	μS
CE to BYTE Switching Low or High	_	telfl telfh	_		5		5	ns

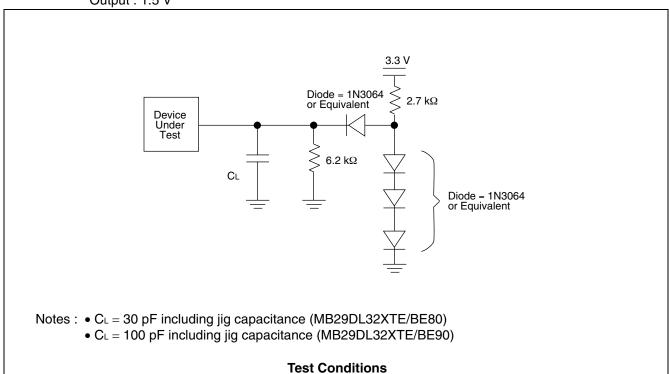
Note: Test Conditions:

Output Load: 1 TTL gate and 30 pF (MBM29DL32XTE/BE80)

1 TTL gate and 100 pF (MBM29DL32XTE/BE90)

Input rise and fall times: 5 ns Input pulse levels: 0.0 V or 3.0 V Timing measurement reference level

> Input: 1.5 V Output: 1.5 V



• Write/Erase/Program Operations

	/Program Operations	0				Va	lue			
	Parameter	Syl	mbol		80			90		Unit
		JEDEC	Standard	Min	Тур	Max	Min	Тур	Max	
Write Cycle Time)	tavav	twc	80	_	_	90		_	ns
Address Setup T	ime	tavwl	tas	0	_	_	0	_	_	ns
Address Setup T Toggle Bit Polling	ime to OE Low During	_	taso	12	_	_	15	_		ns
Address Hold Tir	ne	twlax	t ah	45	_	_	45			ns
Address Hold Tir During Toggle Bi	ne from CE or OE High t Polling		tант	0			0			ns
Data Setup Time		tоvwн	tos	30	_	_	35	_	_	ns
Data Hold Time		twndx	tон	0	_	_	0	_	_	ns
Output Enable	Read		toru	0	_	_	0			ns
Hold Time	Toggle and Data Polling	— tоен	LOEH	10	_	_	10	_	_	ns
CE High During	Toggle Bit Polling		t CEPH	20	_	_	20	_	_	ns
OE High During	Toggle Bit Polling		t oeph	20	_	_	20	_	_	ns
Read Recover Ti	me Before Write	t GHWL	t GHWL	0	_	_	0	_	_	ns
Read Recover Time Before Write		tghel	t GHEL	0	_	_	0	_	_	ns
CE Setup Time		telwl	tcs	0	_	_	0	_	_	ns
WE Setup Time		twlel	tws	0	_	_	0	_	_	ns
CE Hold Time		twheh	t cH	0	_	_	0			ns
WE Hold Time		tehwh	twн	0	_	_	0			ns
Write Pulse Widt	h	twLwH	twp	35	_	_	35	_	_	ns
CE Pulse Width		teleh	t cp	35	_	_	35	_	_	ns
Write Pulse Widt	h High	twhwL	t wph	25	_	_	30	_	_	ns
CE Pulse Width I	High	tehel	tсрн	25	_	_	30	_	_	ns
Programming	Byte	twhwh1	twnwn1		8	_		8		μS
Operation	Word	tvvnvvni	CVVHVVHI		16			16		μS
Sector Erase Op	eration*1	twhwh2	twhwh2		1			1		s
Vcc Setup Time			tvcs	50			50			μS
Rise Time to V _{ID} *	2		tvidr	500			500			ns
Rise Time to VAC	c* ³		tvaccr	500			500			ns
Voltage Transitio	Voltage Transition Time*2		t vlht	4			4			μS
Write Pulse Widt	h* ²		twpp	100		_	100	—		μS
OE Setup Time t	o WE Active*2		toesp	4		_	4	_		μS
CE Setup Time to	o WE Active*2	_	tcsp	4			4			μS
Recover Time from	om RY/BY	_	tпв	0			0	_	_	ns
RESET Pulse Wi	idth	_	t _{RP}	500	_	_	500			ns

(Continued)

(Continued)

	S.v.	Value							
Parameter	Symbol		80			90			Unit
	JEDEC	Standard	Min	Тур	Max	Min	Тур	Max	
RESET High Level Period before Read	_	tпн	200	_		200	_		ns
BYTE Switching Low to Output High-Z		t FLQZ	_	_	30	_	_	30	ns
BYTE Switching High to Output Active		t FHQV	_	_	80	_	_	90	ns
Program/Erase Valid to RY/BY Delay		t BUSY	_	_	90	_	_	90	ns
Delay Time from Embedded Output Enable		t eoe	_	_	80	_		90	ns
Erase Time-Out Time		t TOW	50	_	_	50	_	_	μS
Erase Suspend Transition Time		t spd	_	—	20	_	_	20	μS

^{*1 :} This does not include preprogramming time.

^{*2 :} This timing is for Sector Group Protection operation.

^{*3:} This timing is limited for Acclerated Program Operation only.

■ ERASE AND PROGRAMMING PERFORMANCE

Parameter		Limit		Unit	Comments
Parameter	Min	Тур	Max	Oilit	Comments
Sector Erase Time		1	10	S	Excludes programming time prior to erasure
Word Programming Time		16	360	μS	Excludes system-level
Byte Programming Time	_	8	300	μS	overhead
Chip Programming Time	_	_	100	s	Excludes system-level overhead
Program/Erase Cycle	100,000			cycle	_

■ PIN CAPACITANCE

Parameter	Symbol	Test setup	Тур	Max	Unit
Input Capacitance	Cin	V _{IN} = 0	6.0	7.5	pF
Output Capacitance	Соит	V _{OUT} = 0	8.5	12.0	pF
Control Pin Capacitance	C _{IN2}	V _{IN} = 0	8.0	11.0	pF
WP/ACC Pin Capacitance	Сімз	V _{IN} = 0	21.5	22.5	pF

Notes: • Test conditions T_A = +25 °C, f = 1.0 MHz

• DQ₁₅/A₋₁ pin capacitance is stipulated by output capacitance.

■ FBGA PIN CAPACITANCE

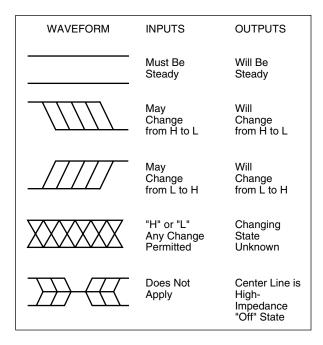
Parameter	Symbol	Condition	Тур	Max	Unit
Input Capacitance	Cin	$V_{IN} = 0$	7.0	9.0	pF
Output Capacitance	Соит	V _{OUT} = 0	9.5	13.0	pF
Control Pin Capacitance	C _{IN2}	V _{IN} = 0	9.0	12.0	pF
WP/ACC Pin Capacitance	Сімз	V _{IN} = 0	21.5	22.5	pF

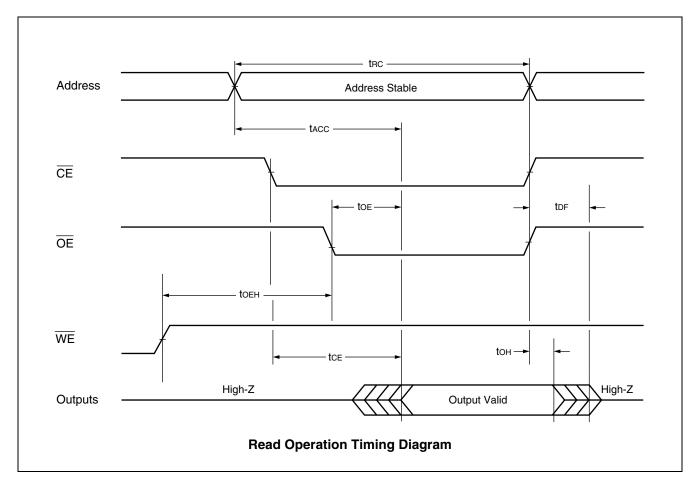
Notes : • Test conditions $T_A = +25$ °C, f = 1.0 MHz

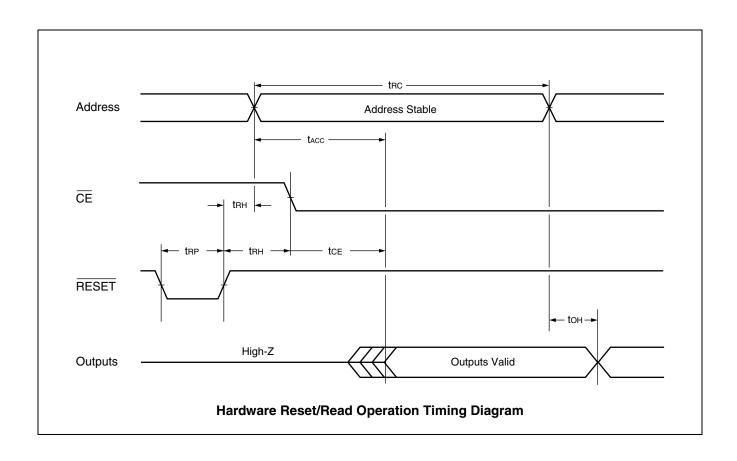
• DQ₁₅/A₋₁ pin capacitance is stipulated by output capacitance.

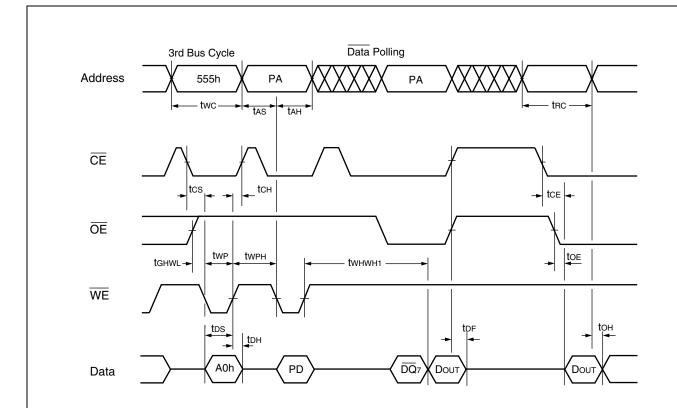
■ TIMING DIAGRAM

• Key to Switching Waveforms





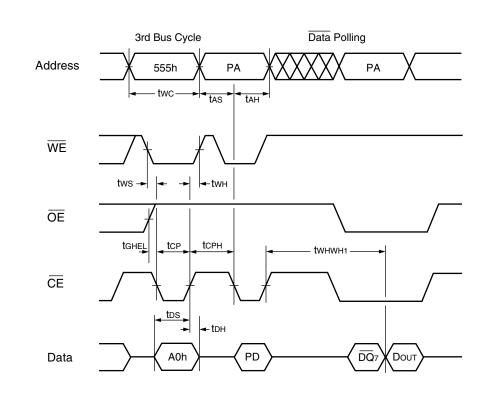




Notes: • PA is address of the memory location to be programmed.

- PD is data to be programmed at byte address.
- \overline{DQ}_7 is the output of the complement of the data written to the device.
- Dout is the output of the data written to the device.
- Figure indicates last two bus cycles out of four bus cycle sequence.
- These waveforms are for the ×16 mode. (The addresses differ from ×8 mode.)

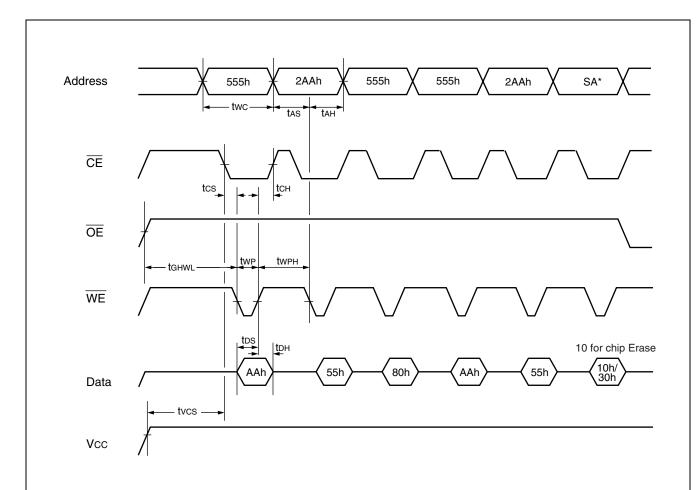
Alternate WE Controlled Program Operation Timing Diagram



Notes: • PA is address of the memory location to be programmed.

- PD is data to be programmed at byte address.
- \overline{DQ}_7 is the output of the complement of the data written to the device.
- Dout is the output of the data written to the device.
- Figure indicates last two bus cycles out of four bus cycle sequence.
- These waveforms are for the ×16 mode. (The addresses differ from ×8 mode.)

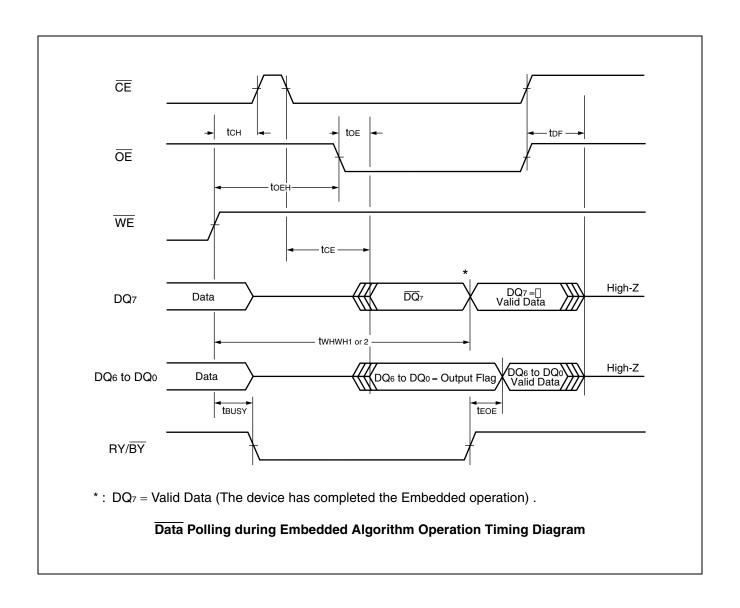
Alternate CE Controlled Program Operation Timing Diagram

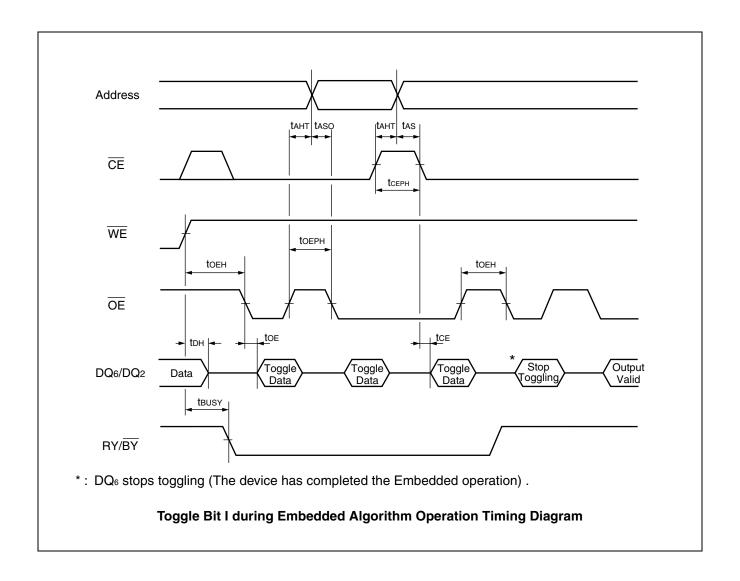


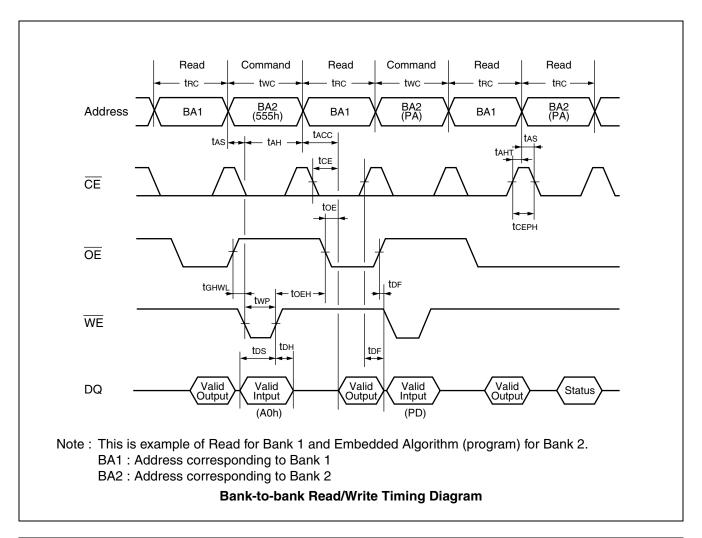
*: SA is the sector address for Sector Erase. Addresses = 555h (Word), AAAh (Byte) for Chip Erase.

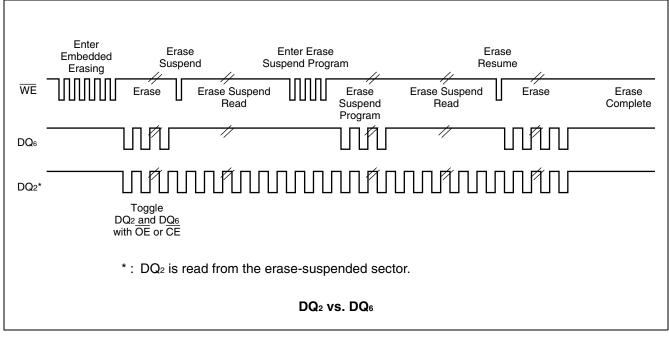
Note: These waveforms are for the $\times 16$ mode. (The addresses differ from $\times 8$ mode.)

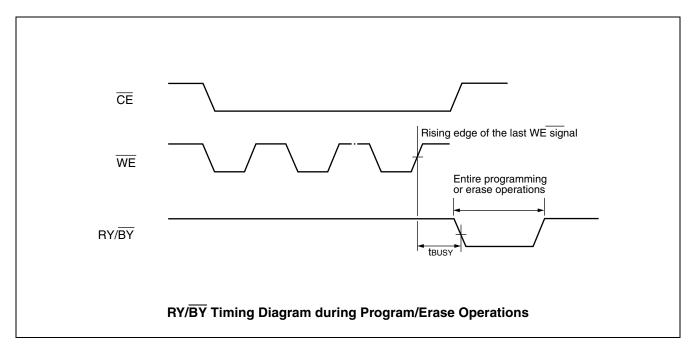
Chip/Sector Erase Operation Timing Diagram

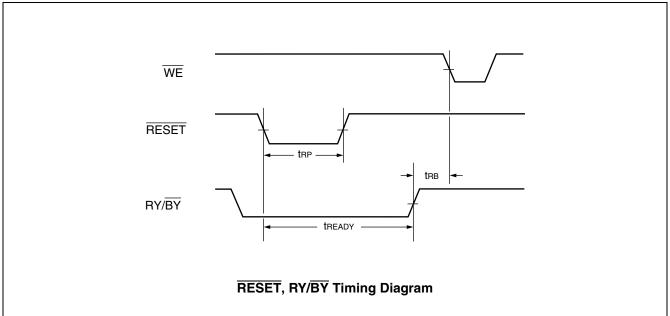


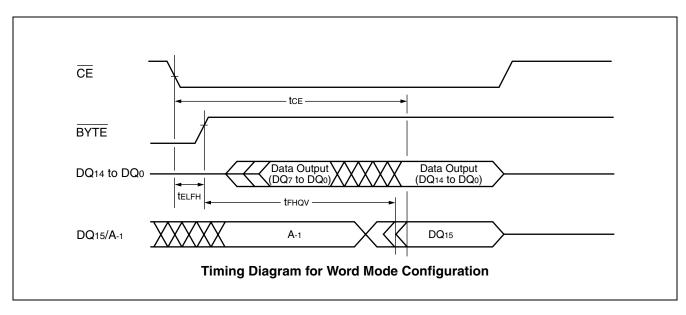


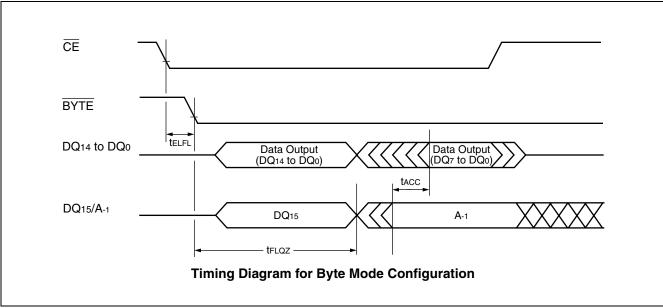


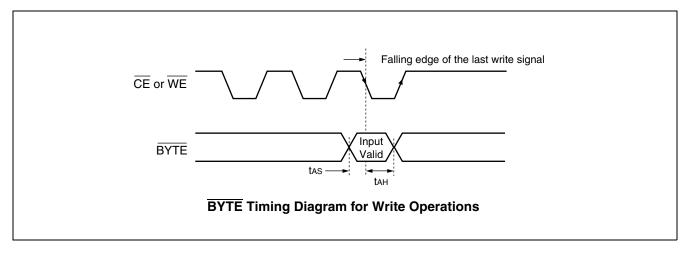


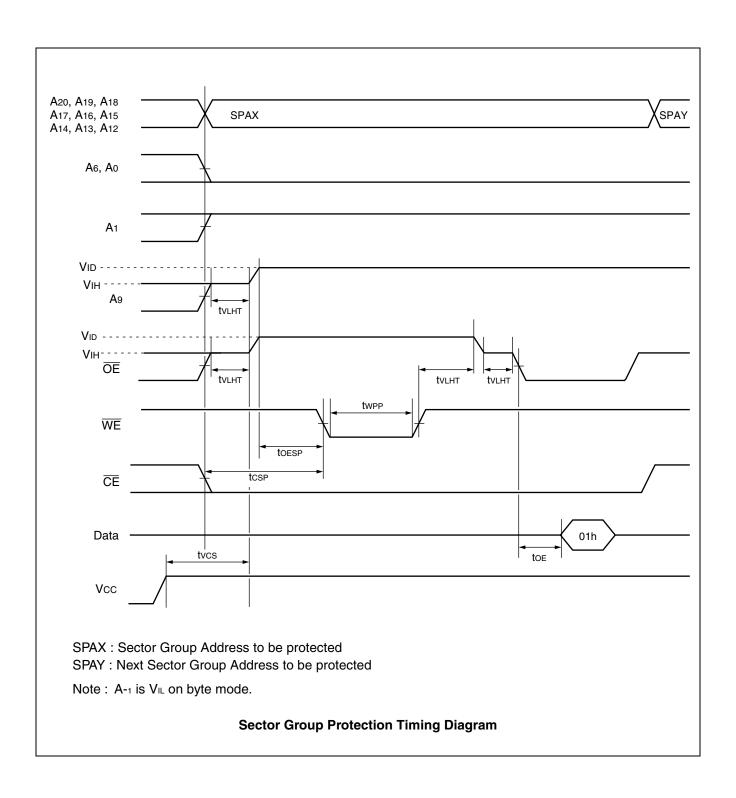


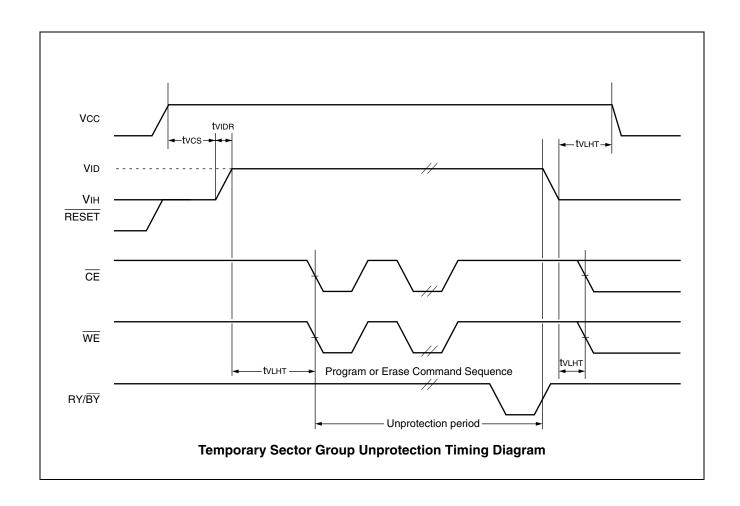


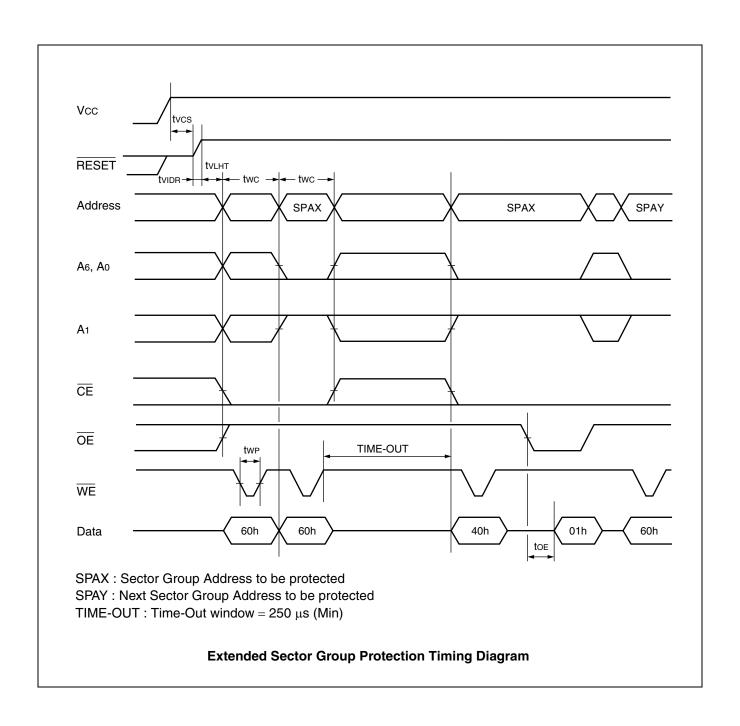


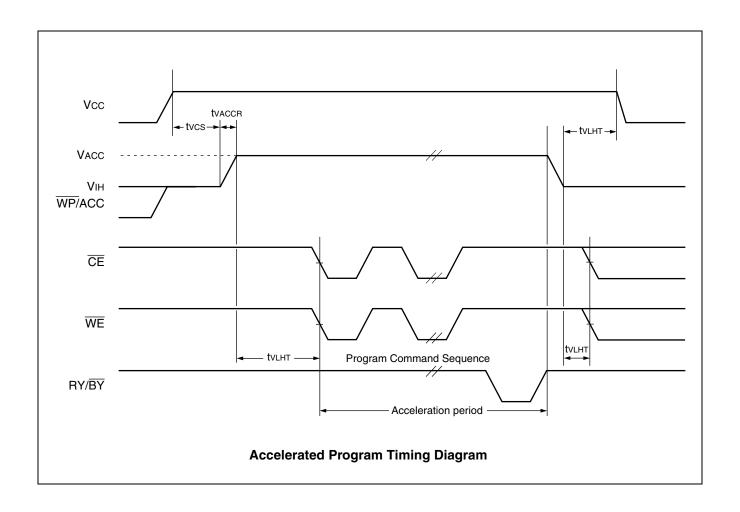






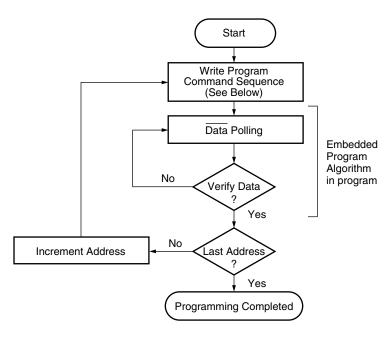




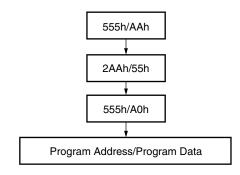


■ FLOW CHART

EMBEDDED ALGORITHM



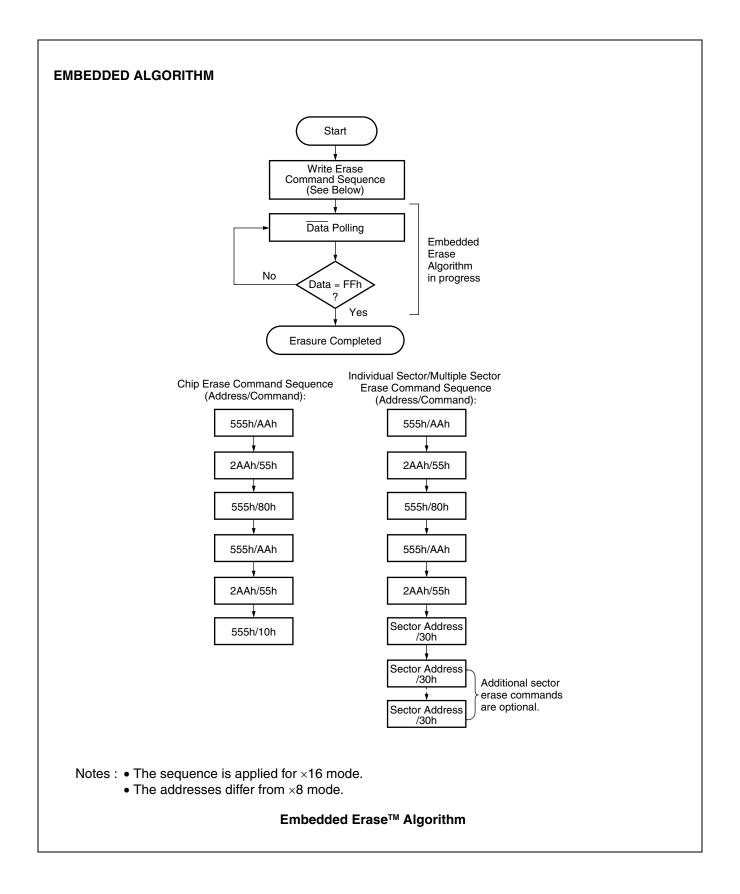
Program Command Sequence (Address/Command):

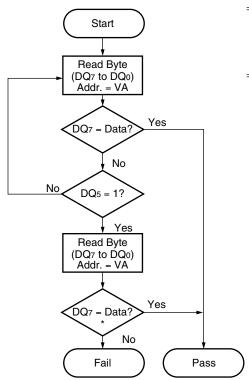


Notes : • The sequence is applied for ×16 mode.

• The addresses differ from ×8 mode.

Embedded Program™ Algorithm



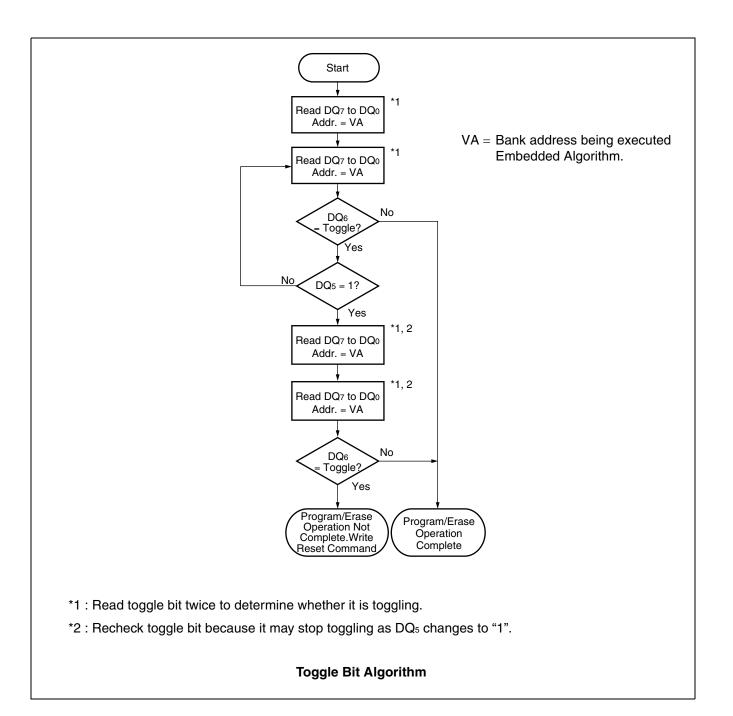


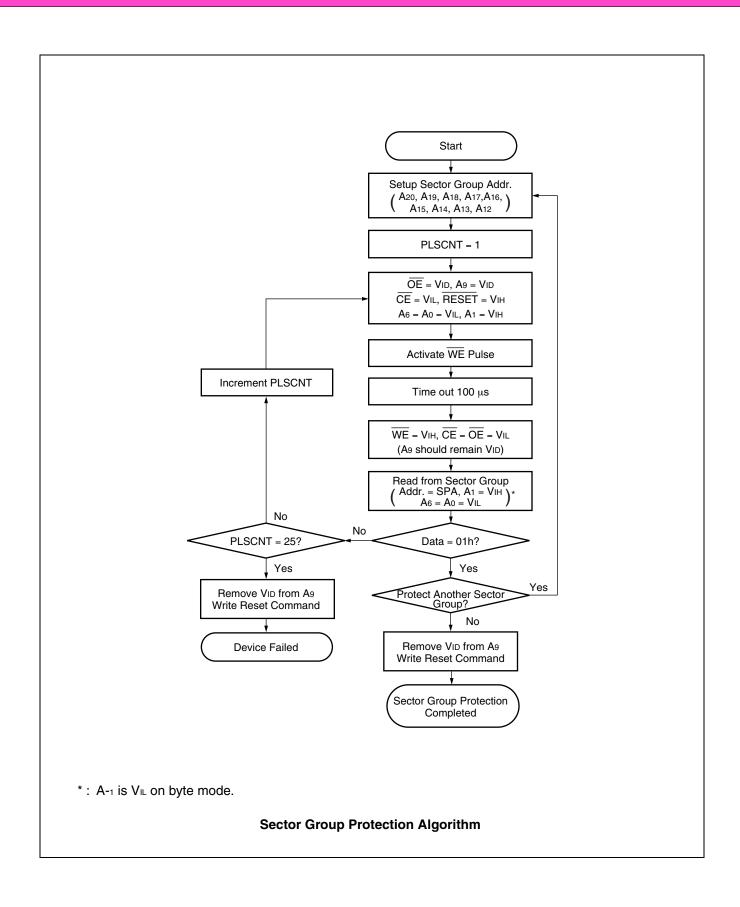
VA = Address for programming

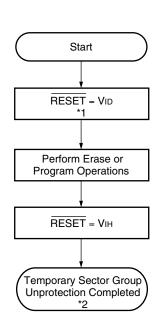
- Any of the sector addresses within the sector being erased during sector erase or multiple sector erases operation.
- Any of the sector addresses within the sector not being protected during chip erase operation.

*: DQ7 is rechecked even if DQ5 = "1" because DQ7 may change simultaneously with DQ5.

Data Polling Algorithm



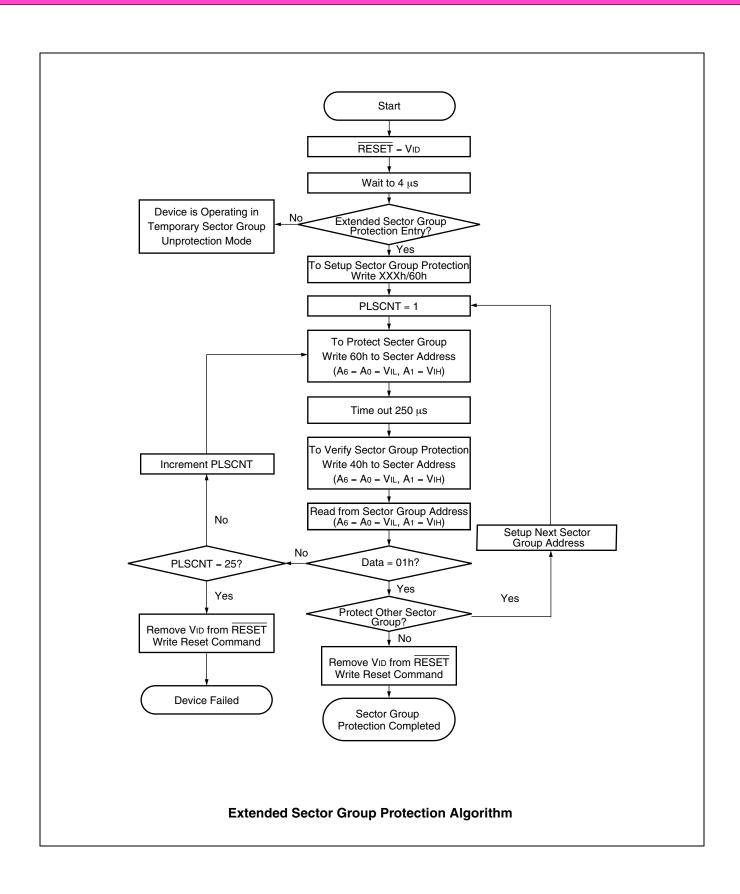


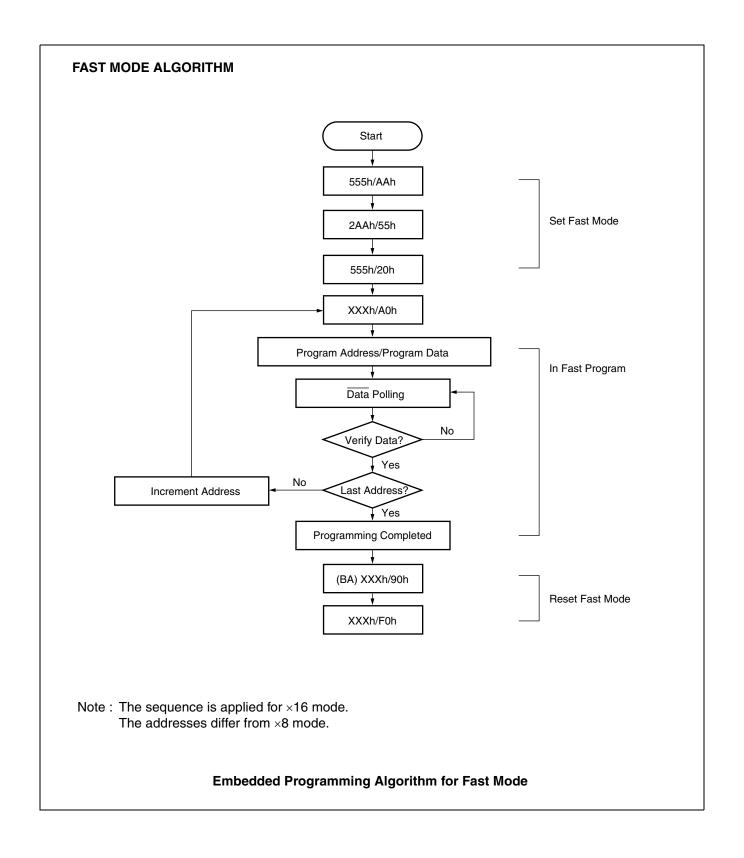


*1 : All protected sector groups are unprotected.

*2 : All previously protected sector groups are protected once again.

Temporary Sector Group Unprotection Algorithm





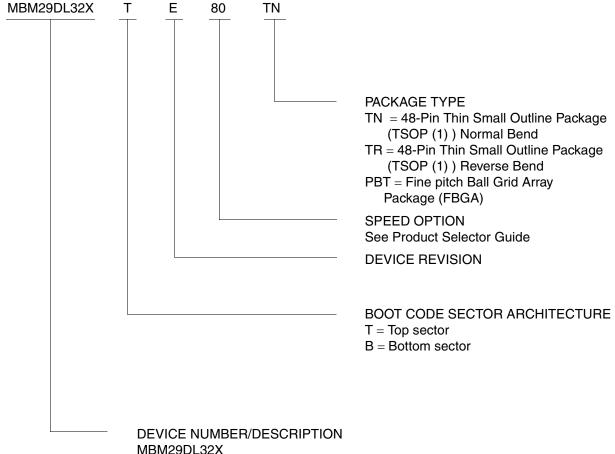
■ ORDERING INFORMATION

Part No.	Package	Access Time (ns)	Remarks
MBM29DL322TE80TN MBM29DL322TE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	80 90	
MBM29DL323TE80TN MBM29DL323TE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	80 90	
MBM29DL324TE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	90	
MBM29DL322TE80TR MBM29DL322TE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	80 90	Top Sector
MBM29DL323TE80TR MBM29DL323TE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	80 90	
MBM29DL324TE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	90	
MBM29DL322TE80PBT MBM29DL322TE90PBT	63-ball plastic FBGA (BGA-63P-M01)	80 90	
MBM29DL323TE80PBT MBM29DL323TE90PBT	63-ball plastic FBGA (BGA-63P-M01)	80 90	
MBM29DL324TE90PBT	63-ball plastic FBGA (BGA-63P-M01)	90	
MBM29DL322BE80TN MBM29DL322BE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	80 90	Bottom Sector
MBM29DL323BE80TN MBM29DL323BE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	80 90	
MBM29DL324BE90TN	48-pin plastic TSOP (1) (FPT-48P-M19) (Normal Bend)	90	
MBM29DL322BE80TR MBM29DL322BE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	80 90	
MBM29DL323BE80TR MBM29DL323BE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	80 90	
MBM29DL324BE90TR	48-pin plastic TSOP (1) (FPT-48P-M20) (Reverse Bend)	90	

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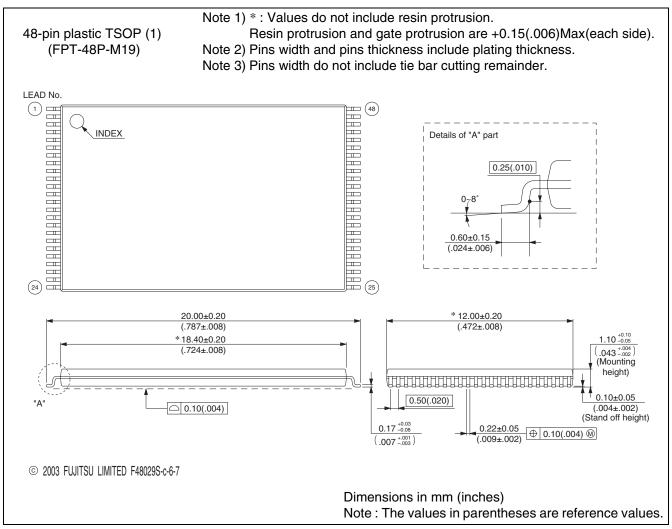
Part No.	Package	Access Time (ns)	Remarks
MBM29DL322BE80PBT MBM29DL322BE90PBT	63-ball plastic FBGA (BGA-63P-M01)	80 90	Bottom Sector
MBM29DL323BE80PBT MBM29DL323BE90PBT	63-ball plastic FBGA (BGA-63P-M01)	80 90	
MBM29DL324BE90PBT	63-ball plastic FBGA (BGA-63P-M01)	90	



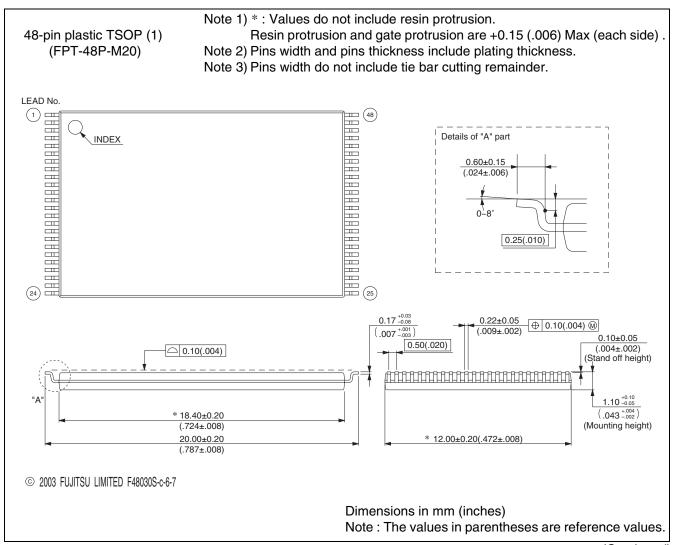
MBM29DL32X 32 Mega-bit (4 M × 8-Bit or 2 M × 16-Bit) CMOS Dual (

32 Mega-bit (4 M \times 8-Bit or 2 M \times 16-Bit) CMOS Dual Operation Flash Memory 3.0 V-only Read, Program, and Erase

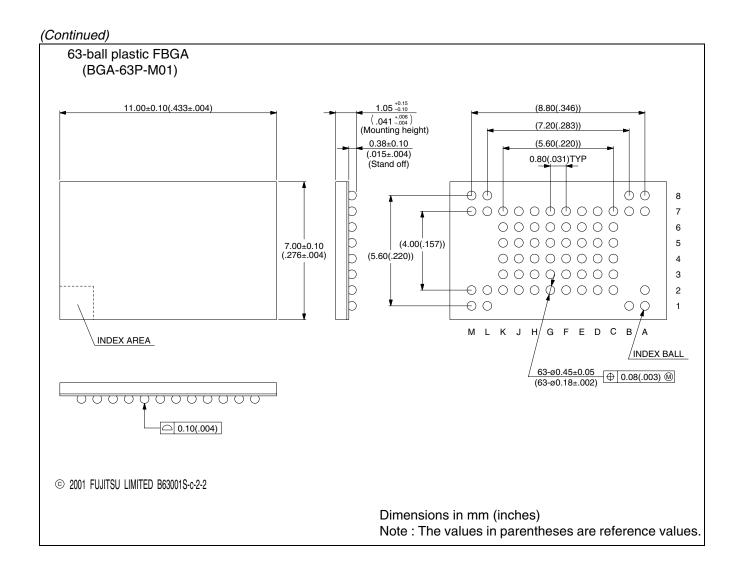
■ PACKAGE DIMENSIONS



(Continued)



(Continued)



Revision History

Revision DS05-20881-8E (July 20, 2007)

The following comment is added.

This product has been retired and is not recommended for new designs. Availability of this document is retained for reference and historical purposes only.

FUJITSU LIMITED

For further information please contact:

Japan

FUJITSU LIMITED Marketing Division Electronic Devices Shinjuku Dai-Ichi Seimei Bldg. 7-1, Nishishinjuku 2-chome, Shinjuku-ku, Tokyo 163-0721, Japan Tel: +81-3-5322-3353

Fax: +81-3-5322-3386 http://edevice.fujitsu.com/

North and South America

FUJITSU MICROELECTRONICS AMERICA, INC. 1250 E. Arques Avenue, M/S 333

Sunnyvale, CA 94088-3470, U.S.A.

Tel: +1-408-737-5600 Fax: +1-408-737-5999 http://www.fma.fujitsu.com/

Europe

FUJITSU MICROELECTRONICS EUROPE GmbH Am Siebenstein 6-10, D-63303 Dreieich-Buchschlag

D-63303 Dreieich-Buchschlag,

Germany

Tel: +49-6103-690-0 Fax: +49-6103-690-122 http://www.fme.fujitsu.com/

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE LTD. #05-08, 151 Lorong Chuan, New Tech Park, Singapore 556741

Tel: +65-6281-0770 Fax: +65-6281-0220

http://www.fmal.fujitsu.com/

Korea

FUJITSU MICROELECTRONICS KOREA LTD. 1702 KOSMO TOWER, 1002 Daechi-Dong, Kangnam-Gu, Seoul 135-280

Korea

Tel: +82-2-3484-7100 Fax: +82-2-3484-7111 http://www.fmk.fujitsu.com/

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